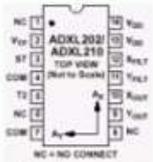


# *Molecular and carbon-based electronic systems*

## ***Lecture 11: Sensing***

*sensors, sensing, transduction & more*  
*ISFETs & nanopores*

# sensors



Accelerometer



Gyro



Pendulum Resistive Tilt Sensors



Piezo Bend Sensor



Metal Detector



Gas Sensor



Geiger-Muller Radiation Sensor



Digital Infrared Ranging



CDS Cell Resistive Light Sensor



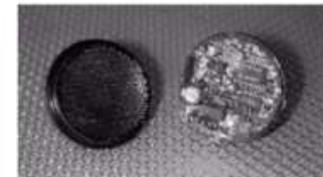
Resistive Bend Sensors



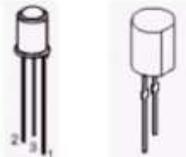
UV Detector



Pyroelectric Detector



Miniature Polaroid Sensor



IR Pin Diode



IR Sensor w/lens



Limit Switch



Mechanical Tilt Sensors



Touch Switch



Pressure Switch



IR Reflection Sensor



IR Amplifier Sensor



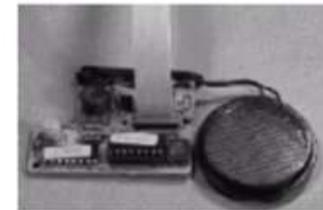
Thyristor



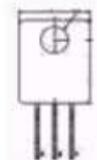
Magnetic Sensor



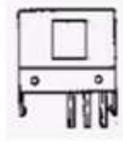
Hall Effect Magnetic Field Sensors



Polaroid Sensor Board



Lite-On IR Remote Receiver



Radio Shack Remote Receiver



IR Modulator Receiver



IRDA Transceiver



Magnetic Reed Switch



Solar Cell



Compass

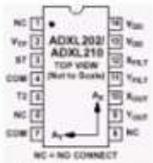


Compass



Piezo Ultrasonic Transducers

# sensors



Accelerometer



Gyro



Pendulum Resistor Tilt Sensors



WeatherSignal  
YOUR MOBILE WEATHER STATION



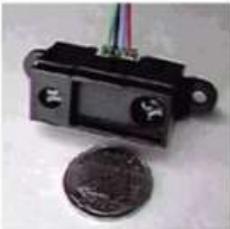
Detector



Gas Sensor



Gieger-Muller Radiation Sensor



Digital Infrared Ranging

**nanoscale, new materials**

low-power, low-cost, robust ... **ubiquitous**



CDS Cell  
Resistive Light Sensor



Resistive Bend Sensor



Humidity and temperature sensor  
(Courtesy of Senshin)



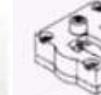
Detector



Limit Switch



Mechanical Tilt Sensors



Pressure



IR Pin

Digital



IR Sensor w/lens

**integration at large scale**

health & environmental monitoring;  
diagnostic tools; personalized medicine;  
drug screening; safety; security;

**control of organic/inorganic interfaces**  
implants, e.g. neuroprosthetics



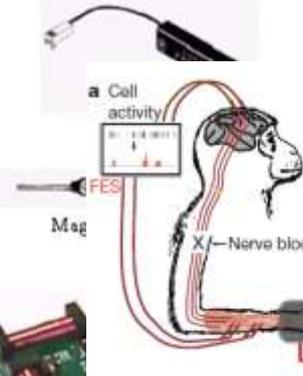
IR Reflection Sensor



IR Amplifier Sensor



Thyristor



a Cell activity

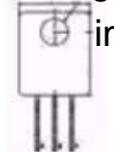
FES

Mag

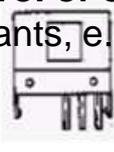
X - Nerve block

Wrist torque

Field



Lite-On IR Remote Receiver



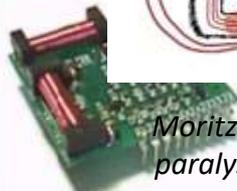
Radio Shack Remote Receiver



IR Modulator Receiver

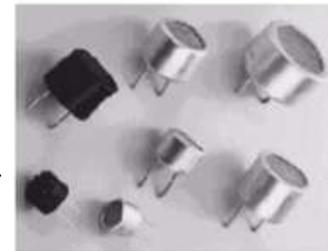


Solar Cell



Compass

Moritz et al., Direct control of paralysed muscles by cortical neurons, Nature (2008)



Piezo Ultrasonic Transducers

# sensors



**nanoscale, new materials**

⇒ low-power, low-cost,  
robust ... **ubiquitous**



# sensors



smart...

phone



refrigerator



***nanoscale, new materials***

⇒ low-power, low-cost,  
robust ... **ubiquitous**

***Internet of Things (IoT)***

***def.:*** Open network of intelligent objects that have the capacity to auto-organize, share information, data and resources, reacting and acting in face of situations and changes in the environment

*Internet 1.0* sharing of data created by people

*Internet "2.0"* sharing of data created by things

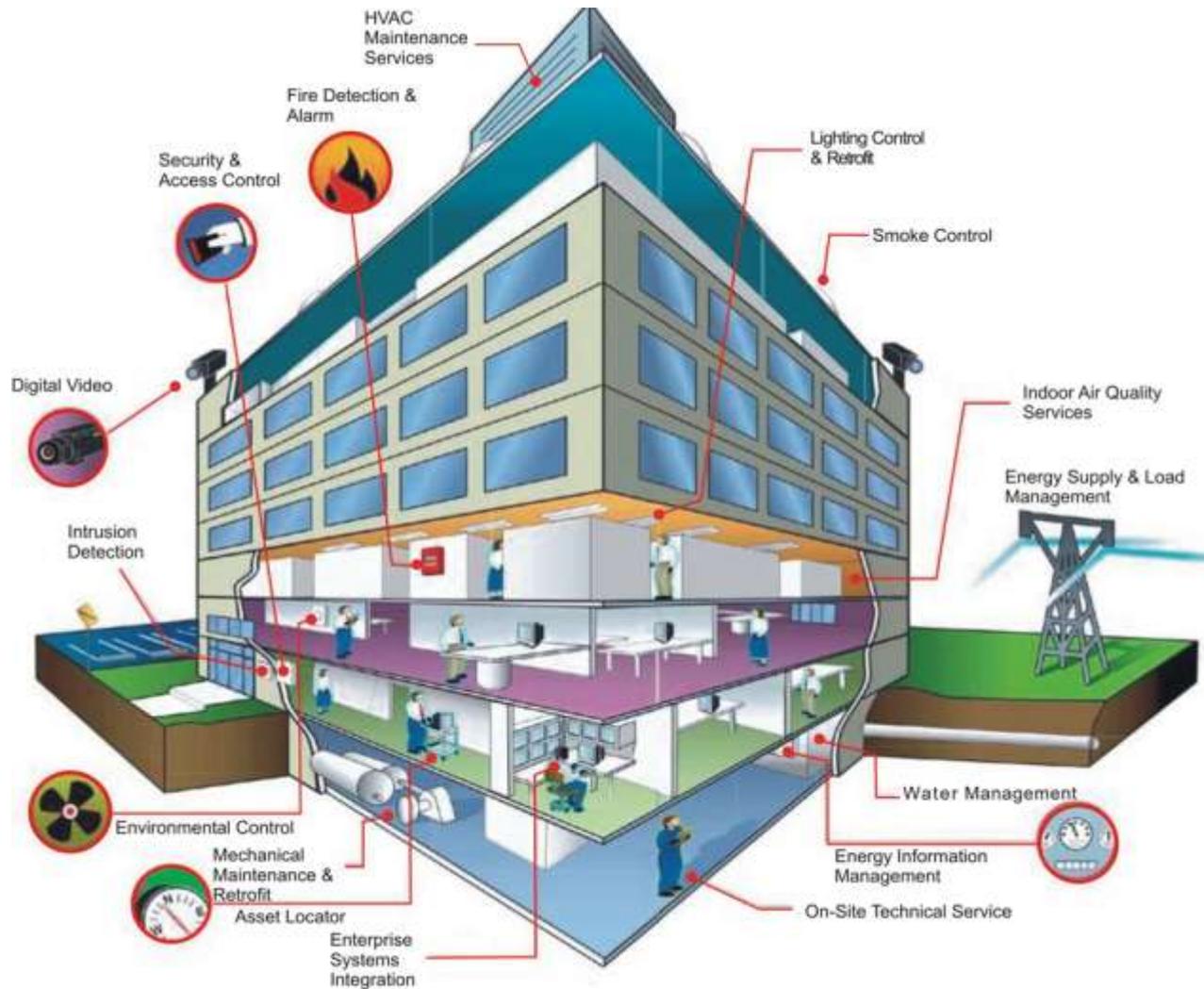
*NB: data protection issues...*

⇒ integration of smart objects ...

# sensors

## smart building: the technical side

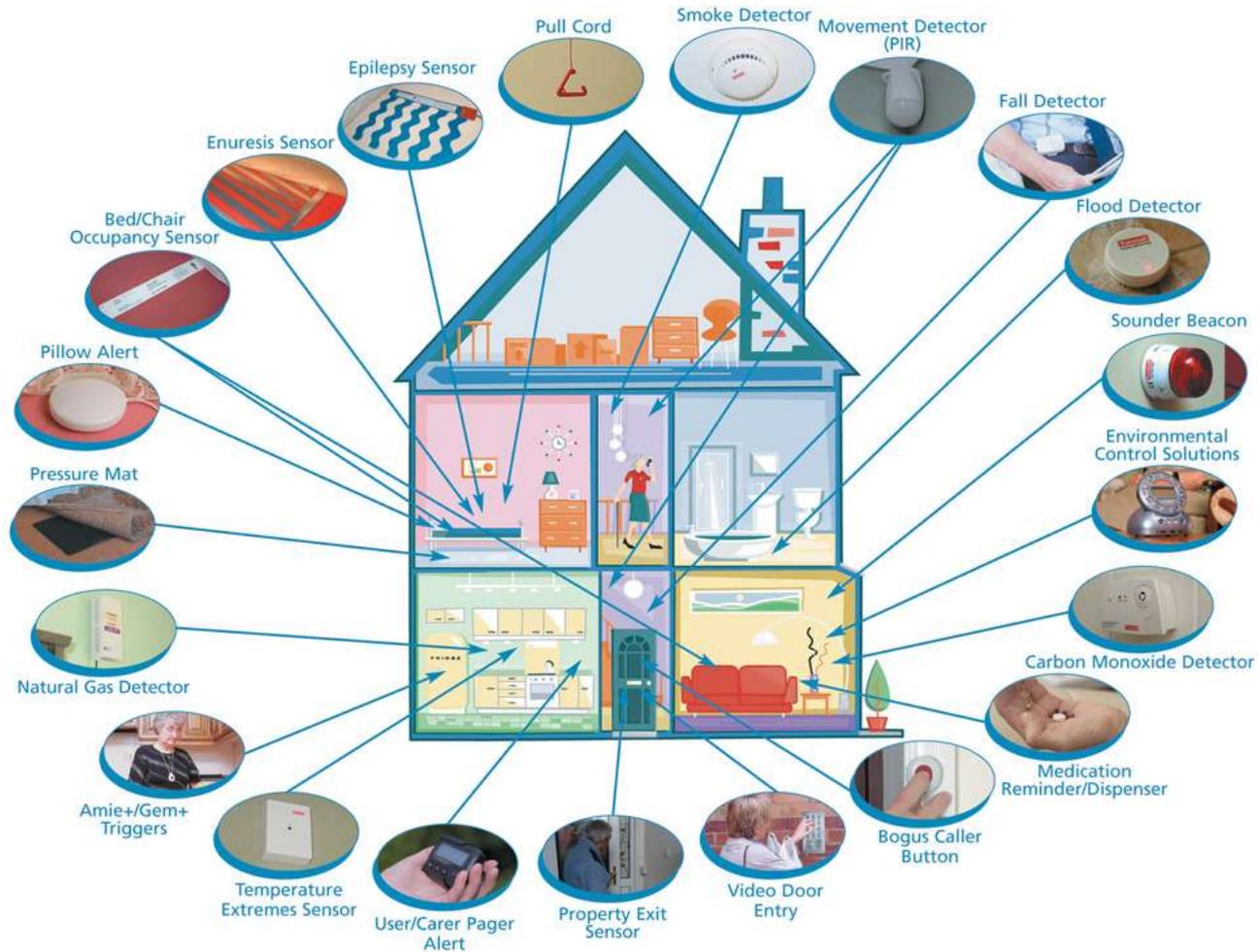
*monitors/integrates conditions of various systems for optimization and alerting, ...*



# sensors

## smart building: the human side

monitors/integrates conditions of various systems for optimization and alerting, ...



# sensors

## smart city

critical infrastructures: energy, water, transportation (avoid congestion, state of bridges), waste management, ...



# sensors



smart  
refrigerator



smart  
building



**nanoscale, new materials**

⇒ low-power, low-cost, robust ... **ubiquitous**

**Internet of Things (IoT)**

"smart" monitoring for environment, health care, agriculture/farming, logistics

⇒ **sensors beyond p, T**

detection, quantification and monitoring of more complex analytes

gases, ions, organic molecules, biomarkers, ...

e.g.: **continuous glucose monitoring (diabetes)**

Dexcom, reading on phone/watch

smart  
city



- **general aspects on sensing**

*sensitivity, specificity*

*overview of transducers*

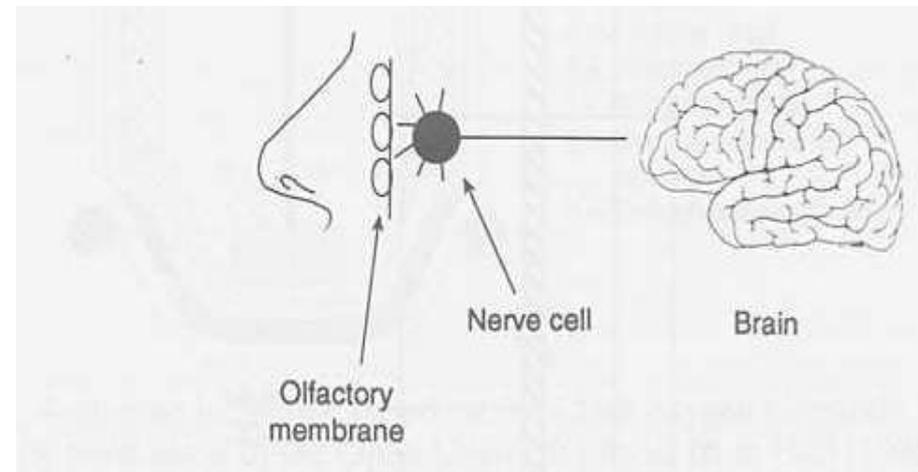
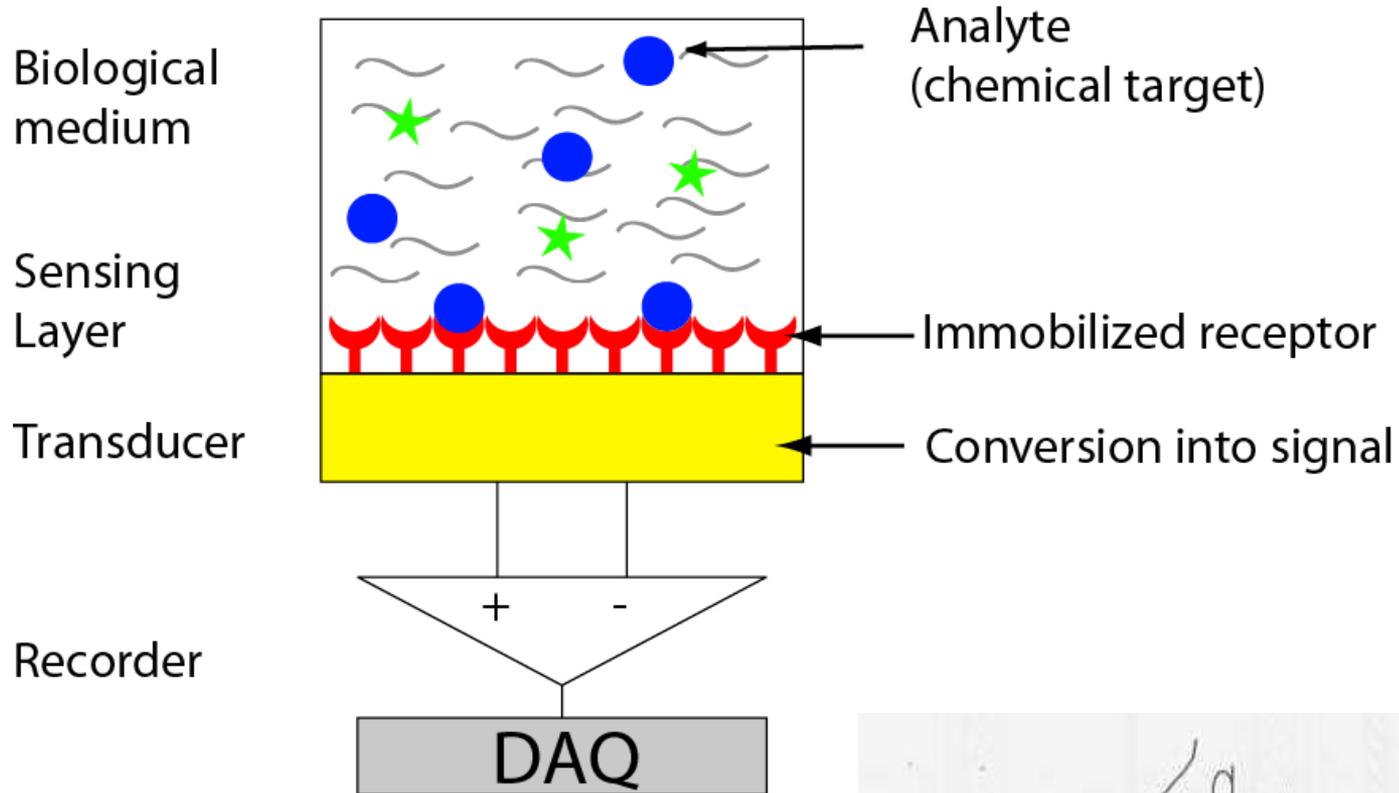
- **field effect transistors (FETs) as charge sensors**

*MOSFET, graphene and GFET*

### **Examples**

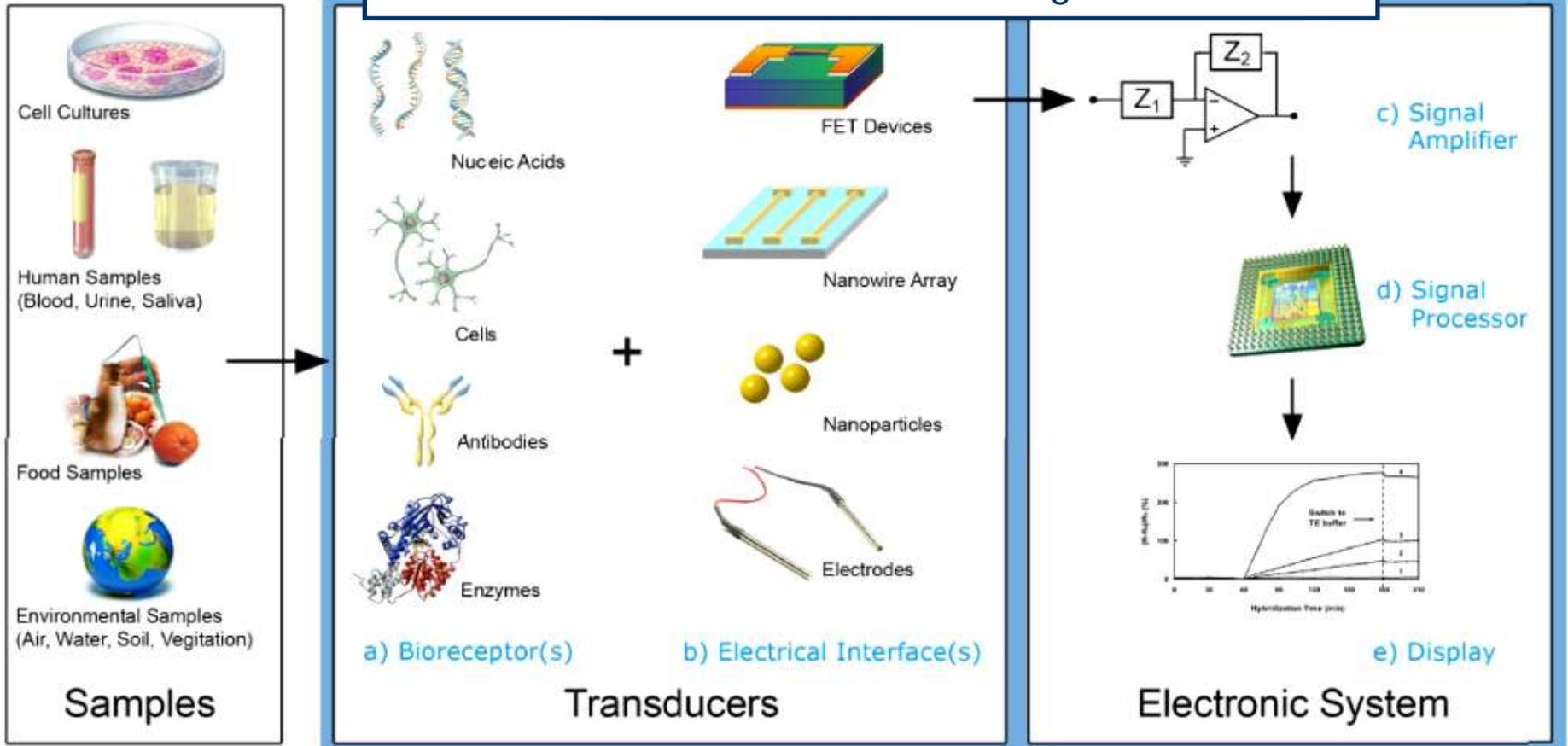
- Ion sensitive field-effect transistors (ISFETs) for pH, ionic and biochemicals detection
- Nanopores for sequencing

# (biochemical-)sensing



# (biochemical-)sensing

*challenge: controlled conversion of (bio-)chemical signal into a well-defined electronic signal*

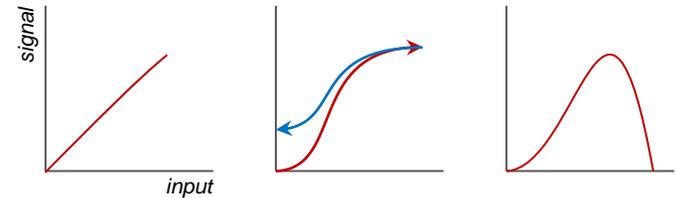


**competences ?**

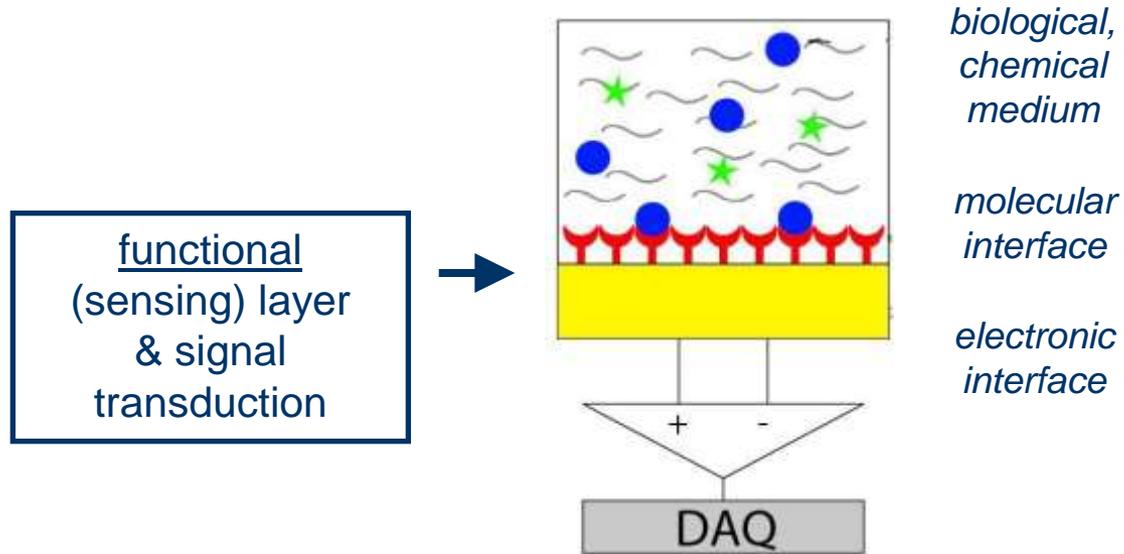
# (biochemical-)sensing

## Characteristics of a sensor

- **Transfer function**, nonlinearity
- **Sensitivity**: typ., derivative of transfer function
- **Selectivity**: response exclusively to changes in specific target analyte concentration
- **SNR, low background**: low noise, with ability for correction (differential measurements)
- **Dynamical range**
- **Response dynamics**: rapid response and recovery
- **Hysteresis** : signal (in)dependent of prior history of measurements (*nanoscale devices: nanotubes, graphene, etc: interfacial polarisation effects at contacts*)
- **Long-term Stability**: not subject to fouling, poisoning, or oxide formation that interferes with signal; prolonged stability of biological molecule
- **Simple calibration** (standards)
- **Size, cost, power consumption**
- **Operating conditions** (pH range, temperature, ionic strength), **biocompatibility**



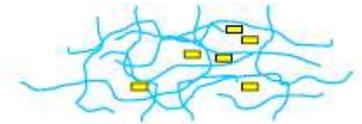
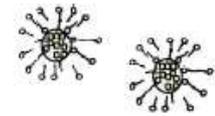
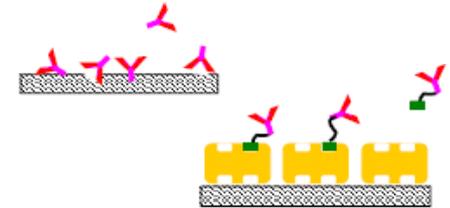
# sensing



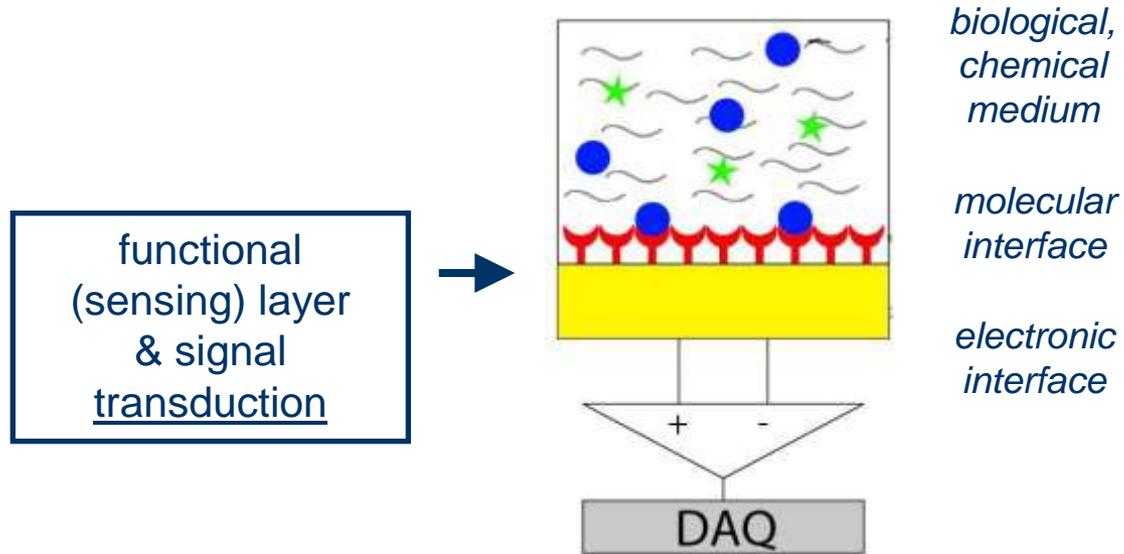
# functional layer

## Functionalization & immobilization techniques

- **adsorption** (non-specific)  
weak bonding; susceptible to pH, temperature, ionic strength, and substrate variations; simple but short lifetime
- **encapsulation**: place biomaterial behind a **membrane permeable** to some materials only (e.g. porous graphene membrane)  
limits contamination, relatively stable towards changes in pH, etc..
- **embedding** of a the sensing biological component in a **matrix** such as a gel or a polymer film  
stable but may limit diffusion of sample towards biodeceptor; activity of biomolecule may be limited also due to gel mesh
- **covalent attachment**  
direct or zero-length cross-linking, strong binding, can limit activity depending on bonding



# sensing



# transduction: electrical

## Transduction

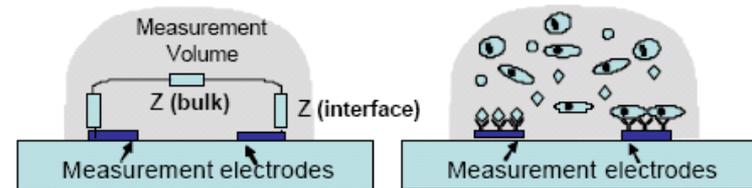
- **electrical & electrochemical**  
*direct measurement of **current** through a molecule for instance, molecular electronics; current monitoring through device while binding of sample*

**charge detection** – e.g. ions, charge species; pH meter; ionic concentration variation, e.g **ISFETs**

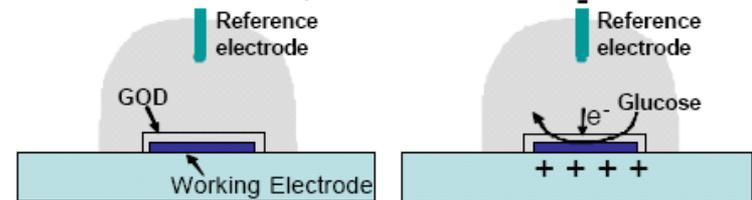
**impedance spectroscopy;**  
*voltammetry or amperometry: cycle a potential to an electrochemical cell with an oxidizing substance)*

### Electrical Detection

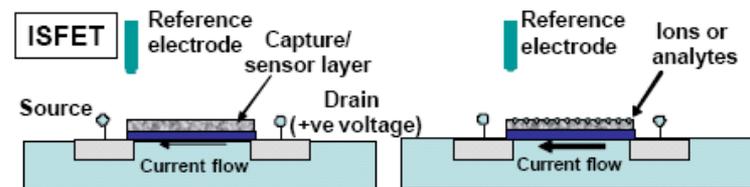
#### Conductometric Detection



#### Amperometer Detection



#### Potentiometric Detection



# example: ISFETs

## ISFETs: ion-sensitive field-effect transistors

concept from the 70's

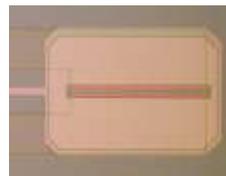
Bergveld, *IEEE Trans. Biomed. Eng* (1970)

Bergveld, *IEEE Sensor Conf.* (2003)

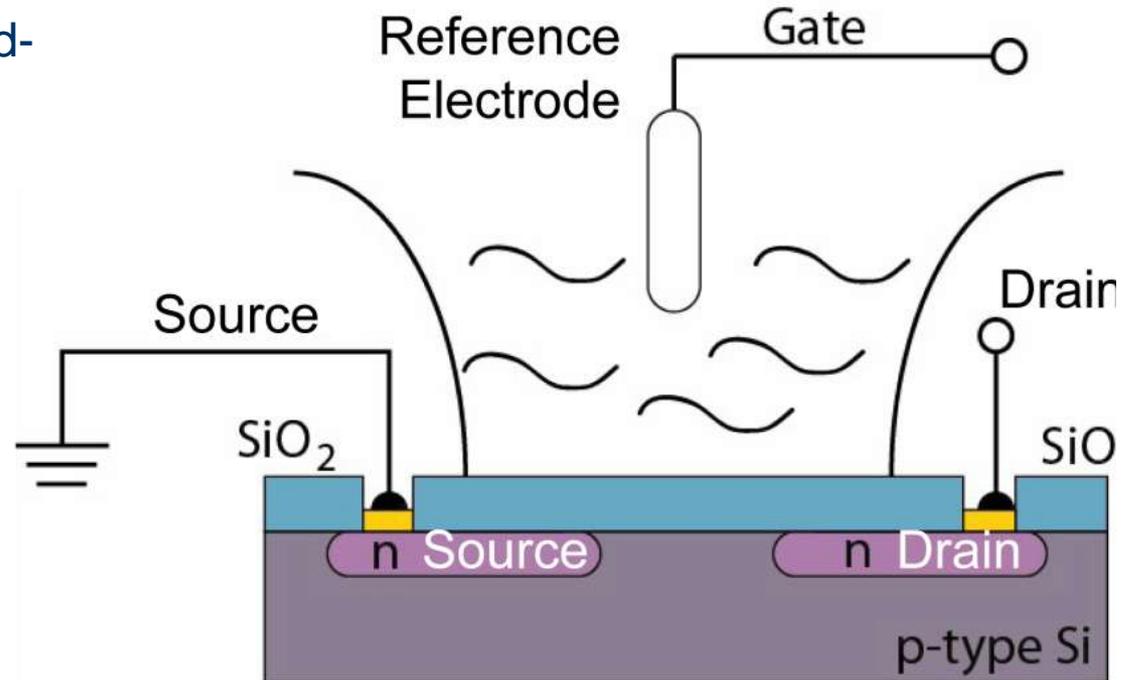
## pH sensors



Mettler-Toledo



Sentron

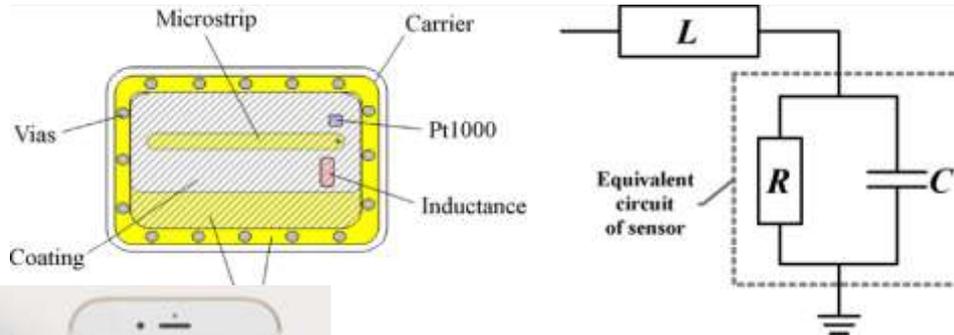


Endress+Hauser :CPS441 and CPS441D  
with integrated Ag/AgCl reference (needs a KCl reservoir )

# example: conductometric detection

## non-invasive glucose monitoring: impedance spectroscopy

- glucose variations affect electrical properties of erythrocytes membranes, and lead to variations of the electrolyte balance (in blood, cells and interstitial fluid)
- changes in interface polarisability of cells (Maxwell-Magner),
- typ. freq. 20-60MHz



**GlucoWatch® Monitor**



**Biovotion**  
*Solianis until 2011*



[www.gluco-wise.com](http://www.gluco-wise.com)



[www.dexcom.com](http://www.dexcom.com)

# transduction: mechanical

## Transduction

- **mechanical**  
mass (QCM - piezo, AFM),  
surface stress (AFM)
- **piezoelectric**  
vibration frequency shifted  
by mass adsorption at  
surface of device; QCM: at  
10MHz,  $4\text{ng cm}^{-2}\text{Hz}^{-1}$
- **calorimetric**  
heat produced or absorbed  
during biochemical  
reactions

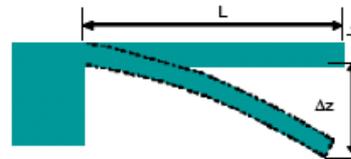
**AFM-based: cf e.g. Ch. Gerber et al.**



**Kavli Prize 2016  
in Nanoscience**

## Mechanical Detection

### Surface Stress Change Detection



$$\Delta z = 4 \left( \frac{l}{t} \right)^2 \frac{(1-\nu)}{E} (\Delta\sigma_1 - \Delta\sigma_2)$$

- $\Delta z$  = deflection of the free end of the cantilever
- $L$  = cantilever length
- $t$  = cantilever thickness
- $E$  = Young's modulus
- $\nu$  = poisson's ratio
- $\Delta\sigma_1$  change in surface stress on top surface
- $\Delta\sigma_2$  change in surface stress on bottom surface

### Mass Change Detection



$$f = \frac{1}{2\pi} \sqrt{\frac{k}{m}}$$

$$\Delta m = \frac{k}{4\pi^2} \left( \frac{1}{f_1^2} - \frac{1}{f_0^2} \right)$$

- $k$  = spring constant
- $m$  = mass of cantilever
- $f_0$  = unloaded resonant frequency
- $f_1$  = loaded resonant frequency



QCM: **Q-Sense**



cantilever: **Concentris**

# transduction: optical

## Transduction

- **optical** (absorption-, fluorescence-, luminescence-, internal reflection spectroscopy; **surface plasmon resonance** - SPR; light scattering)

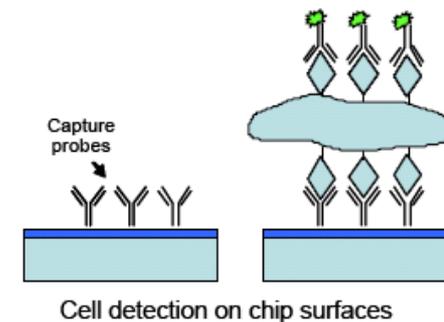
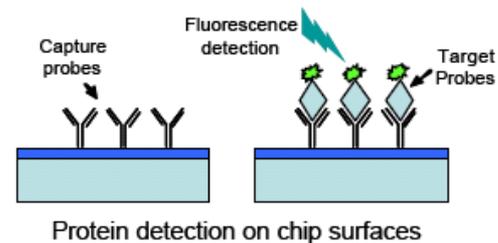
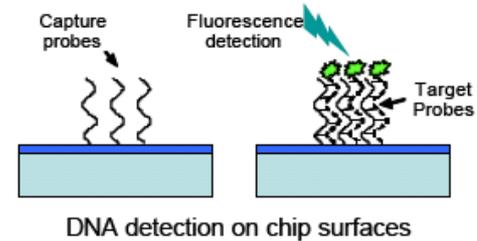


fluorescence: *Affymetrix*



SPR: *Biacore*

## Optical Detection



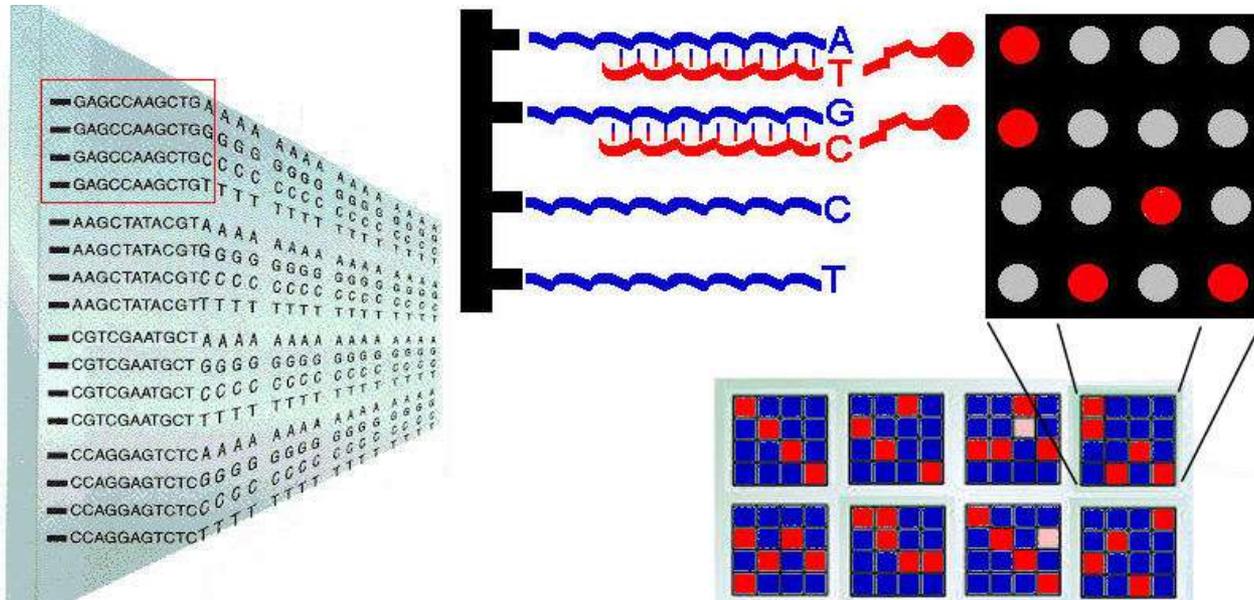
# example: fluorescence, DNA microarray

- Analyte:
- Recognition Molecule:
- Transduction:

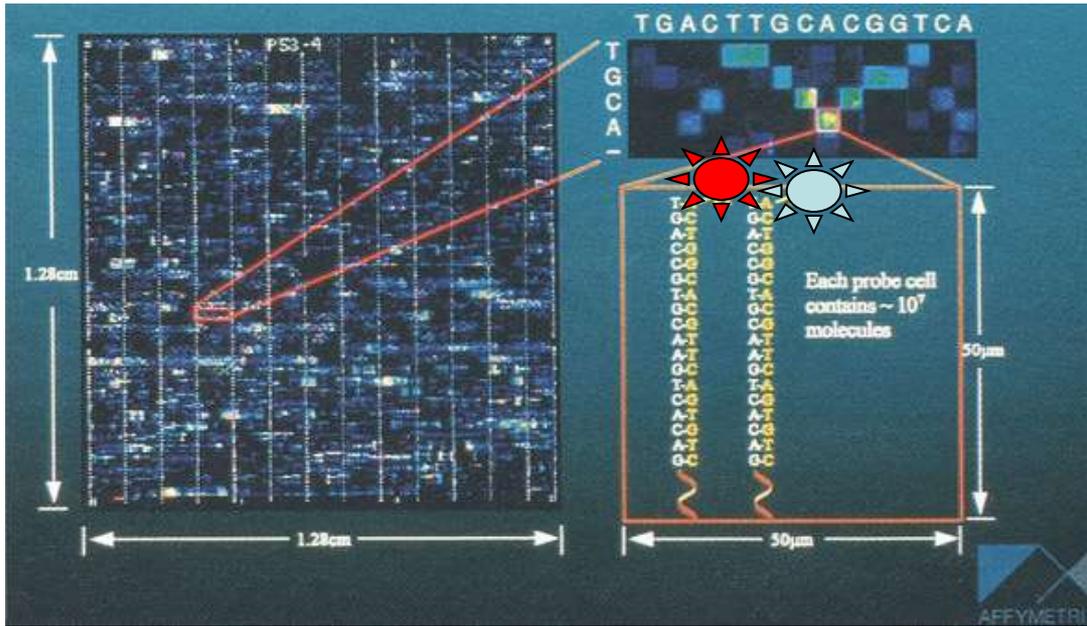
Labelled ss-DNA  
cDNA, mRNA  
Fluorescence



Affymetrix



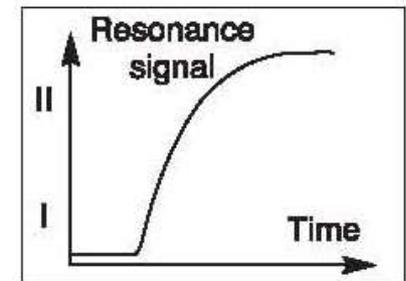
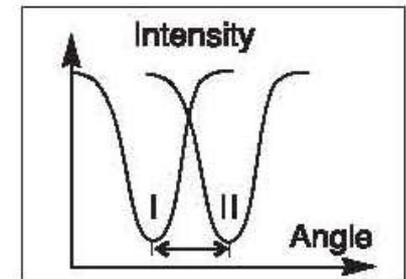
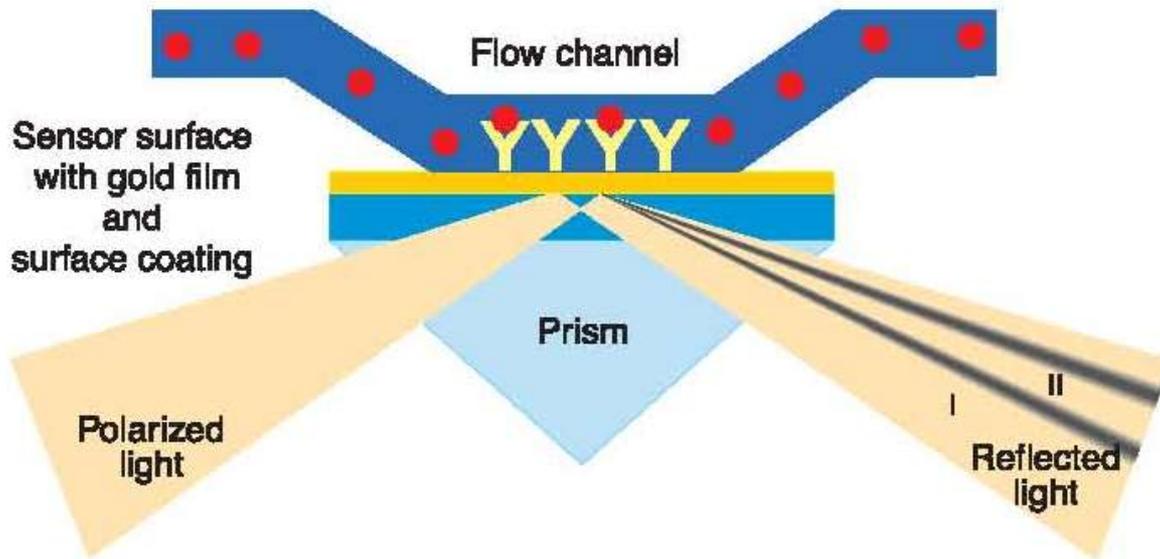
# DNA microarray



Gene-chip,  
Affymetrix

Probe molecules  
have to be labeled

# example: surface plasmon resonance (SPR)



**Sensorgram**

# plasmons: reminder

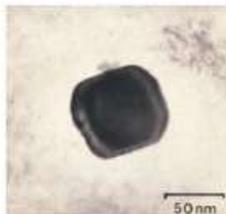
- **response of metals to optical fields**  
 plasma frequency  $\omega_p \sim 10^{15}$  Hz (visible)  
*collective oscillation of  $e^-$  in metal*

$$\omega_p = \sqrt{\frac{n_e e^2}{m^* \epsilon_0}}$$

**reflection**

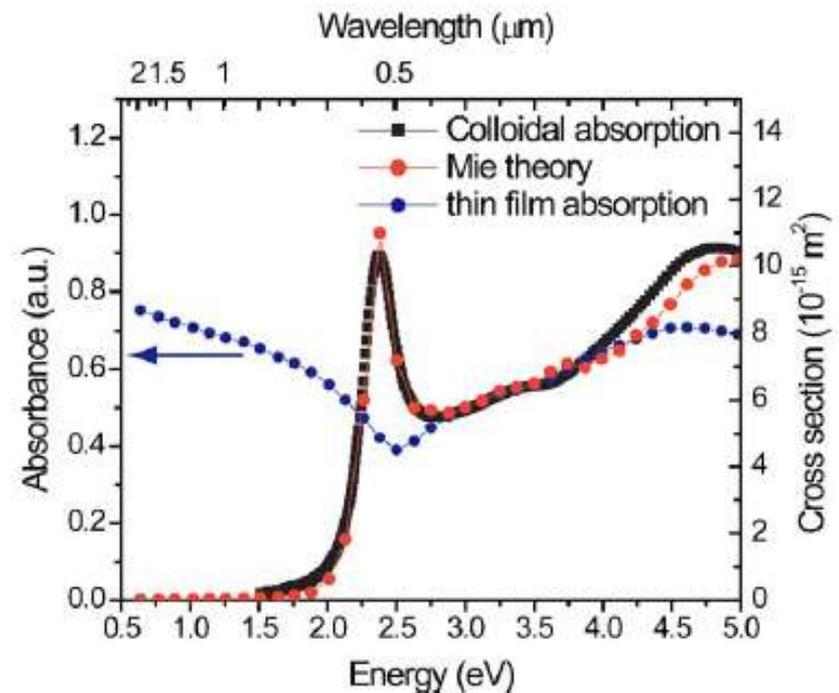


**transmission**



**Lycurgus cup**, 4th century A.D., late Roman  
*British Museum*

*SEM image of a typical nanocrystal embedded in the glass (British museum)*



- calc. spectra (Maxwell) for **thin film** and **30nm Au nanoparticle** (*classical electromagnetism*)
- measured spectrum of **30nm Au**

# plasmons

- **response of metals to optical fields**  
 plasma frequency  $\omega_p \sim 10^{15}$  Hz (visible)  
*collective oscillation of  $e^-$  in metal*

$$\omega_p = \sqrt{\frac{n_e e^2}{m^* \epsilon_0}}$$

- **plane-wave excitation of metal particle**  
 *$e$  confined in sphere diameter  $d \ll \lambda$*

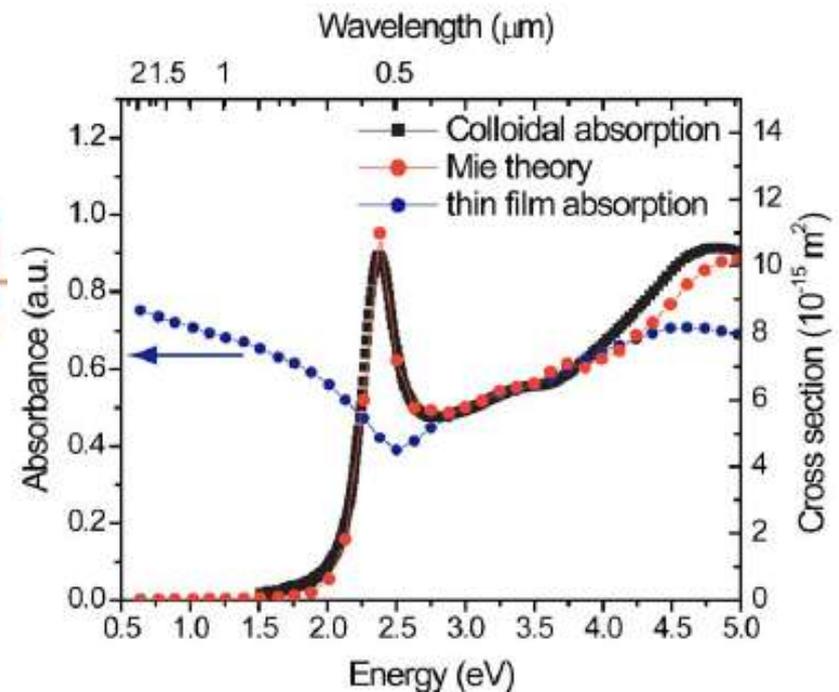
- in-phase motion of conduction  $e$   
 $\Rightarrow$  **polarization charges** at surface



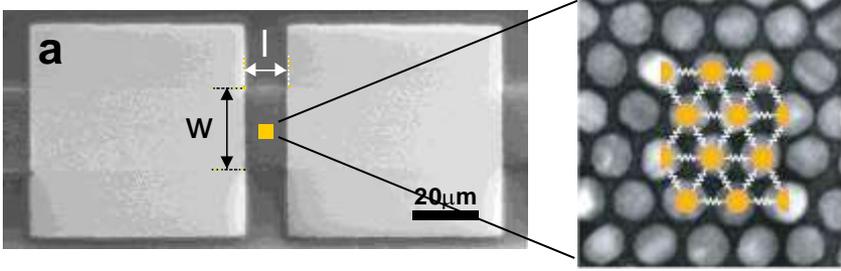
- pol. charge  $\Rightarrow$  restoring force  
**resonance at dipole plasmon freq**  
 *$\pi/2$  phase lag with driving field*

- **resulting dipolar field** (outside the particle)  
 $\Rightarrow$  enhanced absorption and scattering for em waves & enhanced near field at surface

- **NB: larger particles: retardation effects, higher order modes, dephasing**



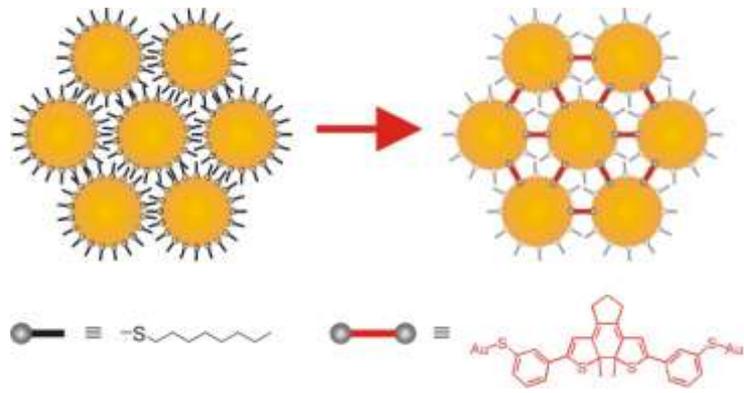
# Remember: NP arrays, light-controlled conductance switching



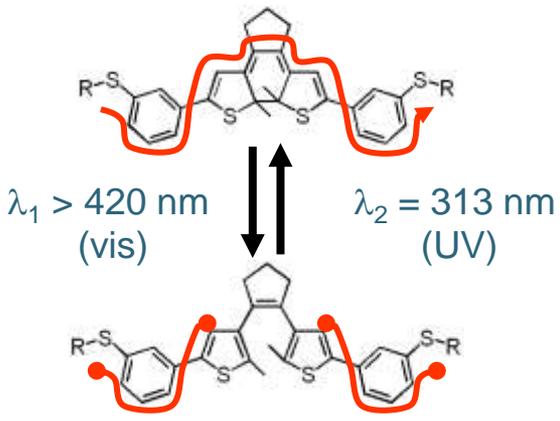
sheet resistance:  
 $R_{\square} = R \cdot w / l$

junction resistance  
 $R_J = (2/\sqrt{3}) \cdot R_{\square}$

$R_J = 1/G_J$

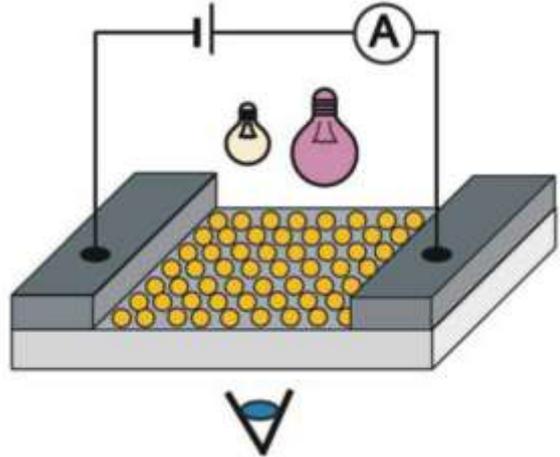


## light-controlled molecular switch

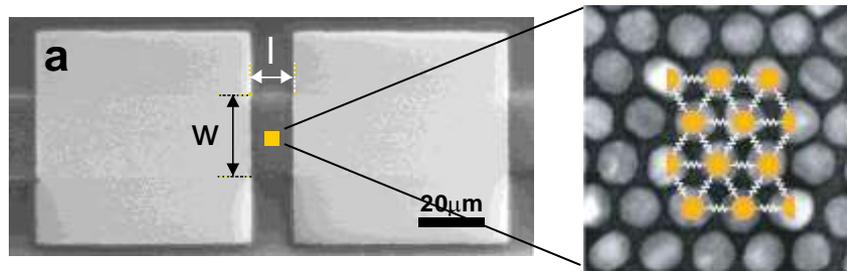


"ON" state  
 extended conjugation

"OFF" state  
 interrupted conjugation



# light-controlled conductance switching



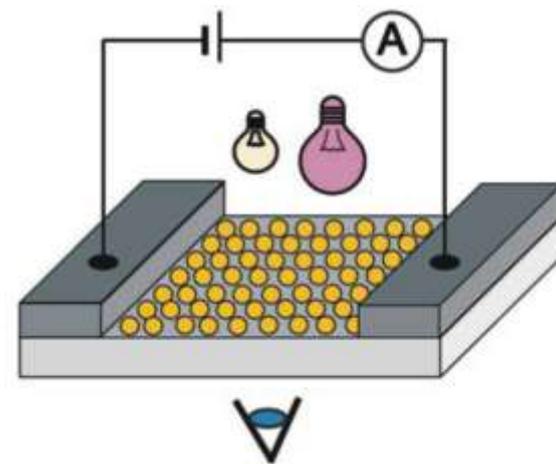
sheet resistance:

$$R_{\square} = R \cdot w / l$$

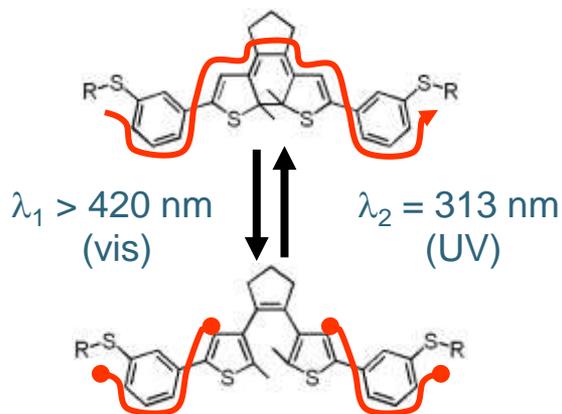
junction resistance

$$R_J = (2/\sqrt{3}) \cdot R_{\square}$$

$$R_J = 1/G_J$$

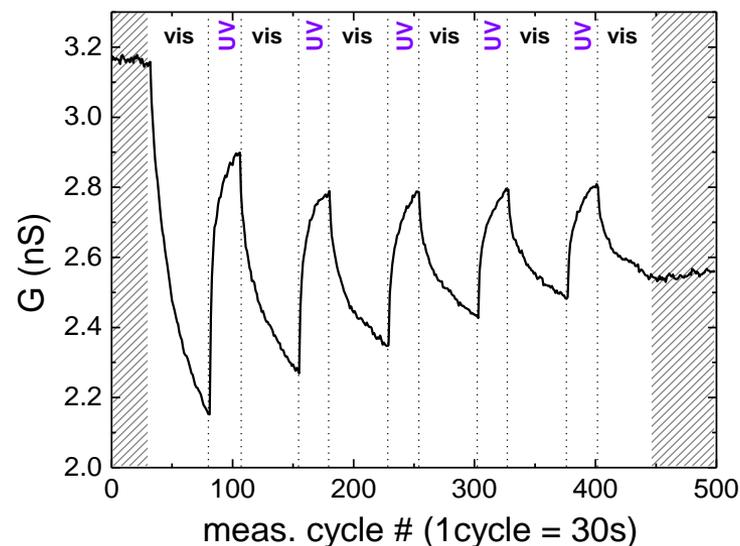


## light-controlled molecular switch



**"ON" state**  
extended  
conjugation

**"OFF" state**  
interrupted  
conjugation



# plasmon resonances in NP arrays

## optical spectroscopy (absorption)

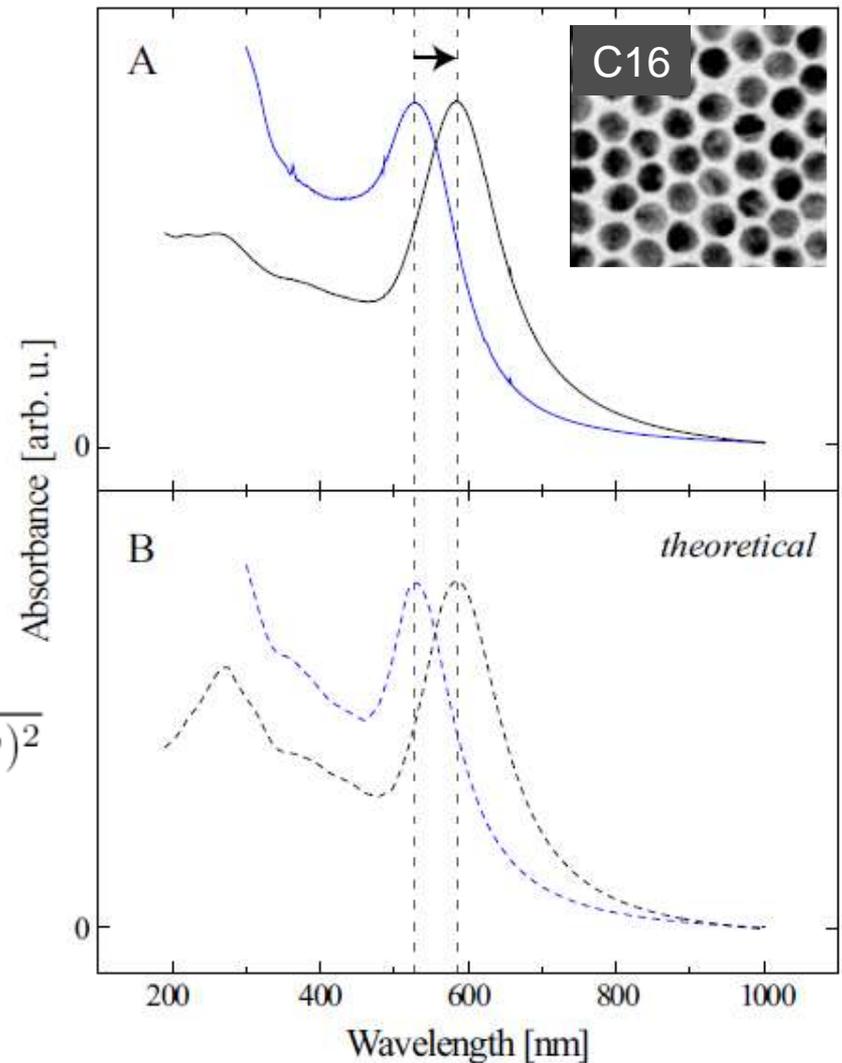
plasmon generated by E-field component of an irradiating EM wave

*C16-capped Au nanoparticles (10nm  $\varnothing$ )  
in solution (blue) and as an array (black)  
red shift of SPR due to array*

**absorption cross-section: Mie**  
(small particles, dipolar approx.)

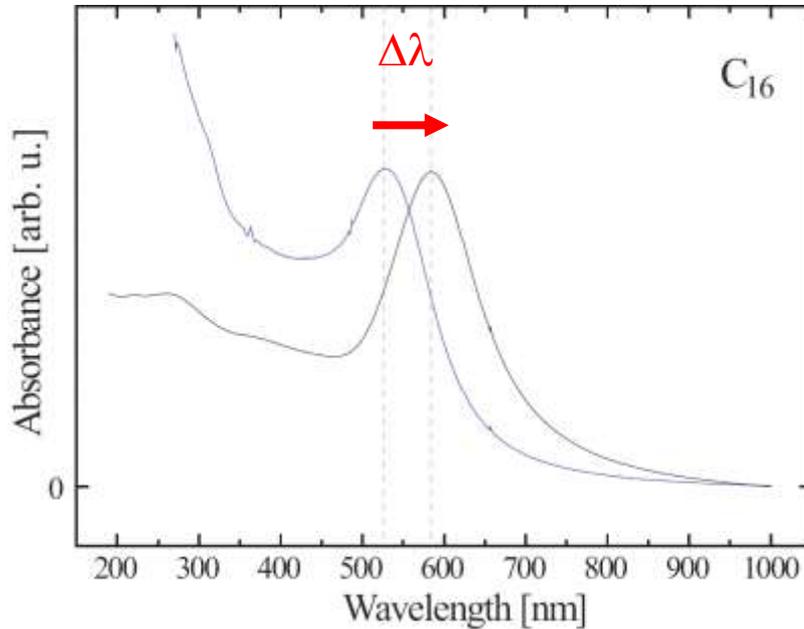
$$\sigma(\omega) = 12\pi \frac{\omega}{c} \epsilon_m^{3/2} R^3 \frac{\epsilon_2(\omega)}{[\epsilon_1(\omega) + 2\epsilon_m]^2 + \epsilon_2(\omega)^2}$$

medium permittivity  $\epsilon_m$   
nanoparticle  $\epsilon(\omega) = \epsilon_1(\omega) + i\epsilon_2(\omega)$

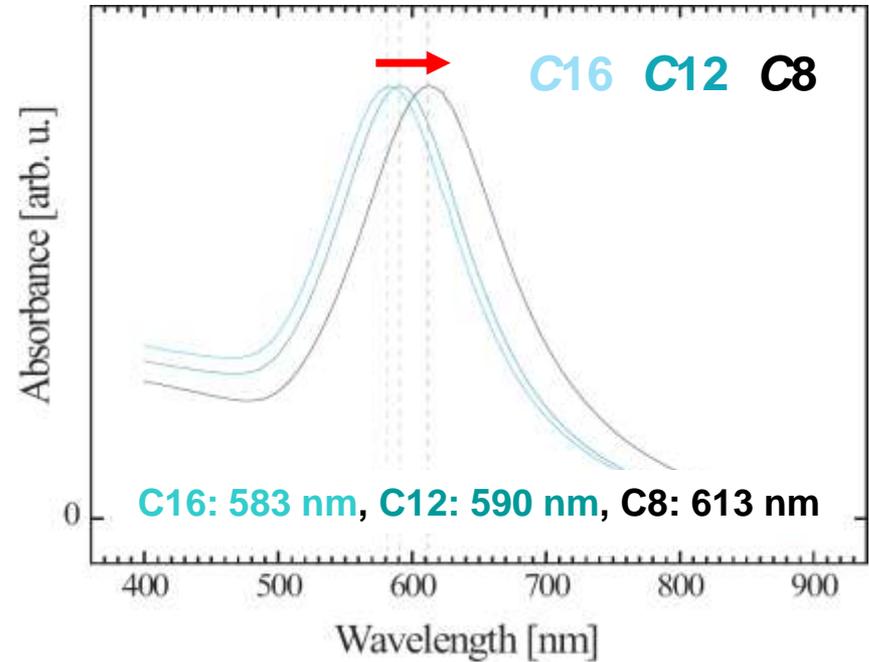


# plasmon resonances in NP arrays

*solution vs array*

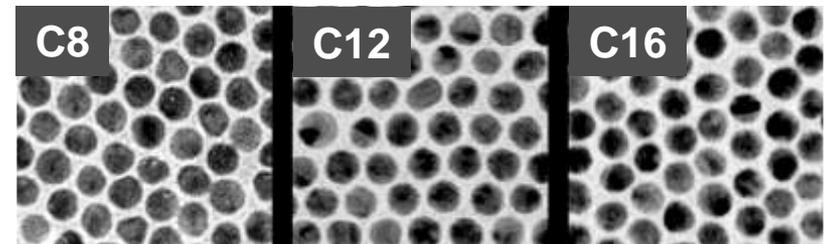


*different arrays*



## C16-capped nanoparticles

in **solution (blue)** and as an **array (black)**,  
**red shift** of surface plasmon resonance:  
526 nm to 583 nm.



# characterizing plasmon resonances

**absorption cross-section: Mie**  
(small particles, dipolar approx.)

$$\sigma(\omega) = 12\pi \frac{\omega}{c} \varepsilon_m^{3/2} R^3 \frac{\varepsilon_2(\omega)}{[\varepsilon_1(\omega) + 2\varepsilon_m]^2 + \varepsilon_2(\omega)^2}$$

nanoparticle permittivity: Drude-Lorentz-Sommerfeld

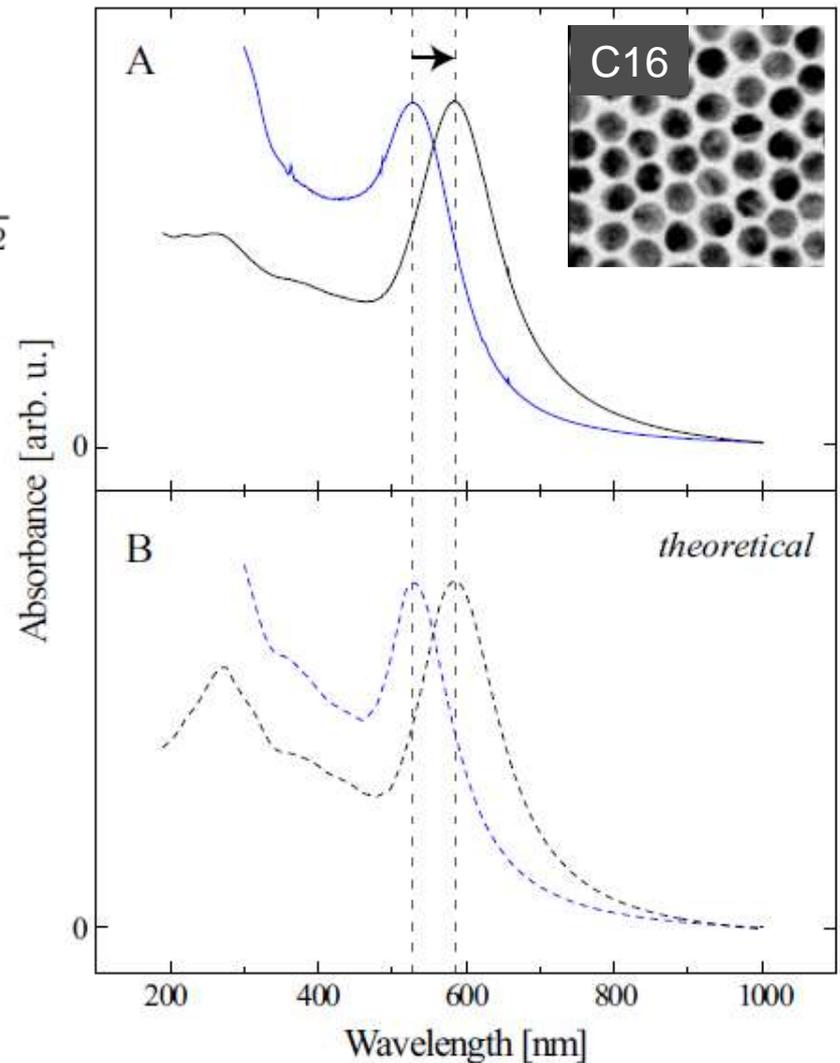
$$\varepsilon(\omega) = 1 - \frac{\omega_p^2}{\omega(\omega + i\Gamma)} \quad \omega_p = \sqrt{\frac{n_0 e^2}{\varepsilon_0 m_e}}$$

$$\varepsilon_1(\omega, R) = 1 - \frac{\omega_p^2}{\omega^2 + \Gamma^2(R)} + \varepsilon_{1,\text{core}}$$

$$\varepsilon_2(\omega, R) = \frac{\omega_p^2 \Gamma(R)}{\omega(\omega^2 + \Gamma^2(R))} + \varepsilon_{2,\text{core}}$$

$$\Gamma(R) = \frac{v_F}{l_\infty} + A \frac{v_F}{R} \quad \text{damping constant (radius dep.)}$$

medium permittivity  $\varepsilon_m$   
nanoparticle  $\varepsilon(\omega) = \varepsilon_1(\omega) + i\varepsilon_2(\omega)$



# characterizing plasmon resonances

**absorption cross-section: Mie**  
(small particles, dipolar approx.)

$$\sigma(\omega) = 12\pi \frac{\omega}{c} \varepsilon_m^{3/2} R^3 \frac{\varepsilon_2(\omega)}{[\varepsilon_1(\omega) + 2\varepsilon_m]^2 + \varepsilon_2(\omega)^2}$$

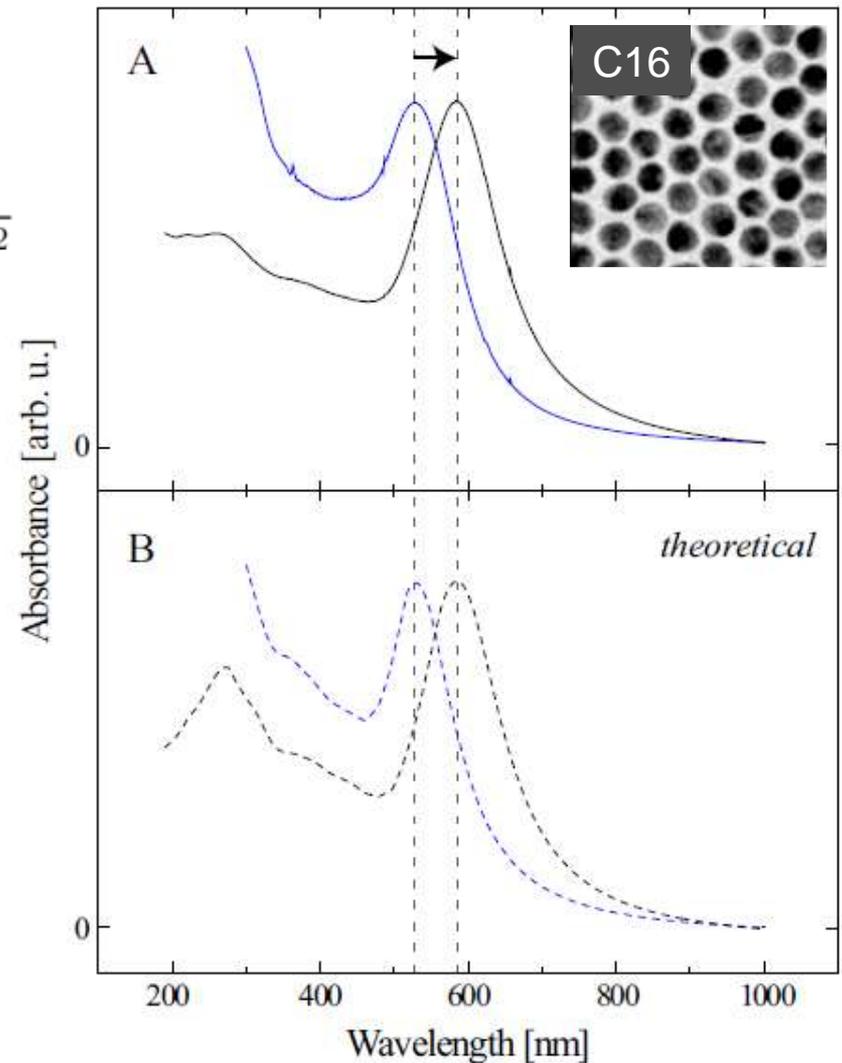
$$\propto \frac{1}{(\omega - \omega_M)^2 + (\Gamma/2)^2} \quad \omega_M = \frac{\omega_p}{(1 + 2\varepsilon_m)^{1/2}}$$

**NB**

in **solution**: dilute system, Mie ok

as **array** interaction between neighboring nanoparticles, red-shift

⇒ **effective medium permittivity**  
*Maxwell-Garnett*



# optical absorption

in **solution**: dilute system, Mie ok

**array**: confined system, interaction between neighboring nanoparticles

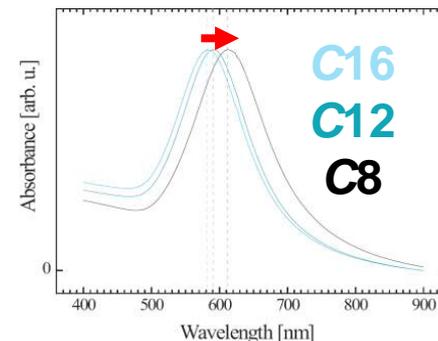
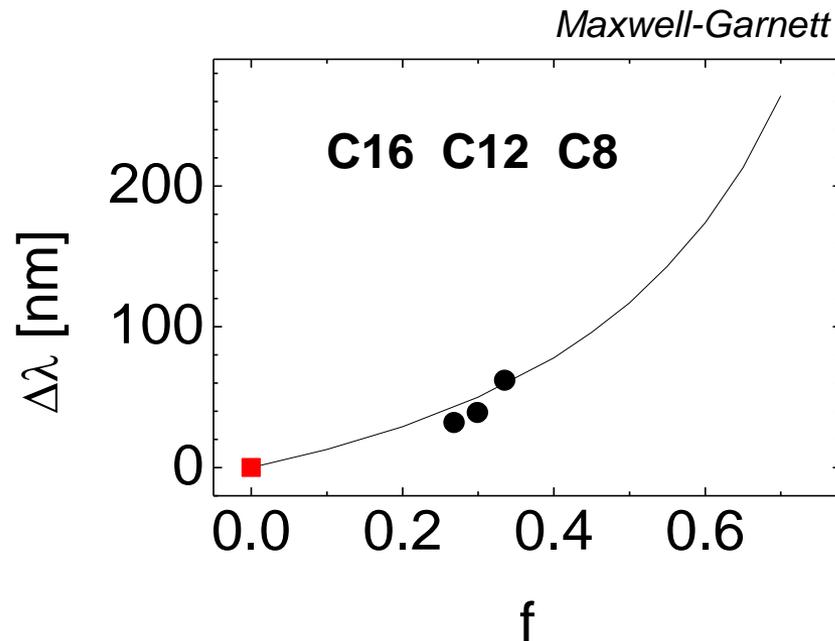
⇒ **effective medium permittivity**  
*Maxwell-Garnett*

$$\varepsilon_{eff}(\omega) = \varepsilon_m \frac{1 + 2f\Lambda}{1 - f\Lambda} \quad \Lambda = \frac{\varepsilon(\omega) - \varepsilon_m}{\varepsilon(\omega) + 2\varepsilon_m}$$

filling factor  $f = V_{clusters}/V_{total}$

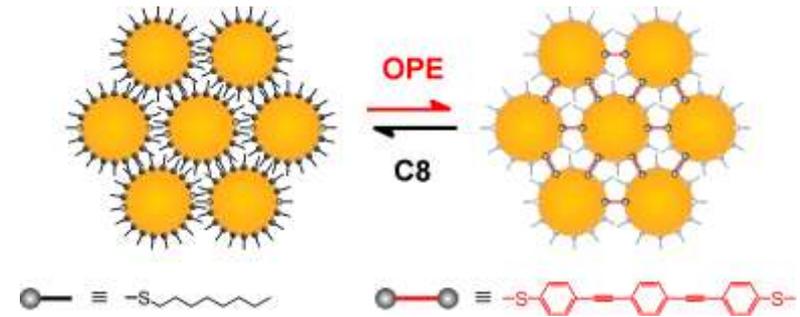
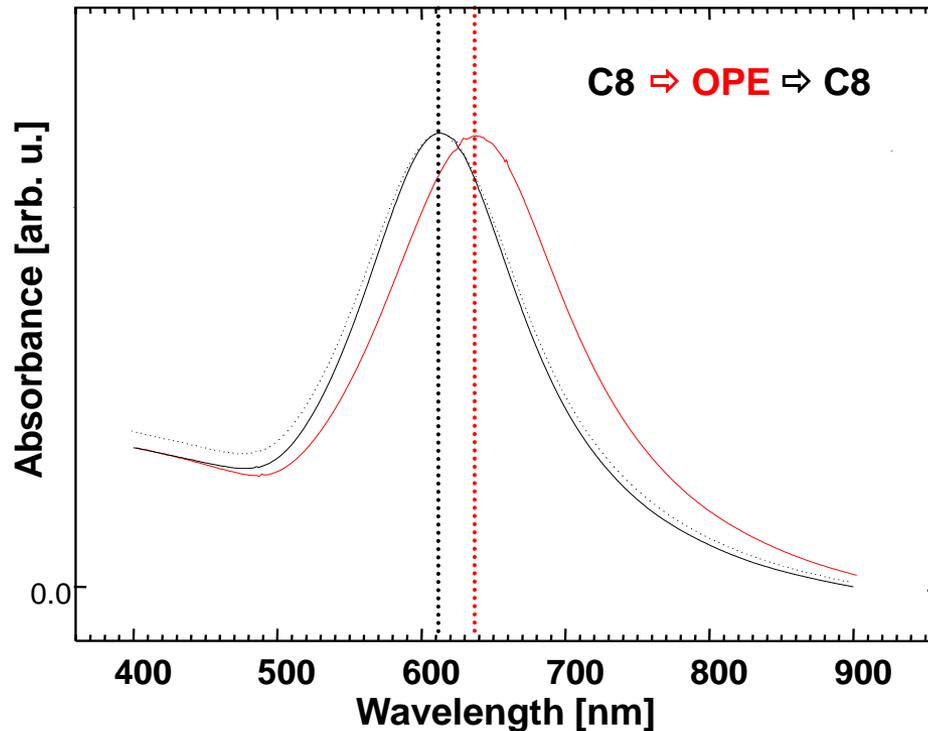
**Resonance condition**  $\varepsilon_1(\omega_{sp})(1 - f) + \varepsilon_m(2 + f) = 0$

*Mie: f=0*  $\varepsilon_1 + 2\varepsilon_m = 0$



# plasmon resonances shift during molecular exchange

## plasmon resonance for array during exchange



$$\Delta\lambda \approx 20\text{nm} \Leftrightarrow \Delta\epsilon \approx 0.5$$

$$\epsilon_{\text{C8}}=1.9-2.2^{(1)}, \epsilon_{\text{OPE}}=3.1-3.9^{(2)}$$

⇒ **exchange efficiency**  
**20% to 40%**

*NB: partial exchange ensures stability of array*

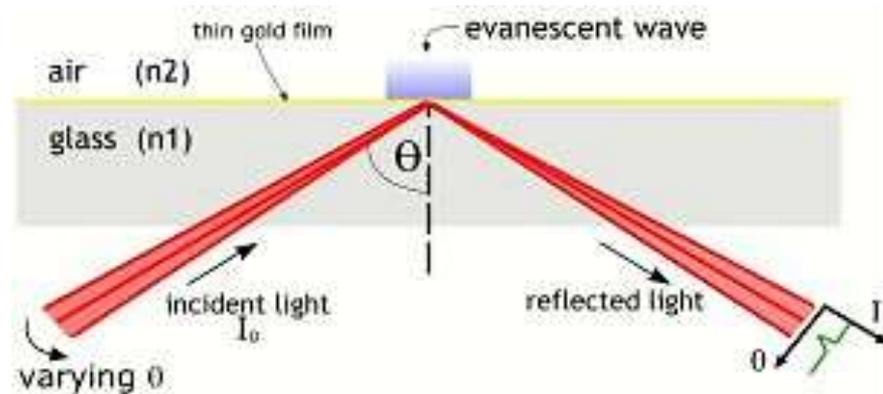
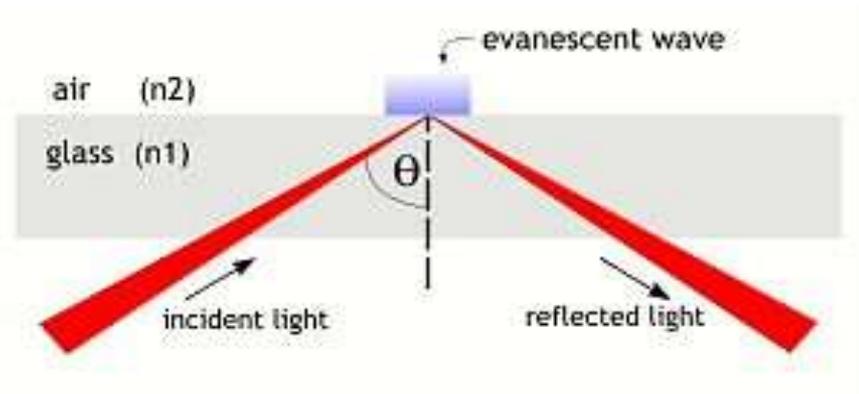
**plasmon resonance:  
very sensitive to  
surface modification**

(1) G. Whitesides et al., APL, 1998.  
(2) J. Stapleton et al., Langmuir 2003.

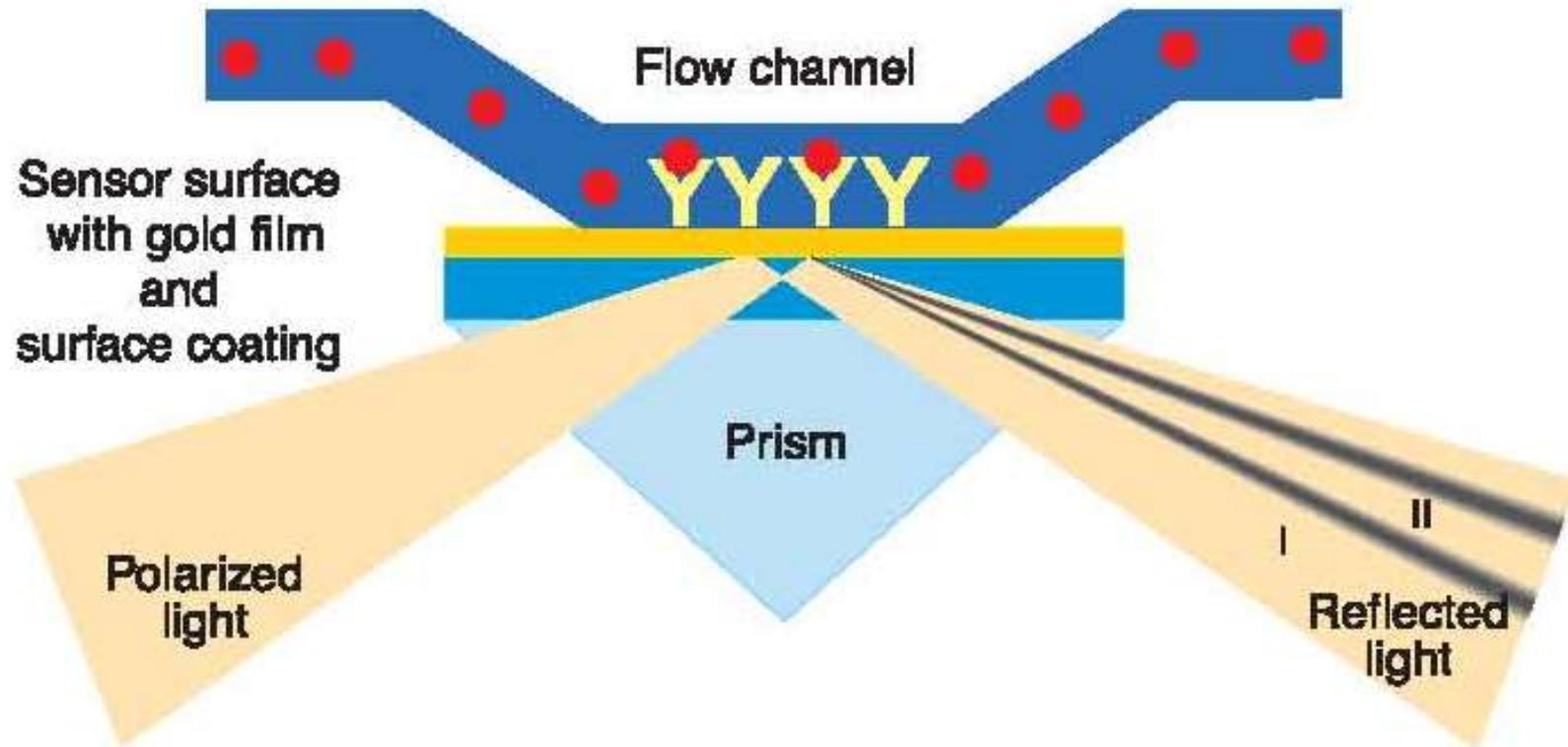
# sensing using surface plasmon resonance

## plasmon in thin films

- TIR above critical angle  $\theta_c$   
(Snell's law:  
 $n_i \cdot \sin(\theta_i) = n_t \cdot \sin(\theta_t)$   
 $\sin(\theta_c) = n_t/n_i$ ,  $n_i > n_t$ )
- when plasmon induced in metallic thin film (proper incidence angle, thus resonance), the reflected intensity shows a drop



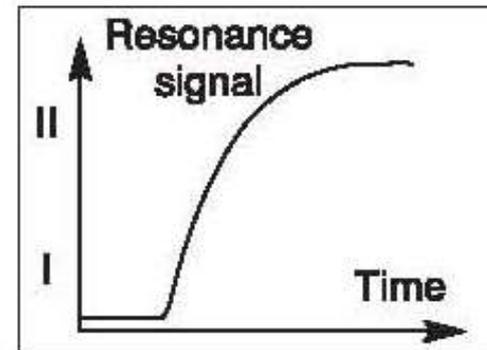
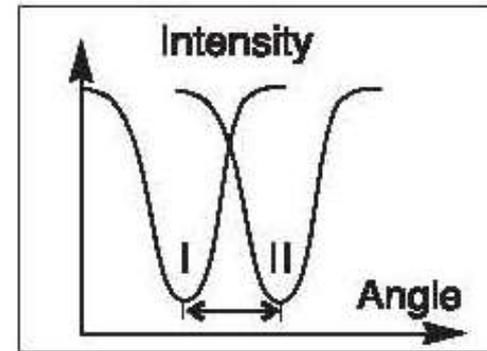
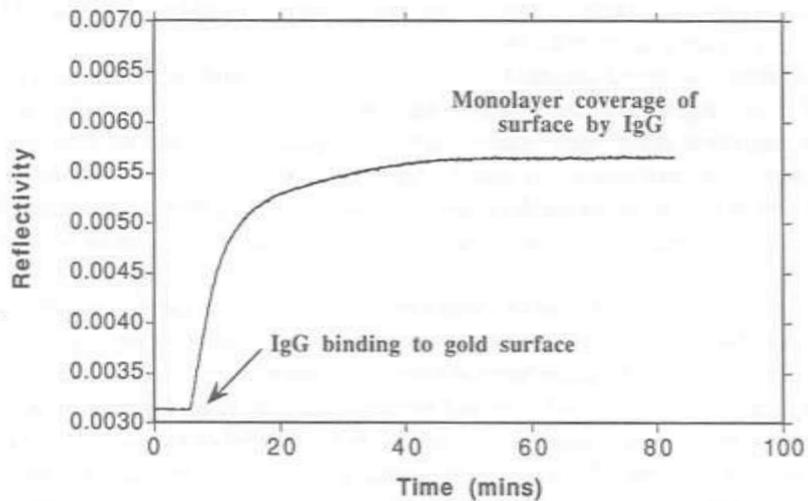
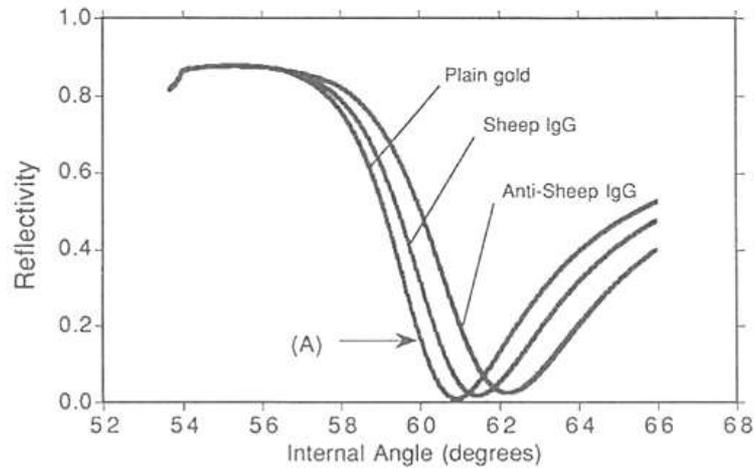
# surface plasmon resonance (SPR)



- SPR angle shift 0.12 °
- Change in protein surface concentration 1 ng/mm<sup>2</sup>
- Change in bulk refractive index 0.001

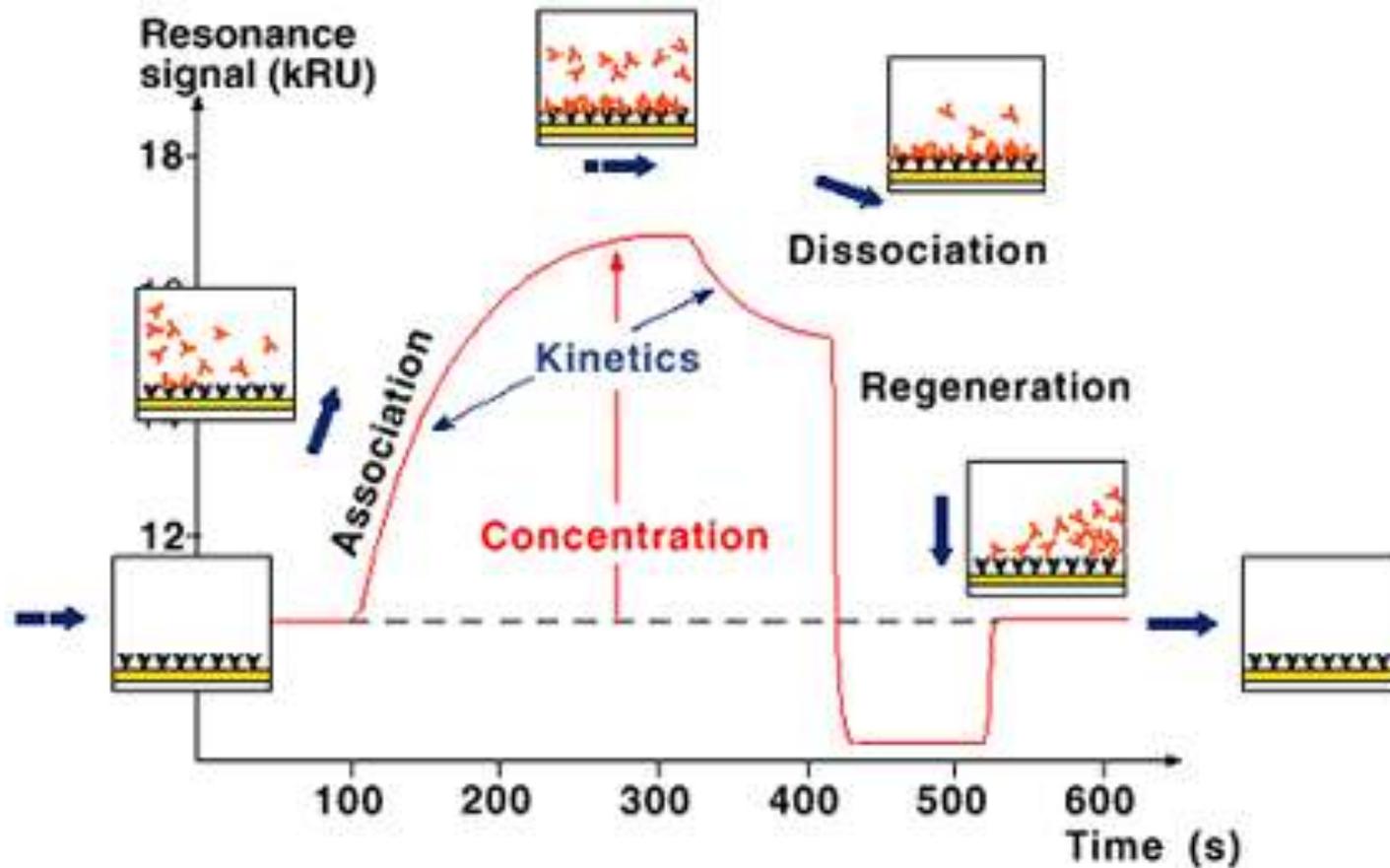
# surface plasmon resonance (SPR)

reflectivity vs angle for three different surface states



Sensorgram

# surface plasmon resonance (SPR)



**drawbacks:** upscalability, integration

- **general aspects on sensing**  
*sensitivity, specificity*  
*overview of transducers*
- **field effect transistors (FETs) as charge sensors**  
*MOSFET, graphene and GFET*

### **Examples**

- Ion sensitive field-effect transistors (ISFETs) for pH, ionic and biochemicals detection
- Nanopores for sequencing

# FETs for charge sensing

**GOAL: specific detection of biochemicals**  
*pH, ionic species, mRNA, DNA, proteins, ...*

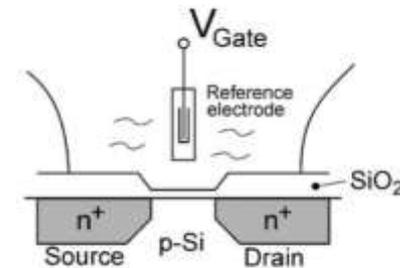
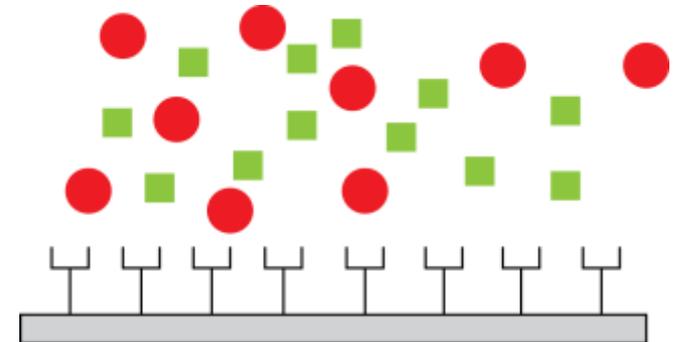
## Requirements

- label-free, multi target sensor,
- quantitative
- upscalable, dense integration: Si-based
- portable, small volume, low cost, low-drift
- implantable, biocompatible

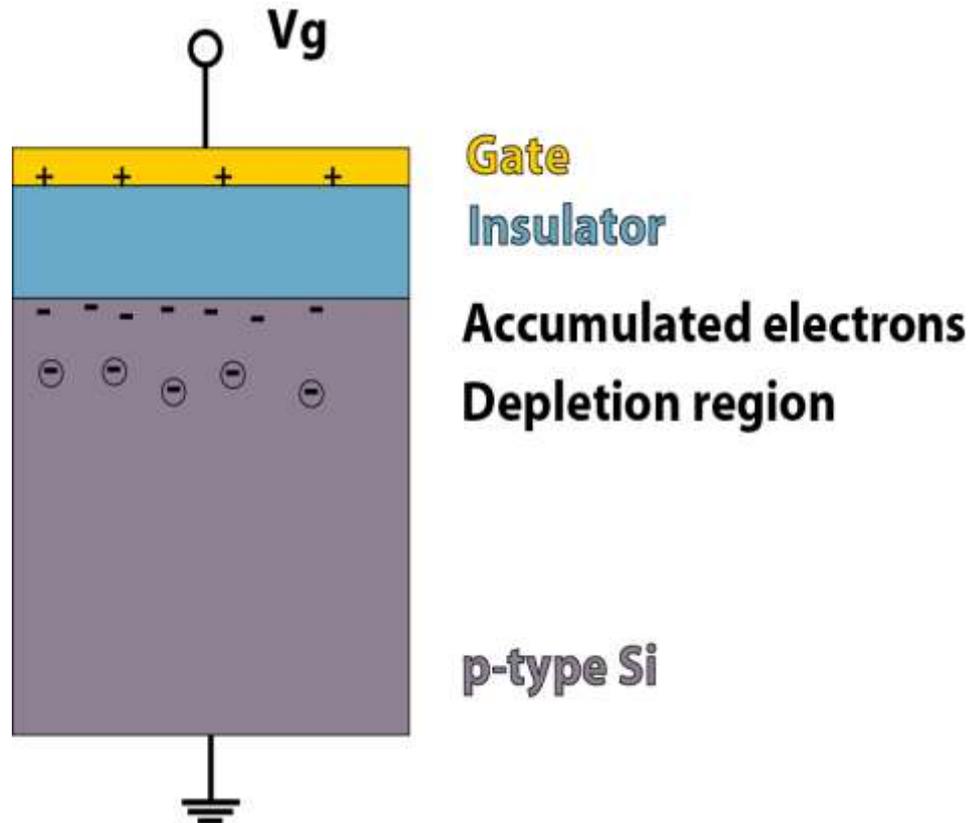
⇒ ***point of care and home diagnostics, implants, drug screening***

⇒ **ISFETs: ion-sensitive field-effect transistors ?**  
*detection of charged species, concept from the 70's*

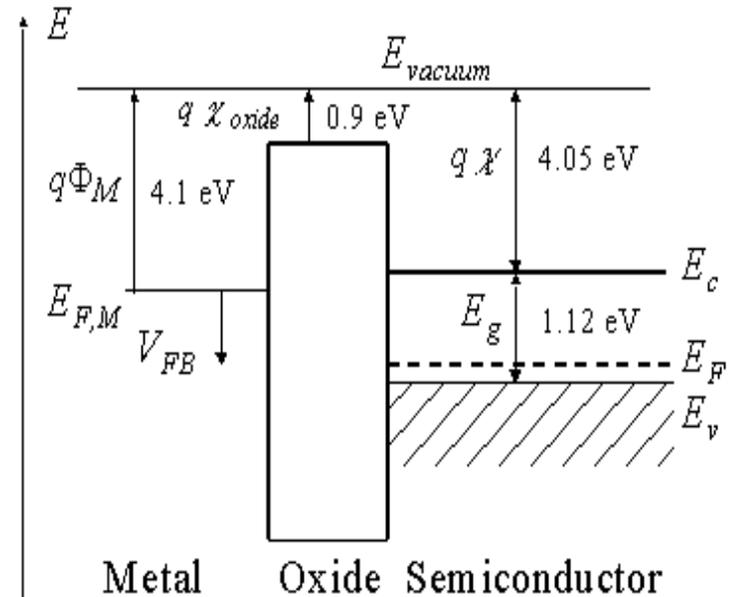
***Transducer of chemical reactions in electrical signals***



# brief reminder: MOS capacitor and MOSFET



energy band diagram



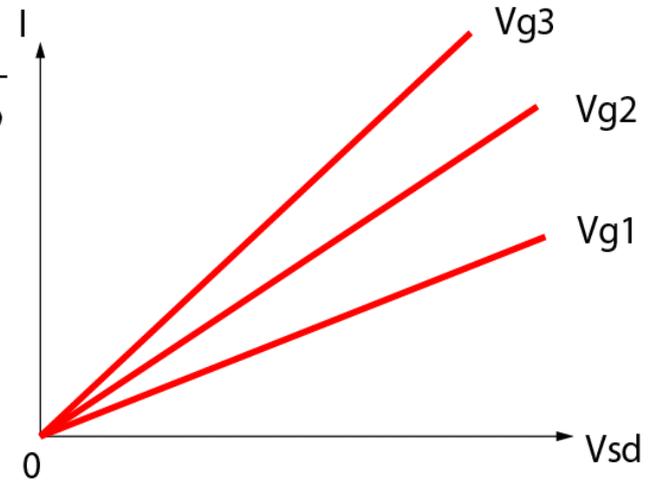
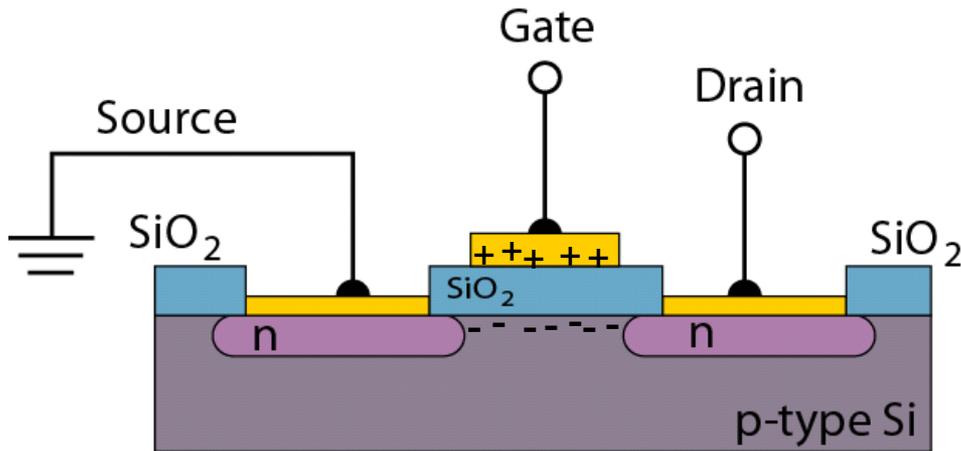
- Workfunction metal and semiconductor
- Interface charge: trapped oxide charge, mobile ionic charge, interface trapped charge

$V_{th}$  depends on  $C_{ox}$ , the semiconductor ( $n_i$ ) and doping ( $N_A$ )

# MOSFET

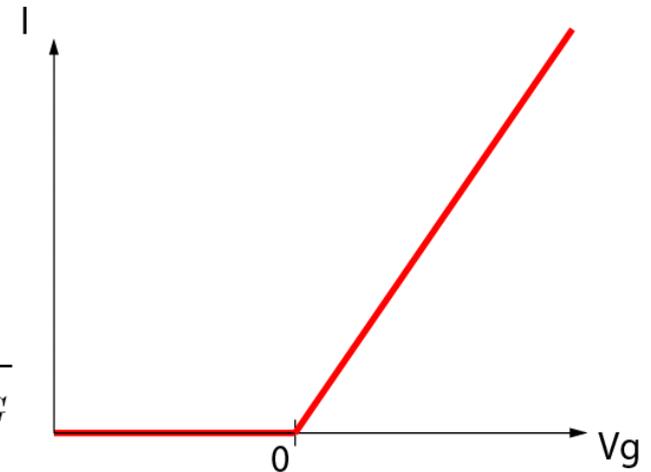
conductance

$$G_{SD} = \frac{dI}{dV_{SD}}$$



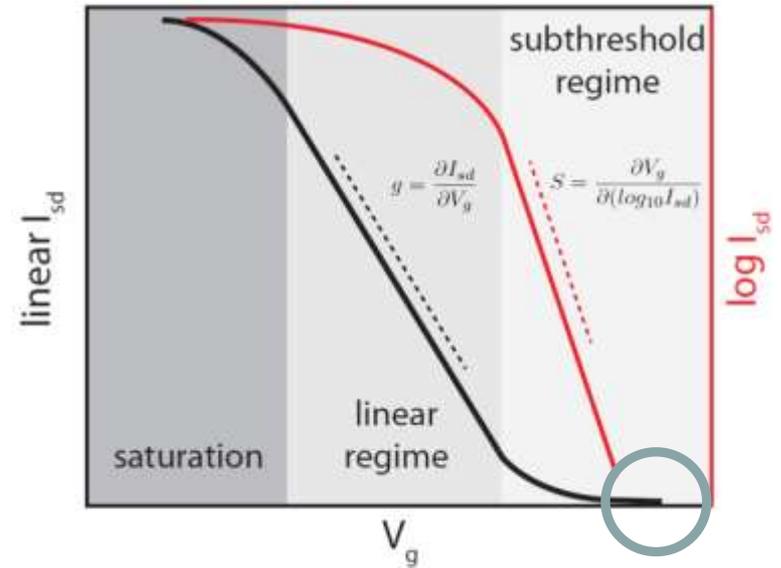
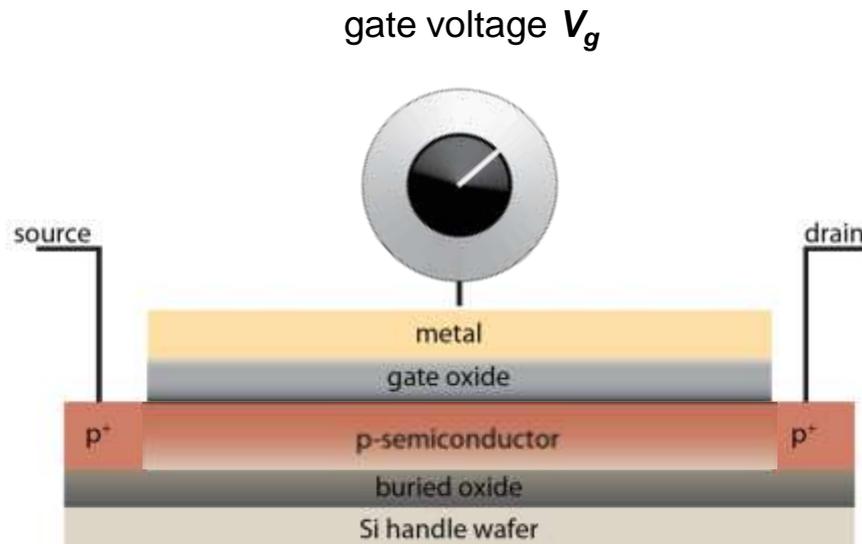
transconductance

$$G_{transc} = \frac{dI}{dV_G}$$



# MOSFET

*transfer characteristics (transconductance)*



$$I_{sd} = \mu C_{ox} \frac{W}{L} (V_g - V_{fb}) V_{sd}$$

# Gas Sensitive MOSFET

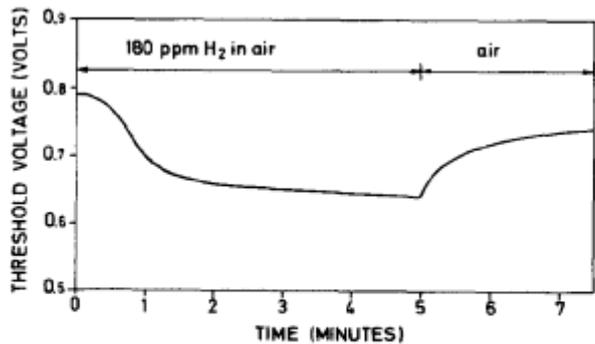
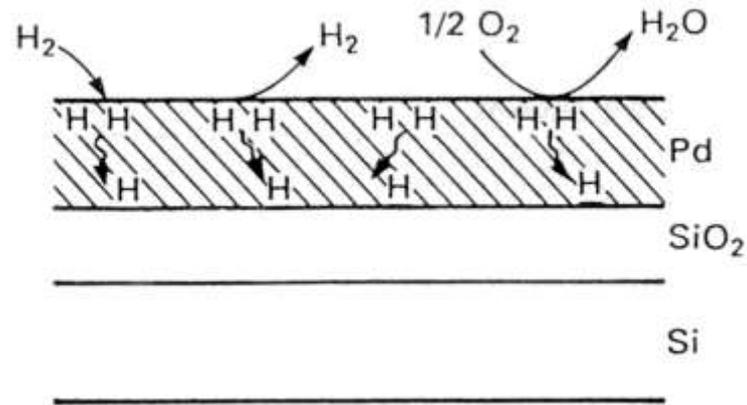
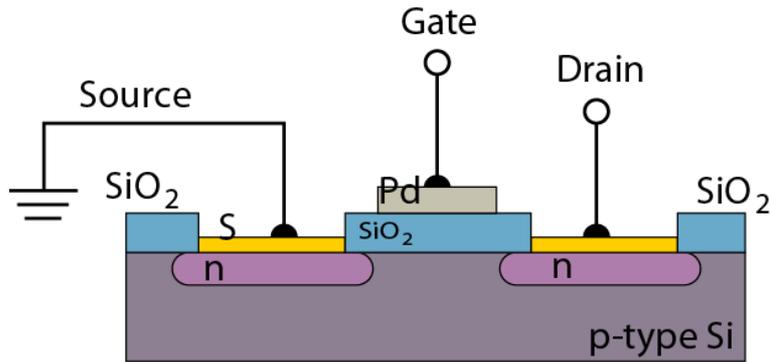


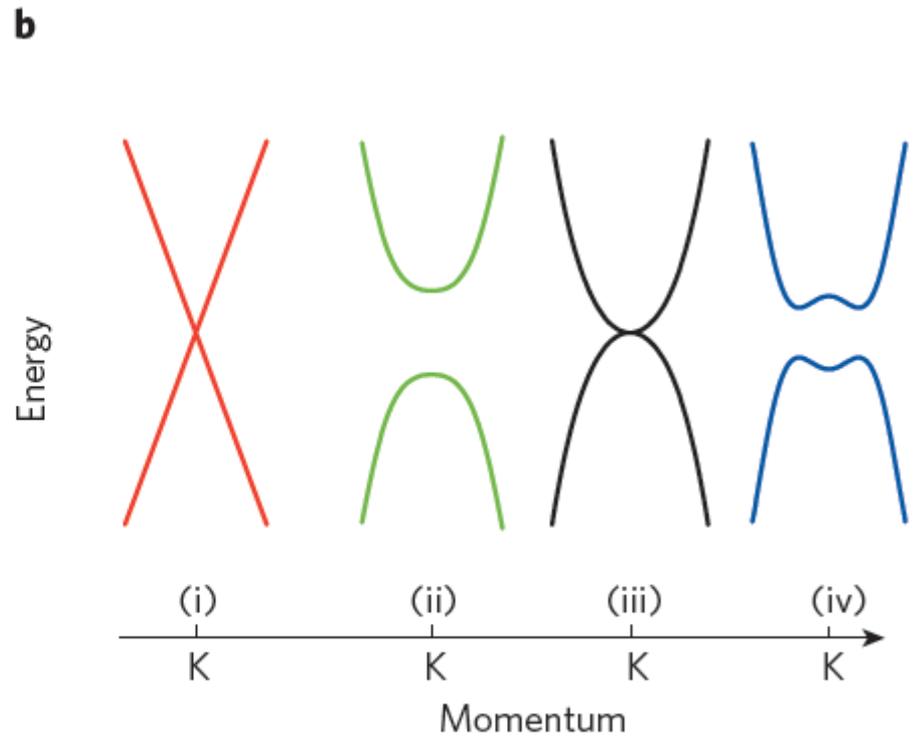
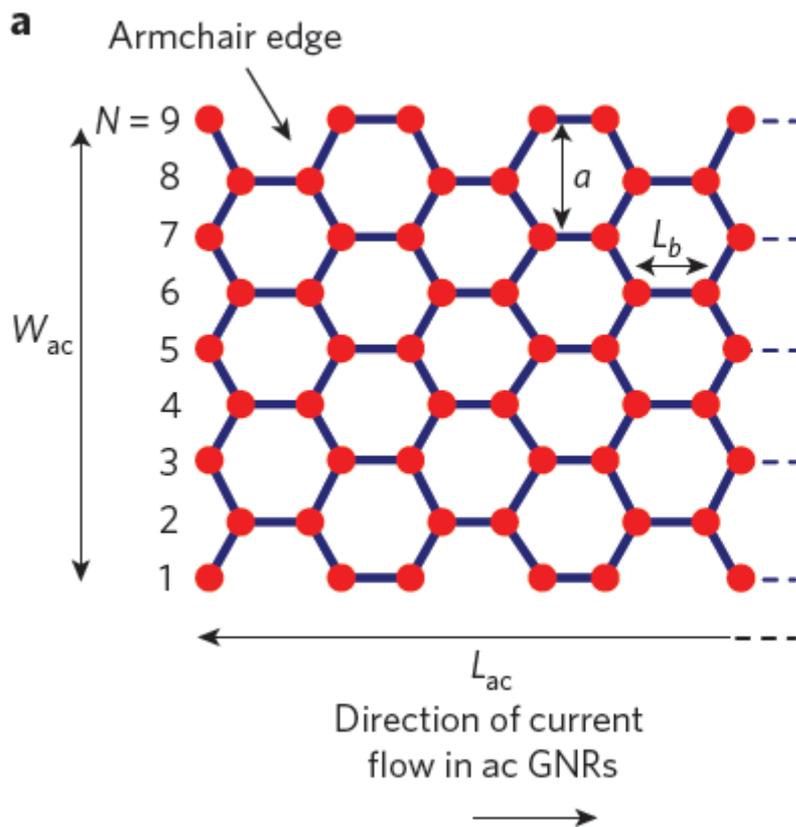
FIG. 4. Transistor threshold voltage as function of time when hydrogen is added to the transistor and removed again. The temperature is 150°C.

$$V_{th} = f(\Phi_{metal})$$

↑  
effect of H

*hydrogen adsorbs, dissociates and diffuses to metal-oxide interface; forming a dipole layer modifying the metal - semiconductor interface (workfunction difference)*

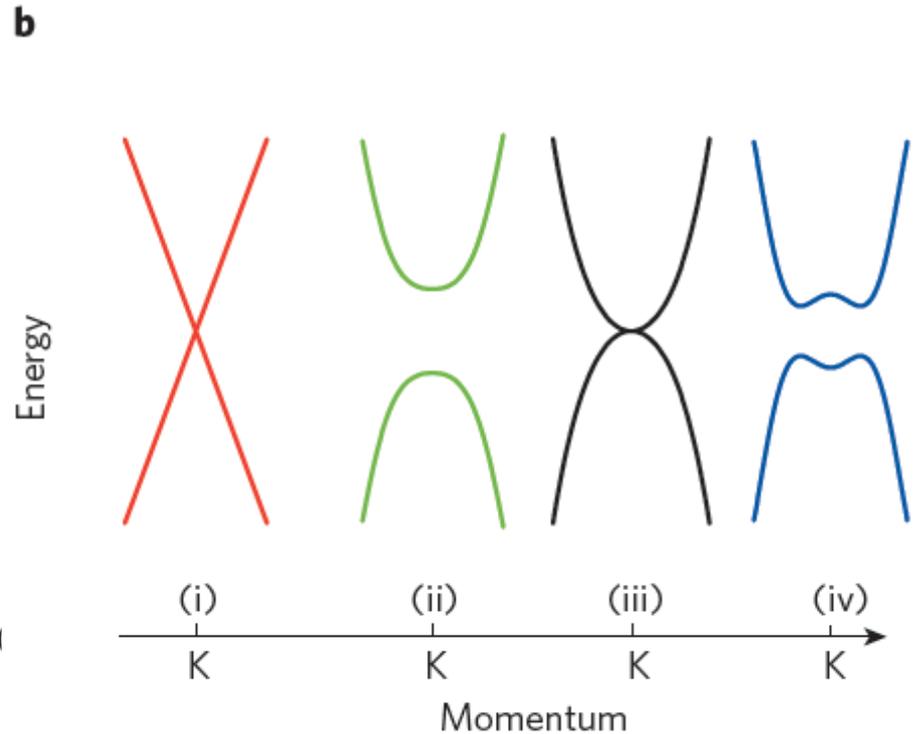
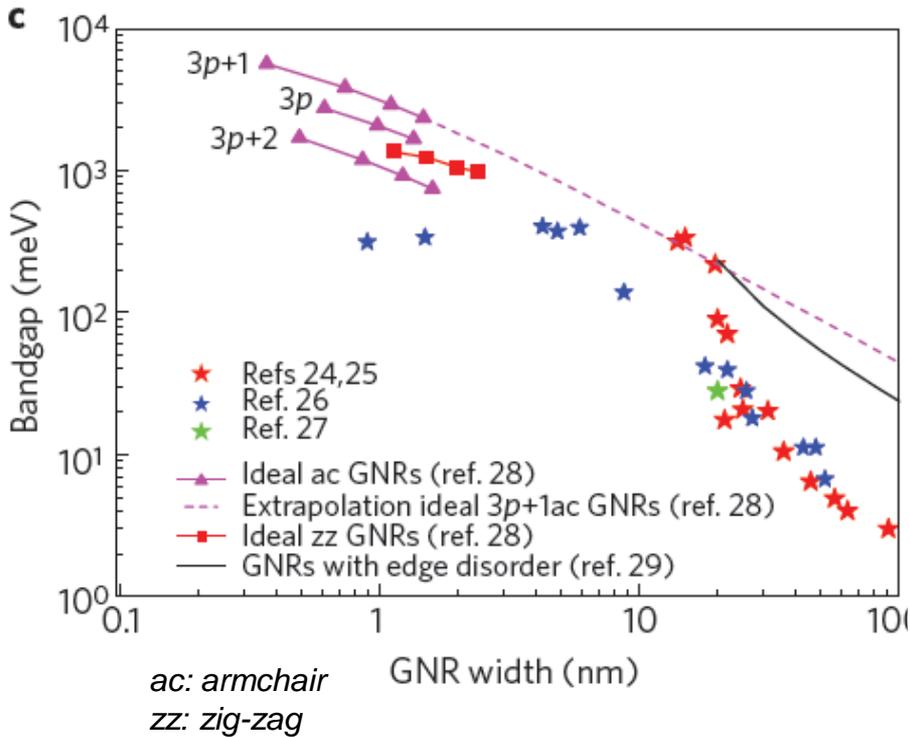
# would graphene FETs be useful ?



- (i) large-area graphene: **no gap!**
- (ii) graphene nanoribbons,
- (iii) unbiased bilayer graphene,
- (iv) bilayer graphene with an applied perpendicular field.

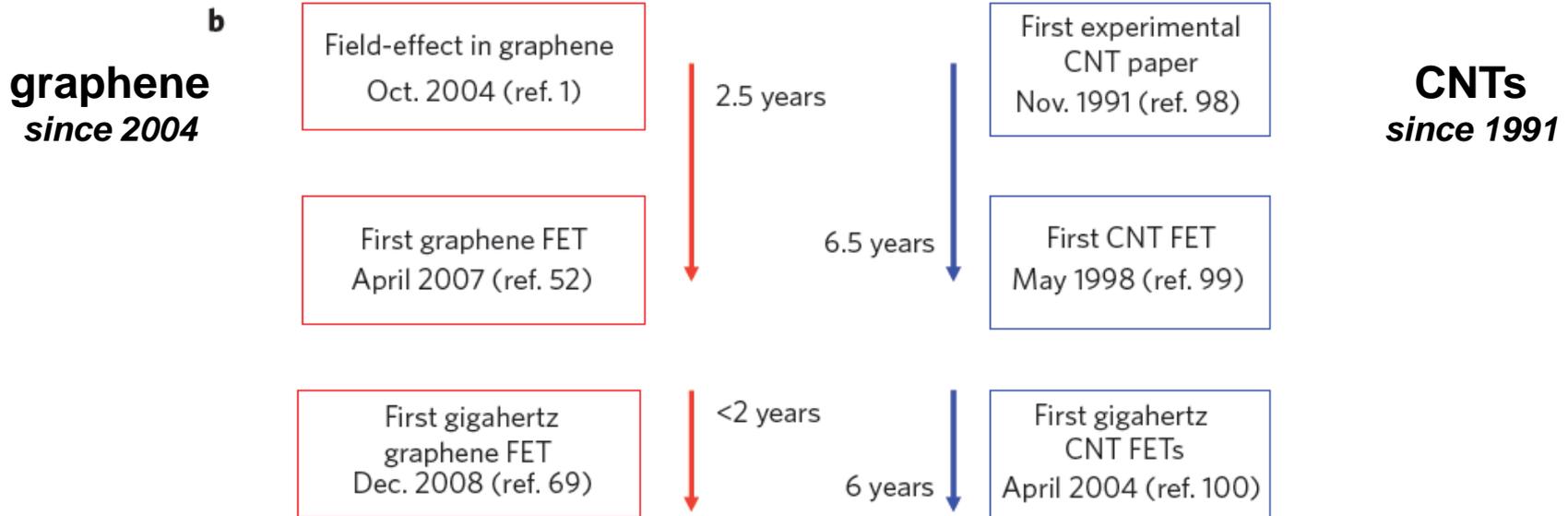
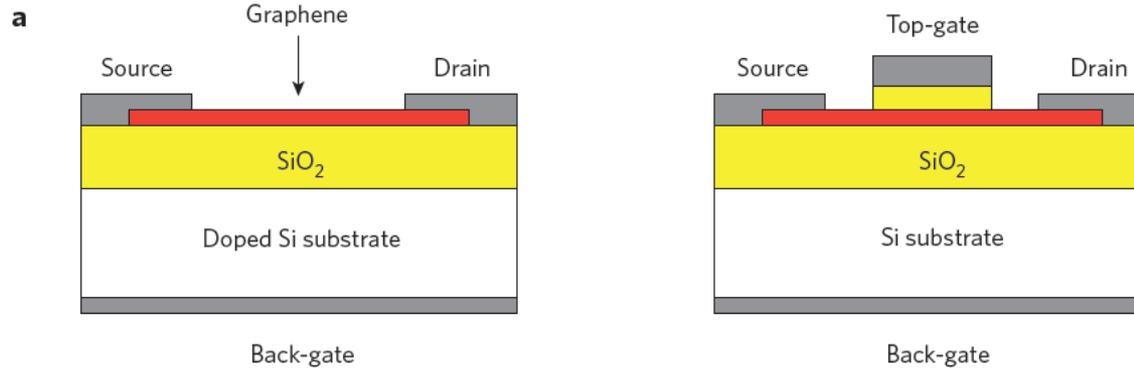
# graphene FET

## graphene nano-ribbons



- (i) large-area graphene,
- (ii) graphene nanoribbons,
- (iii) unbiased bilayer graphene,
- (iv) bilayer graphene with an applied perpendicular field.

# why graphene FETs



Record cut-off frequencies:

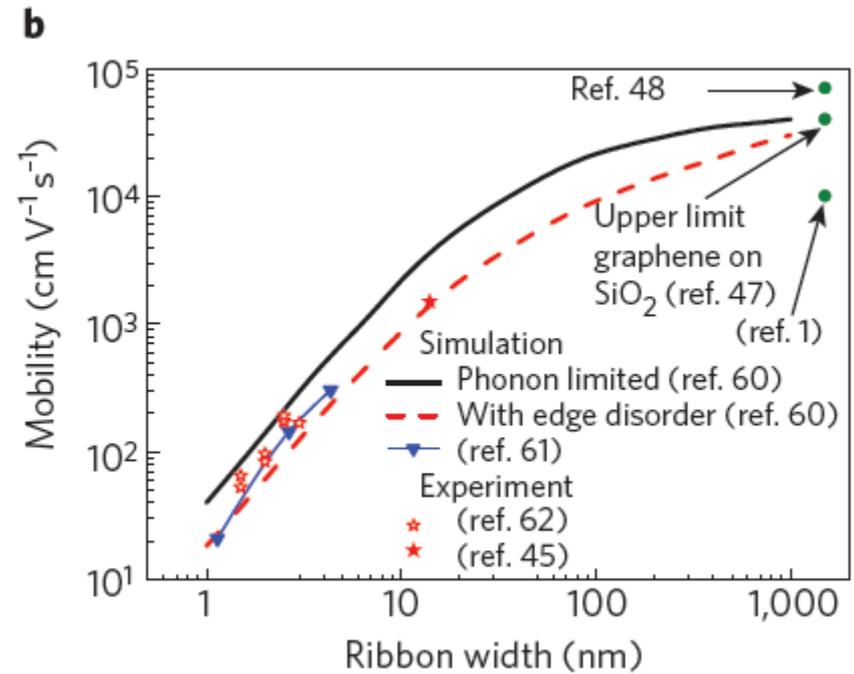
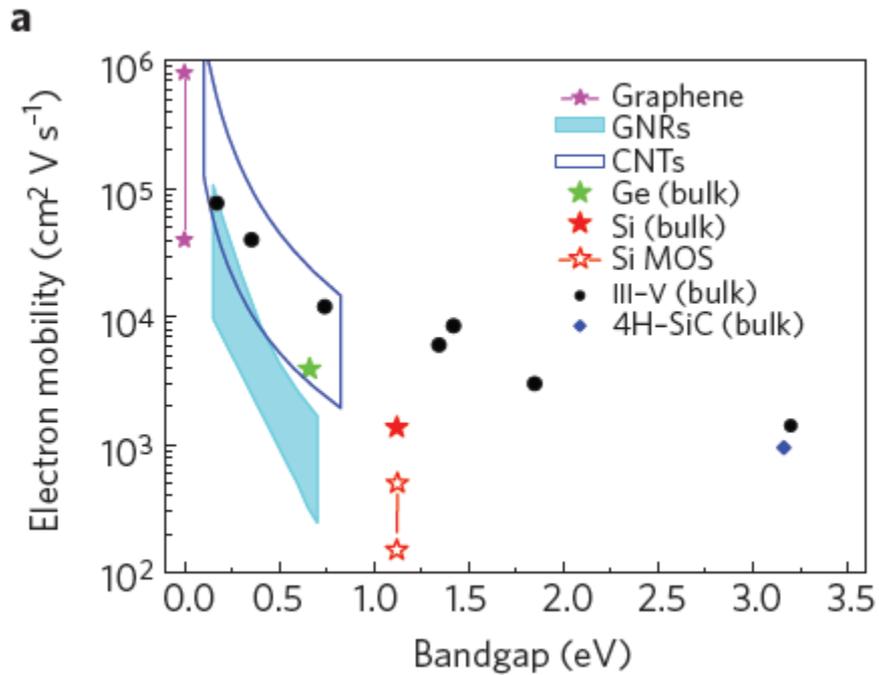
Graphene FET 100 GHz (ref. 73)

CNT FET 80 GHz (ref. 78)

Schwierz, *Nat. Nano* (2010)

# graphene FET

## charge carrier mobility in various materials & graphene



# graphene (graphene-related materials) for sensing

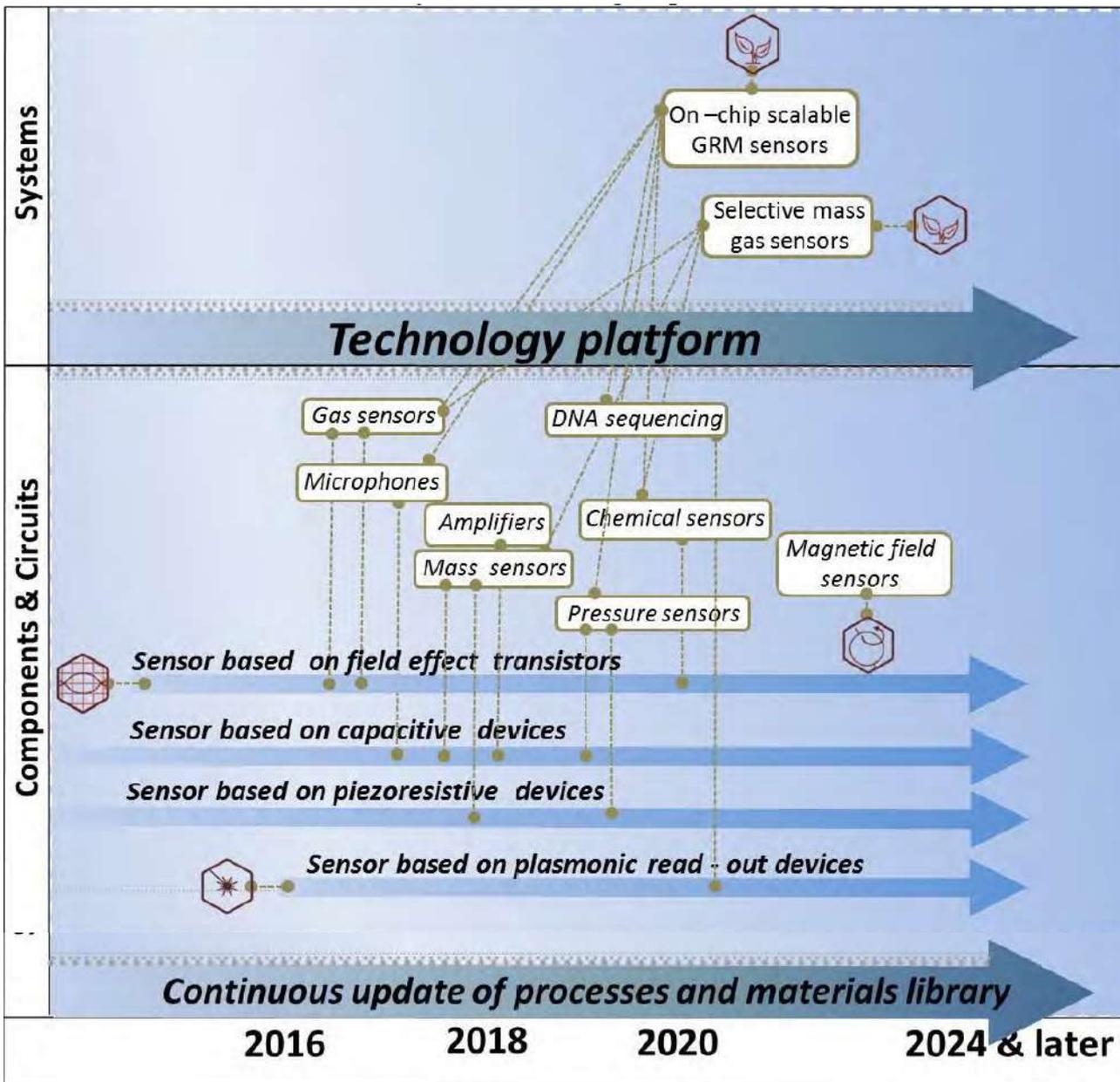
**Table 1** GRMs as a platform for enabling new technologies and applications, with radical [**not incremental**] advances

features	Enabled applications / technologies
Atomic thinness	Flexible devices; thin and flexible electronic components; modular assembly / distribution of portable thin devices
Foldable material	Engineering new materials by stacking different atomic planes or by varying the stacking order of homogeneous atomic planes
All-surface material	Engineering novel 2d crystals with tuneable physical/chemical properties by control of the surface chemistry. Platform for new chemical /biological sensors
Solution - processable	Novel composite materials with outstanding physical properties ( <i>e.g.</i> high thermal conductivity, $\kappa$ ; high Young modulus and tensile strength); Novel functional materials
High carrier mobility ( $\mu$ )	Ultra-high frequency electronic devices
Optical (saturable) absorption; photo-thermoelectric effect	Novel optoelectronic and thermoelectric devices; photodetectors
Field-effect sensitivity	Highly sensitive transducers

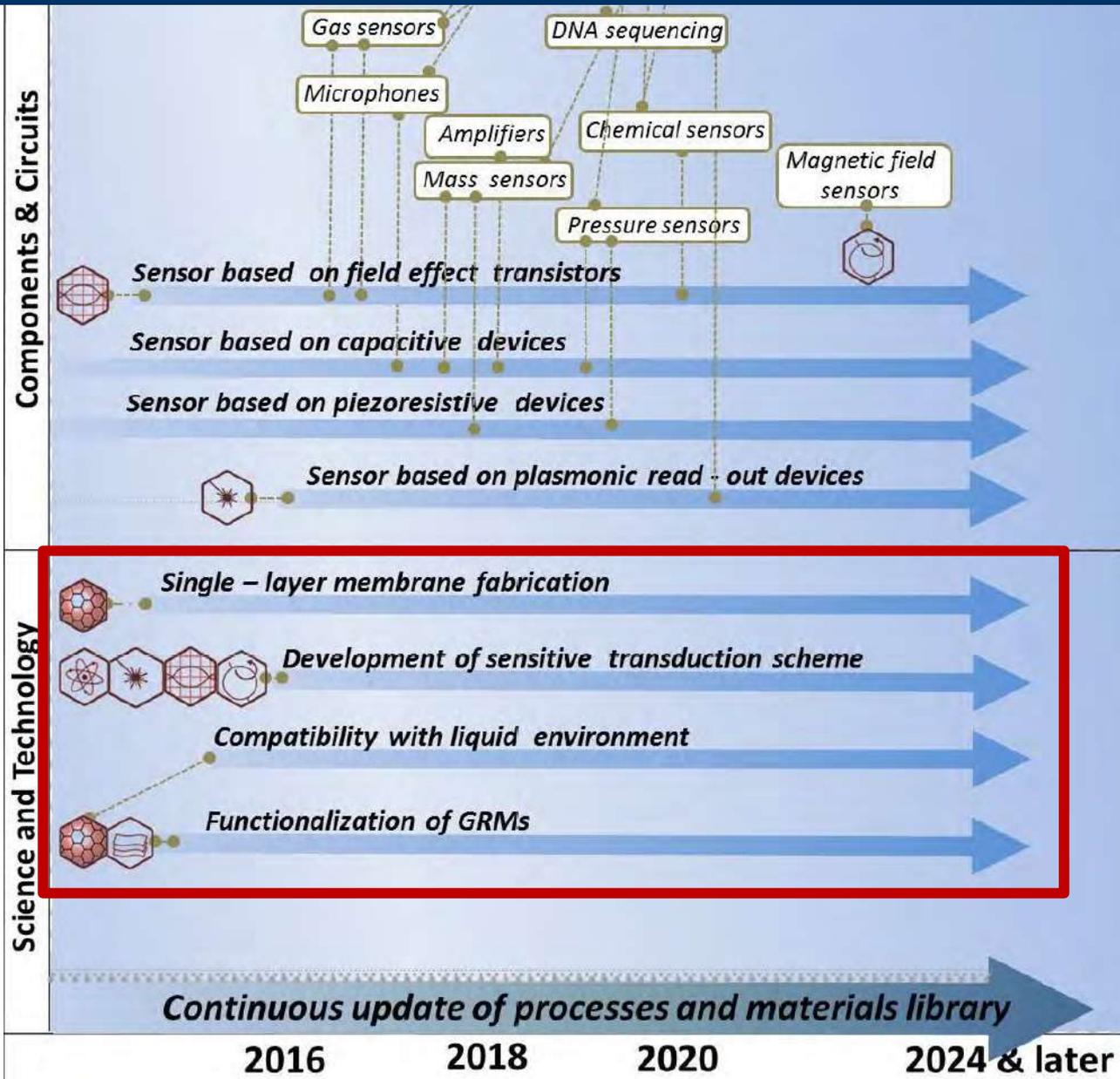
# *graphene (graphene-related materials)*

Optical (saturable) absorption; photo-thermoelectric effect	Novel optoelectronic and thermoelectric devices; photodetectors
Field-effect sensitivity	Highly sensitive transducers
High intrinsic capacitance; high specific surface area (SSA)	Outstanding supercapacitors
Photovoltaic effect, broad-range optical transparency; photocatalytic effects	Energy conversion; energy harvesting; self-powered devices
Theoretically predicted "chiral superconductivity"	High T <sub>c</sub> superconductors
Dirac fermions; pseudospin	Valleytronics

# graphene (graphene-related materials)



# graphene (graphene-related materials)



**devices**

**science & tech.**

# graphene (graphene-related materials)

vision....



- flexible, stretchable (spider silk)
- biodegradable
- high energy density
- low-power, emission-free
- analyzing air pollution traces and providing real-time feedback

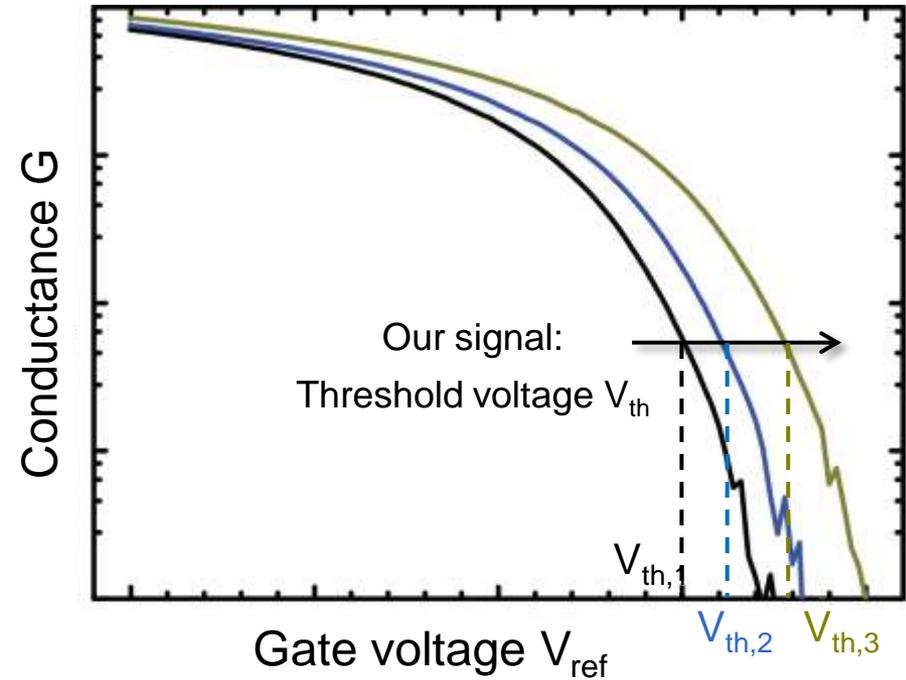
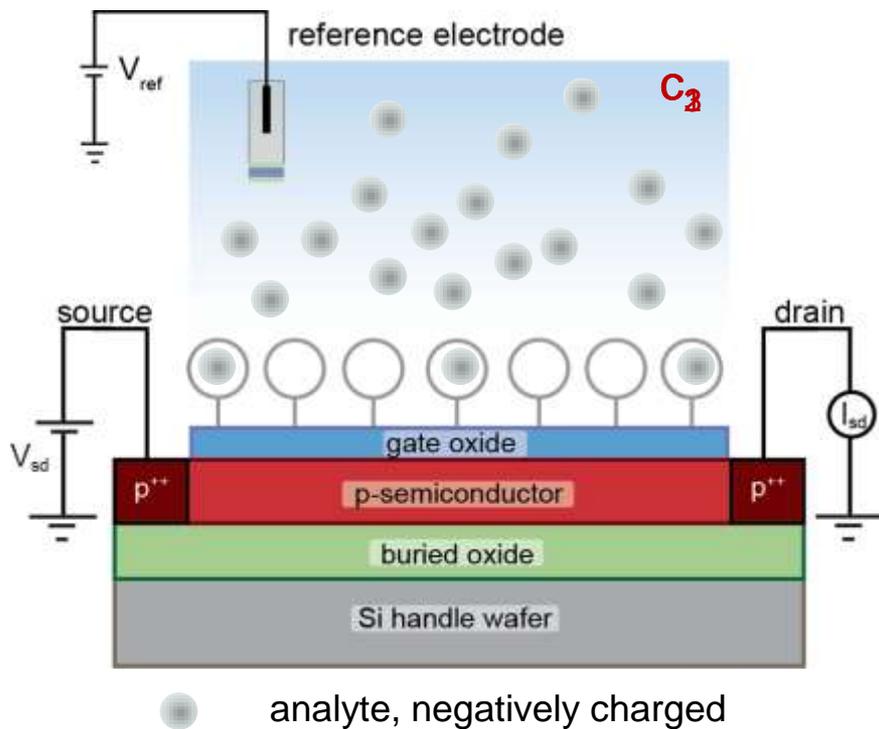
**NOKIA Morph.** *the future mobile device will act as a gateway. It will **connect users to local environment**, as well as the global **internet**. It is an attentive device that **shapes according to the context**. It can change its form from rigid to **flexible** and **stretchable**.*

- **general aspects on sensing**  
*sensitivity, specificity*  
*overview of transducers*
- **field effect transistors (FETs) as charge sensors**  
*MOSFET, graphene and GFET*

### **Examples**

- Ion sensitive field-effect transistors (ISFETs) for pH, ionic and biochemicals detection
- Nanopores for sequencing

# ISFETs as potentiometric biochemical sensors



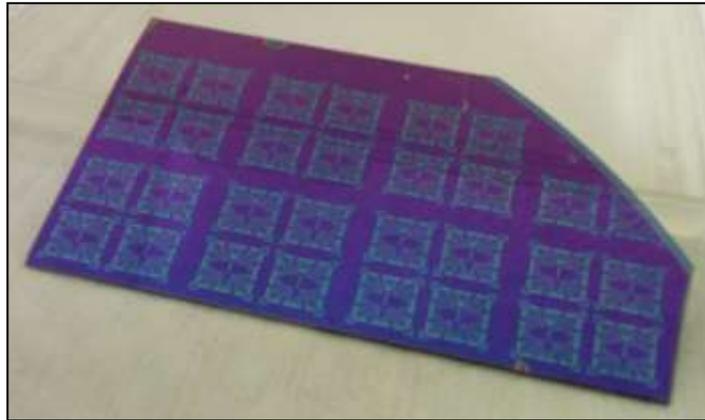
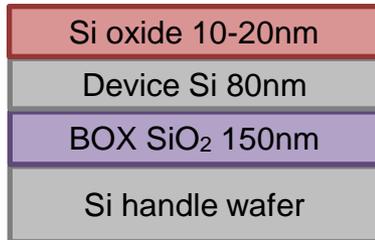
Theoretical limit: Nernst response

$$\Delta V_{th} = V_{th,2} - V_{th,1} = 2.3 \frac{kT}{e} \log_{10} \left( \frac{c_2}{c_1} \right) \approx 59.6 \text{ mV} \cdot \log_{10} \left( \frac{c_2}{c_1} \right)$$

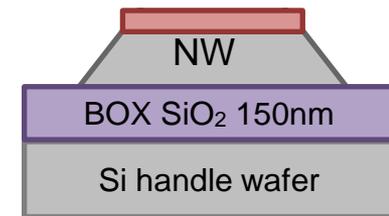
- converts a chemical reaction into an electrical signal
- signal : change in current / shift in threshold voltage

# nanowire fabrication: SOI process

p-type (100) SOI



ALD oxide 10-20nm: **Al<sub>2</sub>O<sub>3</sub>** or **HfO<sub>2</sub>**



Top view:

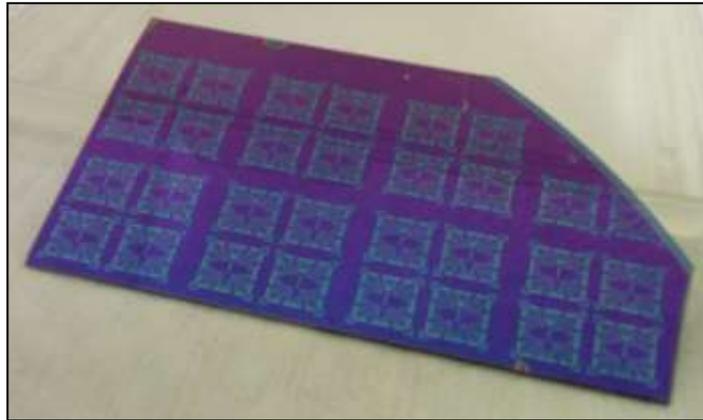


Drain      length: 6μm      Source  
width: 100 nm -1μm

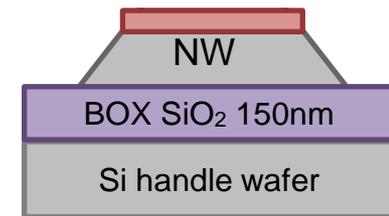
# nanowire fabrication: SOI process

p-type (100) SOI

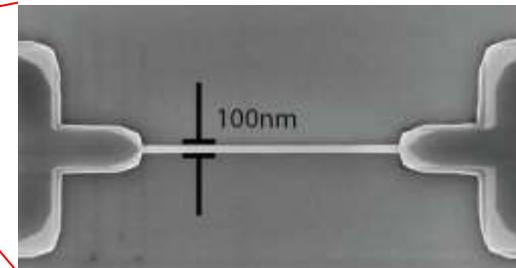
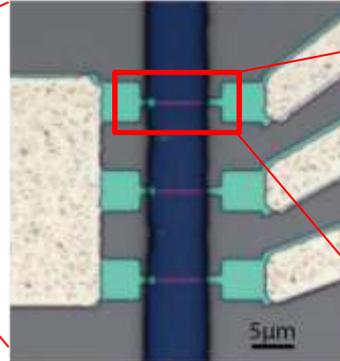
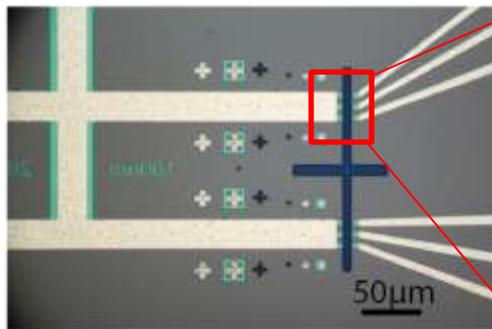
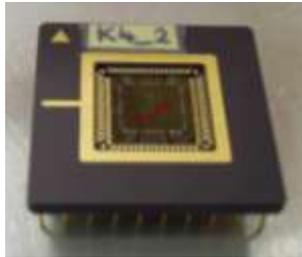
Si oxide 10-20nm
Device Si 80nm
BOX SiO <sub>2</sub> 150nm
Si handle wafer



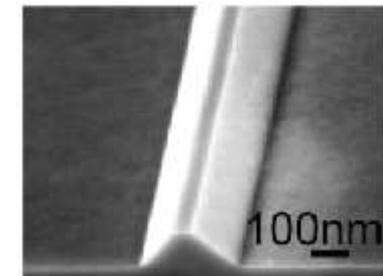
ALD oxide 10-20nm: **Al<sub>2</sub>O<sub>3</sub>** or **HfO<sub>2</sub>**



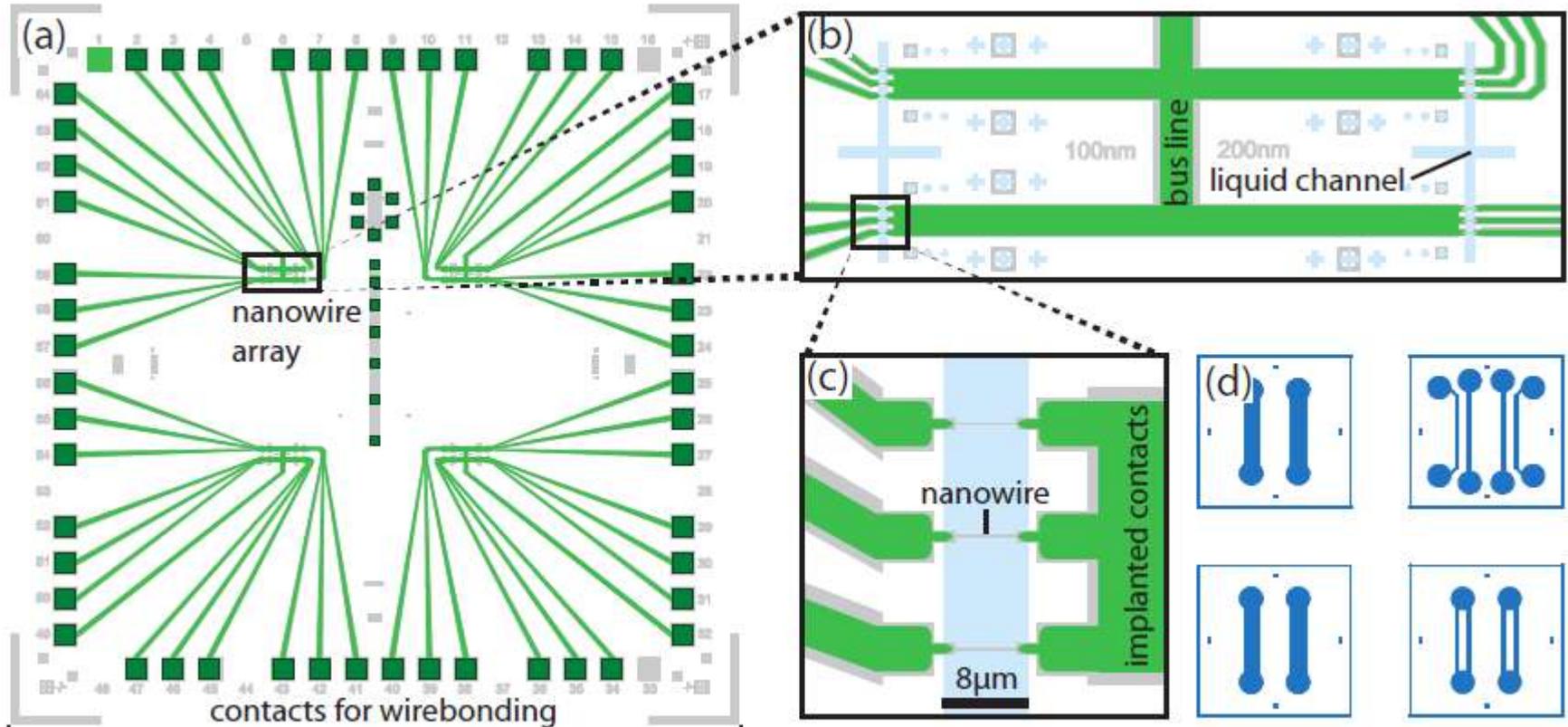
chip carrier



- ALD layer with BF<sub>2</sub><sup>+</sup> ion implantation
- Liquid channel     Metal lines (Al)
- Si nanowire with ALD layer     SU-8

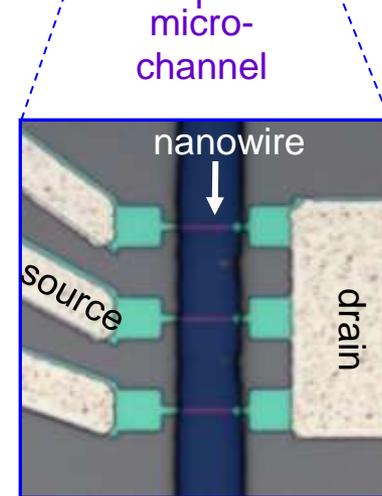
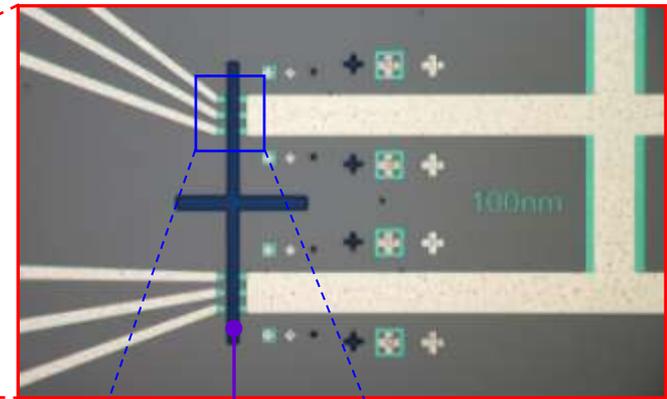
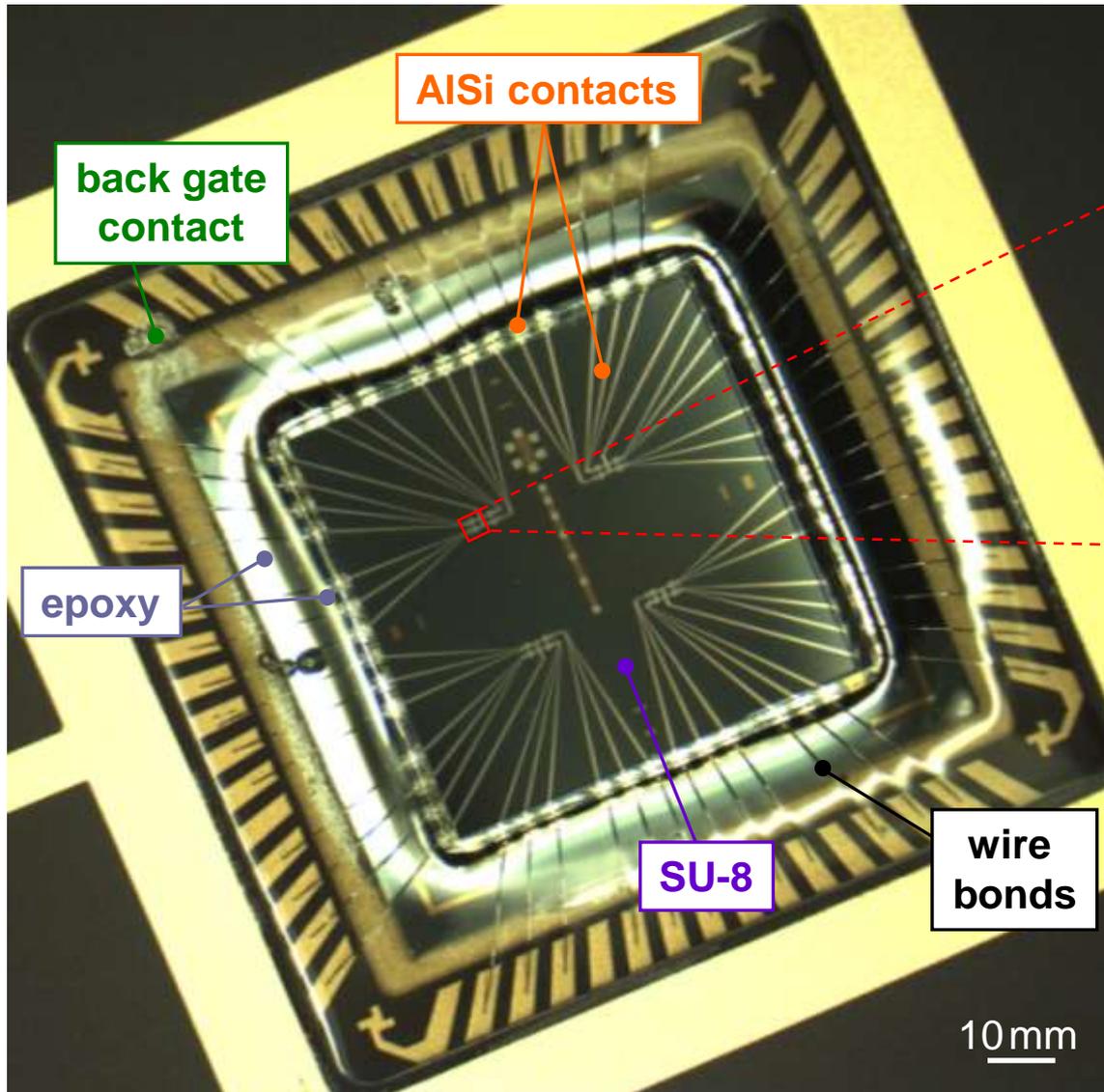


# sensor device layout

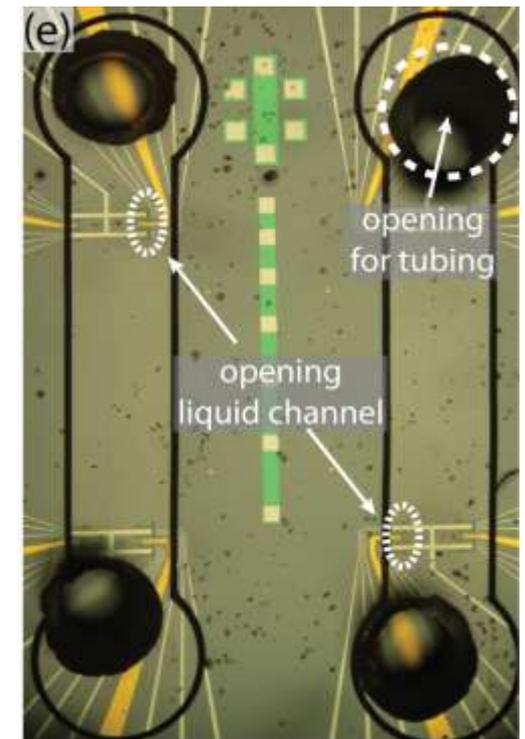
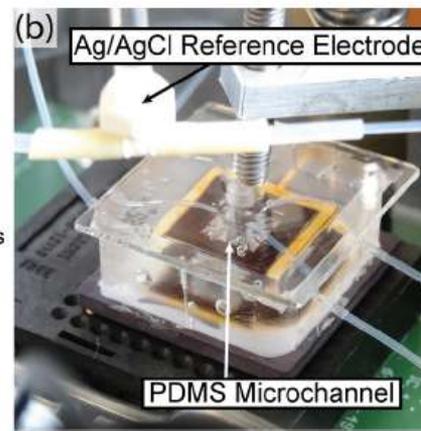
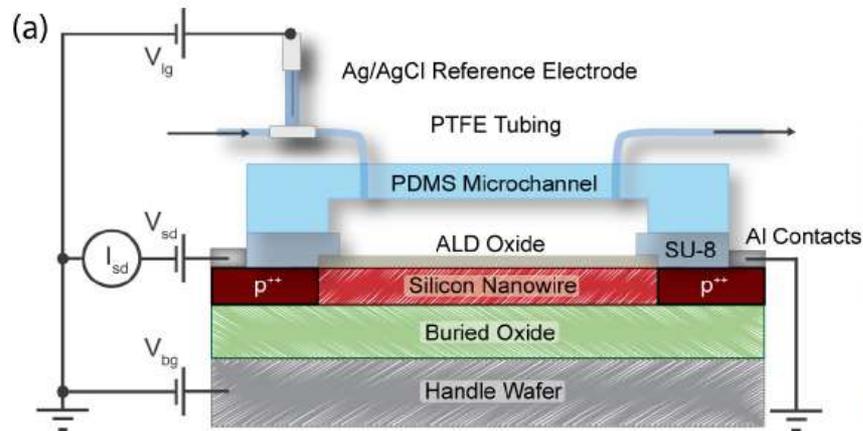
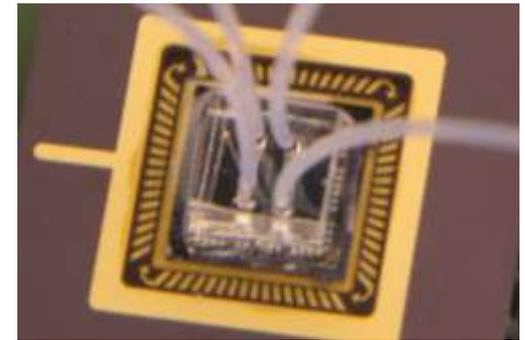
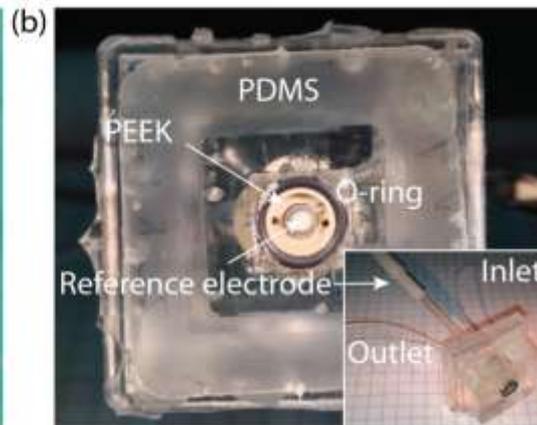
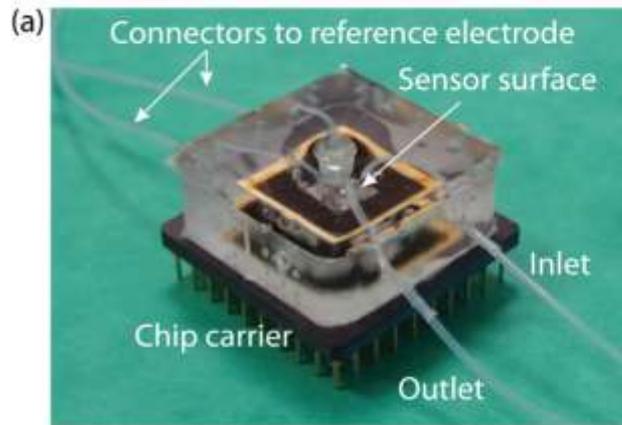


- 48 individually addressable nanowires in 4 separated arrays
- **length**: 6μm, **width** (top): 100nm-1μm, **thickness** (device layer): 80nm
- **fluidic channels with different designs** (functionalization, measurement)

# sensor device layout



# fluidics and measurement setup



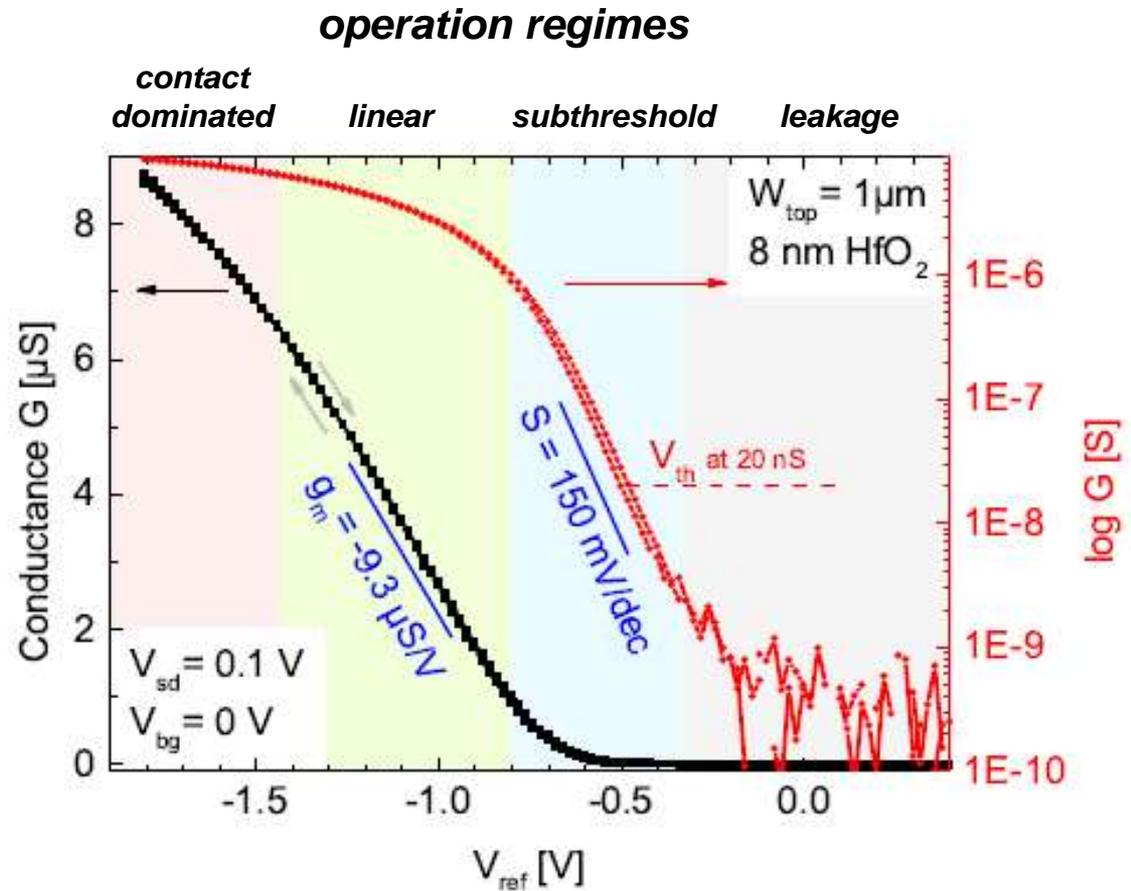
# characterization of SiNW FET

## Transfer curve $G$ vs $V_{ref}$

1  $\mu\text{m}$  wide SiNW  
8 nm  $\text{HfO}_2$  gate oxide

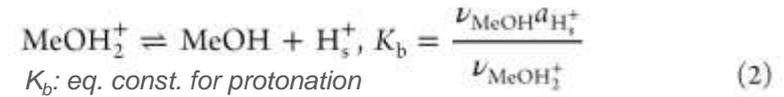
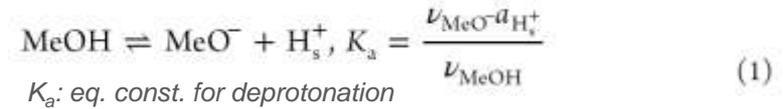
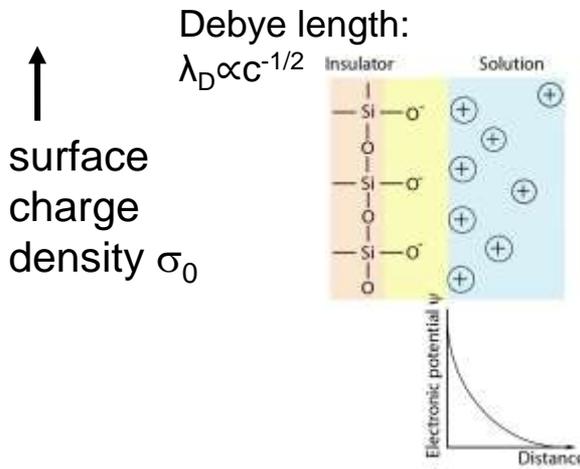
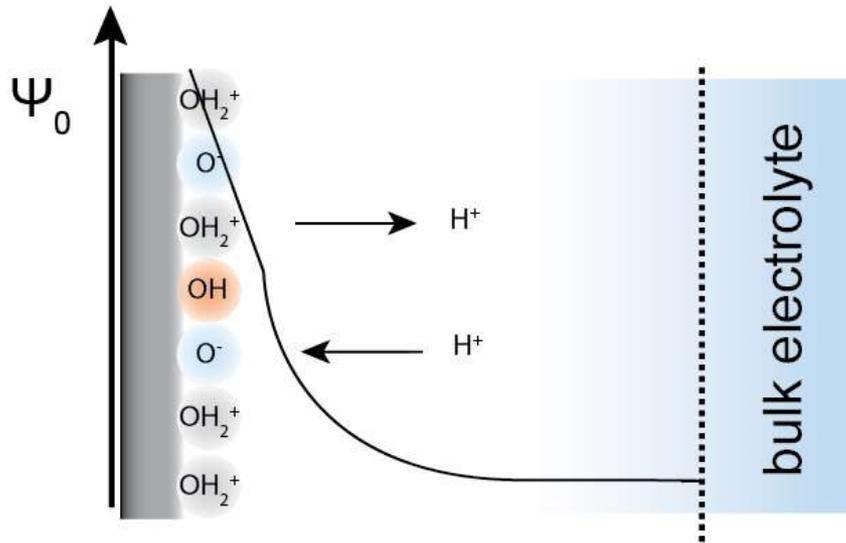
pH 3 buffer solution  
 $V_{sd} = 0.1 \text{ V}$ ,  $V_{bg} = 0 \text{ V}$

*NB: back and forth traces:  
negligible hysteresis*



# response to pH changes

## Site-binding model for a metal (Me) oxide surface



total number of **surface groups**  $N_s$  (density)

$$N_s = \nu_{\text{MeOH}} + \nu_{\text{MeO}^-} + \nu_{\text{MeOH}_2^+} \quad (3)$$

surface charge density

$$\sigma_0 = (\nu_{\text{MeOH}_2^+} - \nu_{\text{MeO}^-})e \quad (4)$$

from eqs 1-4

$$\sigma_0 = eN_s \left( \frac{a_{\text{H}_s^+}^2 - K_a K_b}{a_{\text{H}_s^+}^2 + a_{\text{H}_s^+} K_b + K_a K_b} \right) \quad (5)$$

$a_{\text{H}_s^+}$  activity of surface protons

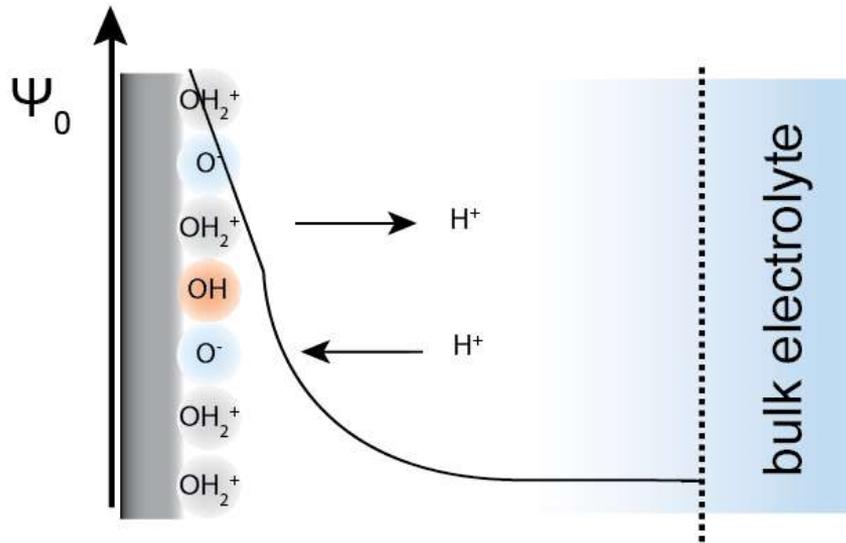
$\nu$  density of surface groups

see e.g. P. Bergveld, *Sensors and Actuators B* 88 1–20 (2003)

Knopfmacher et al., *Nano Lett.* (2010); A. Tarasov et al., *Langmuir* (2012)

# response to pH changes

## Site-binding model



Debye length:

$$\lambda_D \propto c^{-1/2}$$



surface charge density  $\sigma_0$

Surface charge is screened by double layer ions

$$\sigma_0 = C_{dl} \Psi_0 = eN_s \left( \frac{a_{H_s}^2 - K_a K_b}{a_{H_s}^2 + a_{H_s} K_b + K_a K_b} \right) \quad (6)$$

Convert surface proton to bulk proton activity via surface potential  $\psi_0$

$$a_{H_s^+} = a_{H_b^+} \exp\left(-\frac{e\Psi_0}{kT}\right) \quad (7)$$

From (6),(7): relation between  $\psi_0$  and  $\text{pH}_b = -\log(a_{H_b^+})$

$$\Delta V_{th} = -2.3 \frac{k_B T}{e} \alpha \Delta \text{pH} \quad \alpha = \frac{1}{1 + C_{dl}/C_s}$$

$$\Delta V_{th} = -59.5 \text{mV} \alpha \Delta \text{pH}$$

Nernst limit, case  $C_s \gg C_{dl}$  ( $\alpha=1$ ) at  $T=300\text{K}$

$C_s$ : surface buffer capacitance (nb of sites)

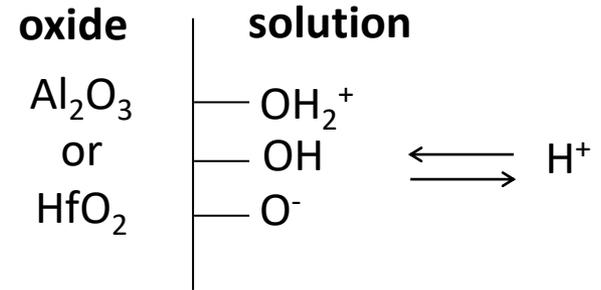
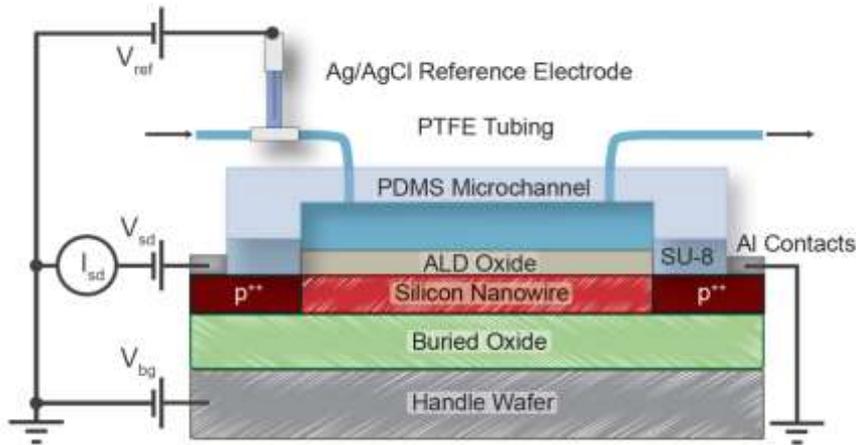
$C_{dl}$ : double layer capacitance

$$C_s = \frac{e^2 N_s}{2.3 k_b T}$$

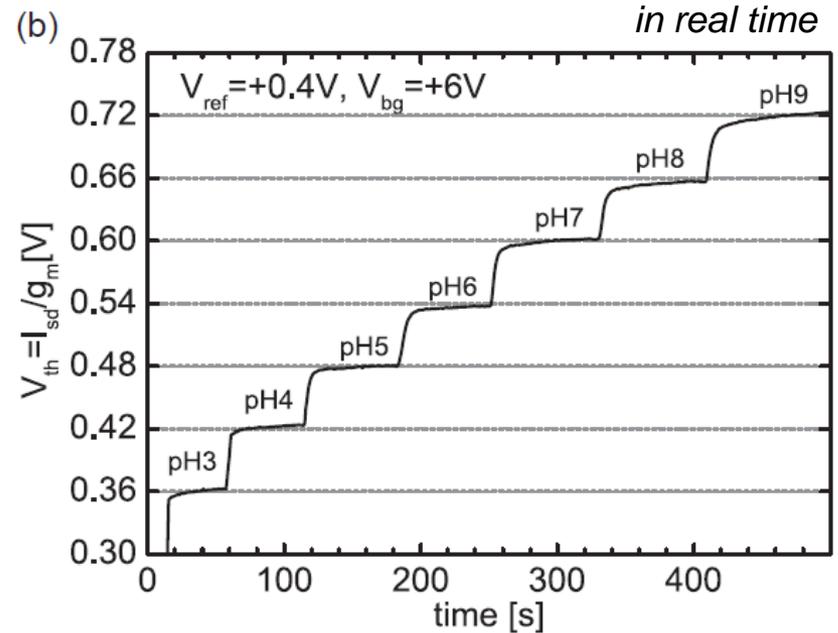
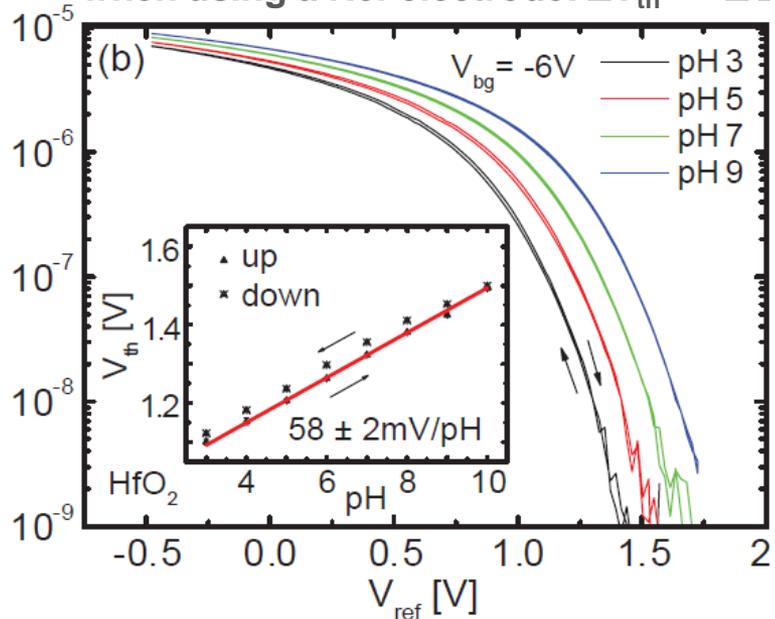
see e.g. P. Bergveld, *Sensors and Actuators B* 88 1–20 (2003)

O. Knopfmacher et al., *Nano Lett.* (2010); A. Tarasov et al., *Langmuir* (2012)

# NW response: pH sensing



when using a Ref electrode:  $\Delta V_{th} = -\Delta\Psi_0$



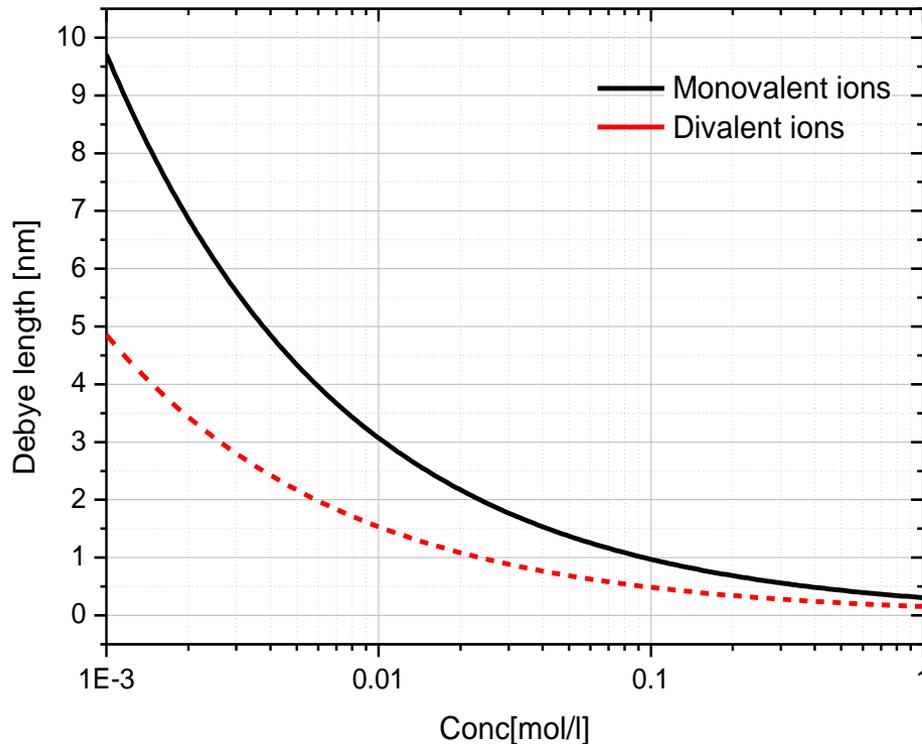
# importance of charge screening (Debye length)

$$\lambda_D = \sqrt{\frac{\epsilon_0 \epsilon_r k_B T}{2 N_A e^2 I}}$$

$$I = \frac{1}{2} \sum_{i=1}^n c_i z_i^2$$

I – ionic strength (I=c for 1:1 electrolyte)

Debye length  $\lambda_D$  at room temperature

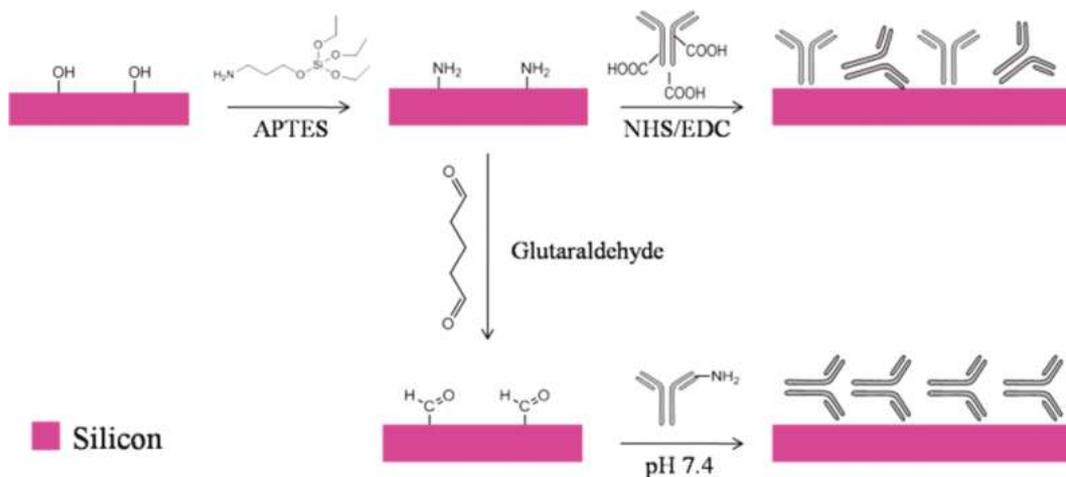
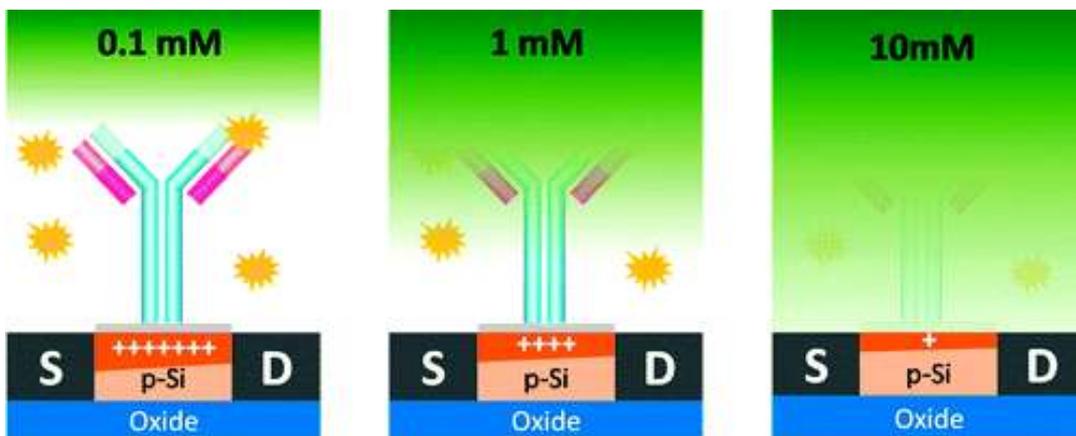


Example: PBS - Phosphate buffered saline

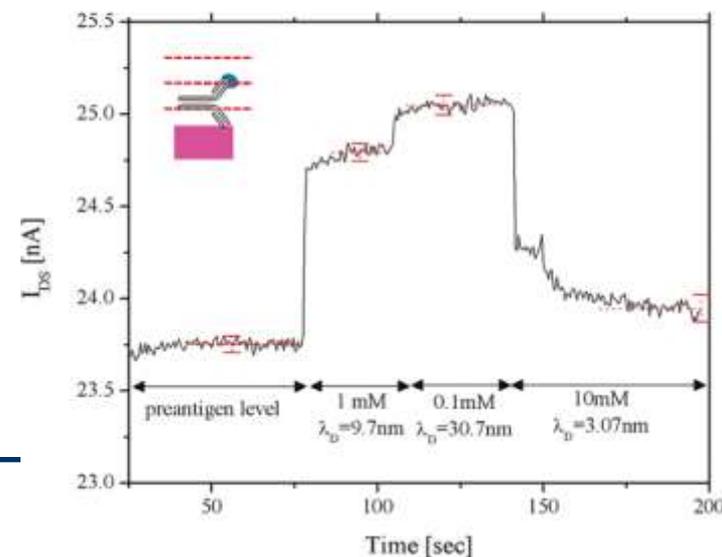
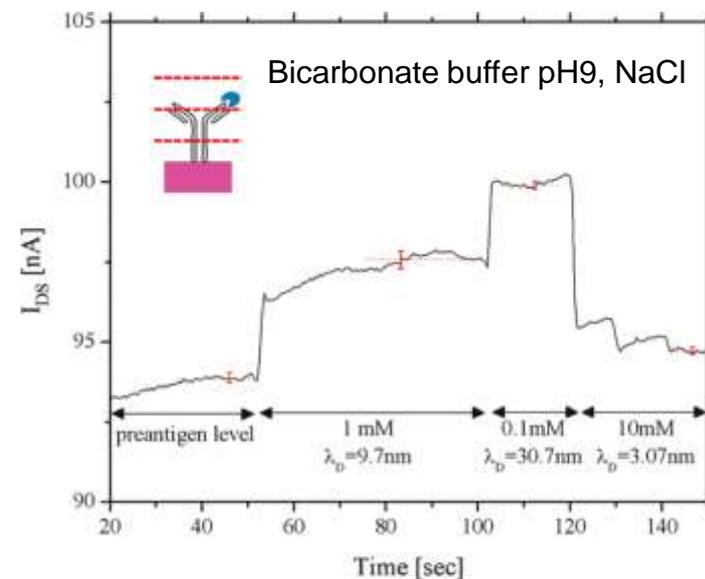
- 137mM NaCl
  - 2.7mM KCl
  - 12mM phosphate
- 1 x PBS ~150mM, pH7.4

PBS dilution	Concentration [mM]	$\lambda_D$
1	150	0.7 nm
0.1	15	2.3 nm
0.01	1.5	7.3 nm

# importance of charge screening (Debye length)

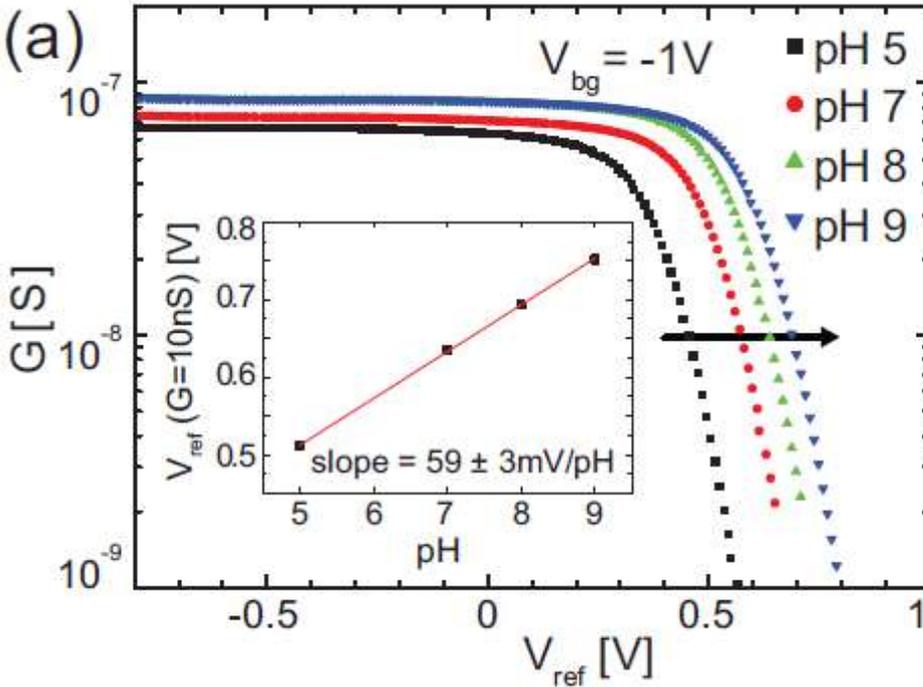


Anti – CA15.3 / Breast cancer biomarker

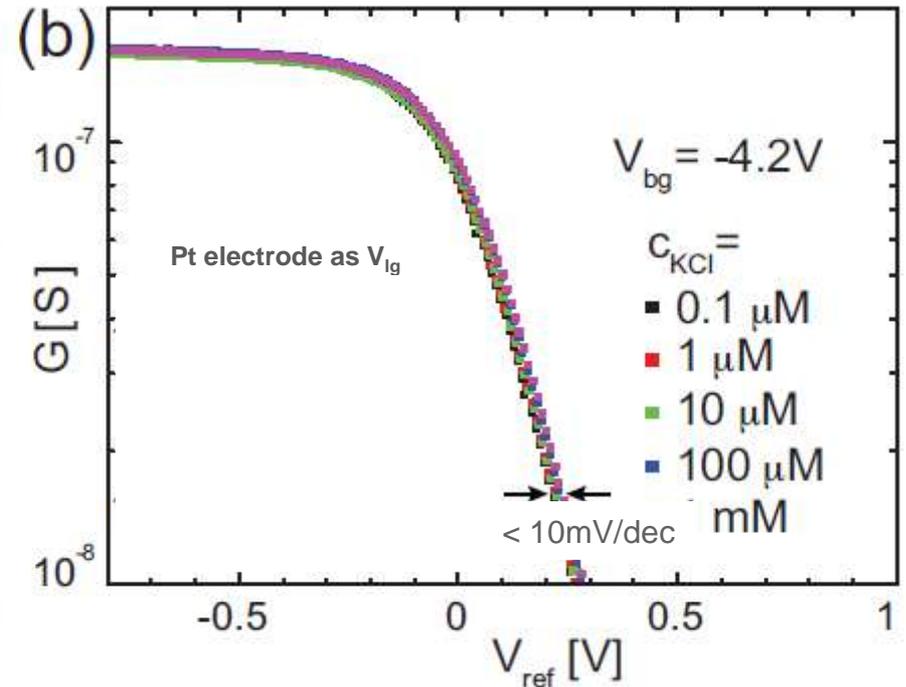


# effect of an increasing background ionic concentration

varying pH



constant pH  
varying ion (KCl) concentration



$$C_{dl} \propto \sqrt{c} \quad ?$$

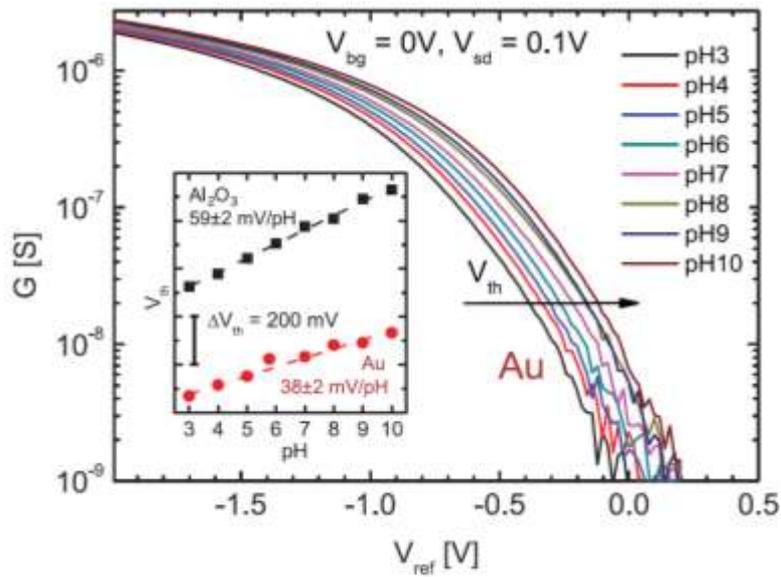
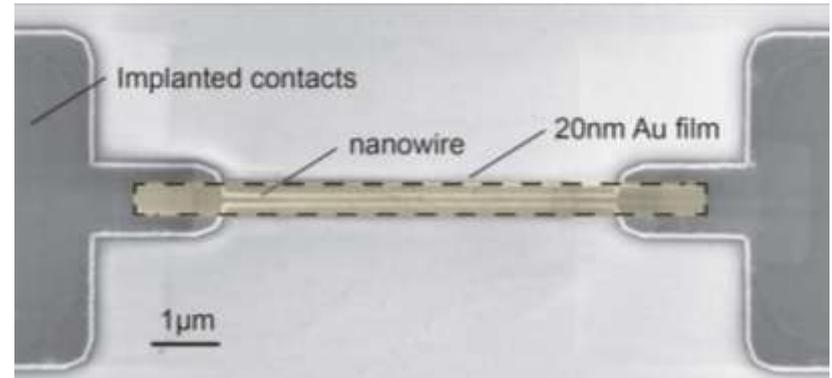
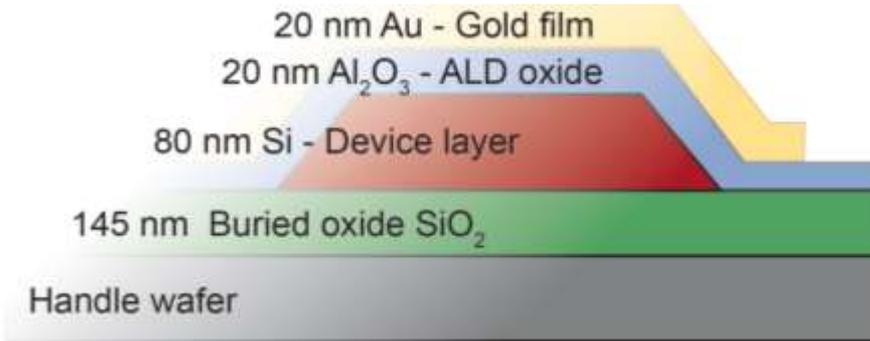
$$\Delta V_{th} = -2.3 \frac{k_B T}{e} \alpha \Delta pH$$

$$\alpha = \frac{1}{1 + C_{dl}/C_s} \approx 1$$

$$\Leftrightarrow C_s \gg C_{dl}$$

NB: not the case for SiO<sub>2</sub>

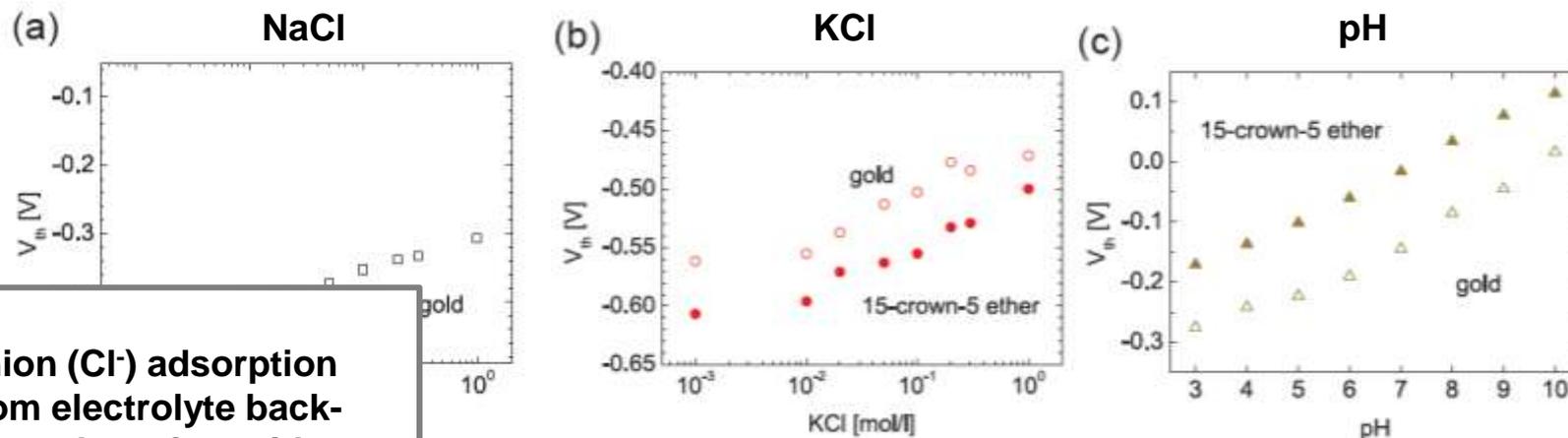
# metal-coated surface: alternative functionalization possibility



## Au film: different surface chemistry

- weaker pH response of Au compared to oxide Al<sub>2</sub>O<sub>3</sub>, HfO<sub>2</sub>
- ⇒ N<sub>s</sub> ~ 2 orders of magnitude smaller compared to Al<sub>2</sub>O<sub>3</sub>  
~1% of surface atoms oxidized

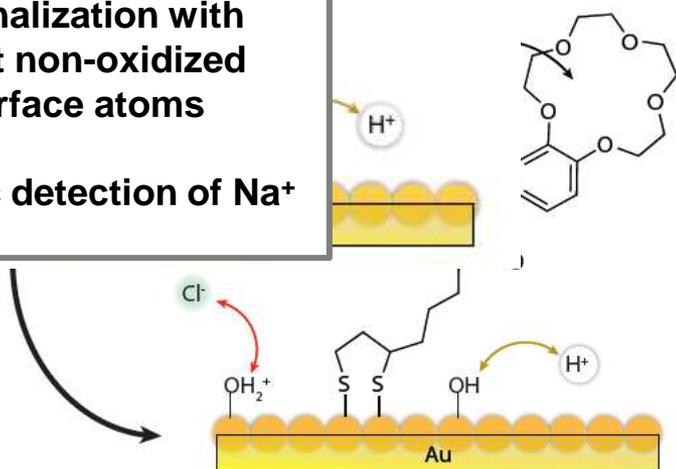
# specific ion detection



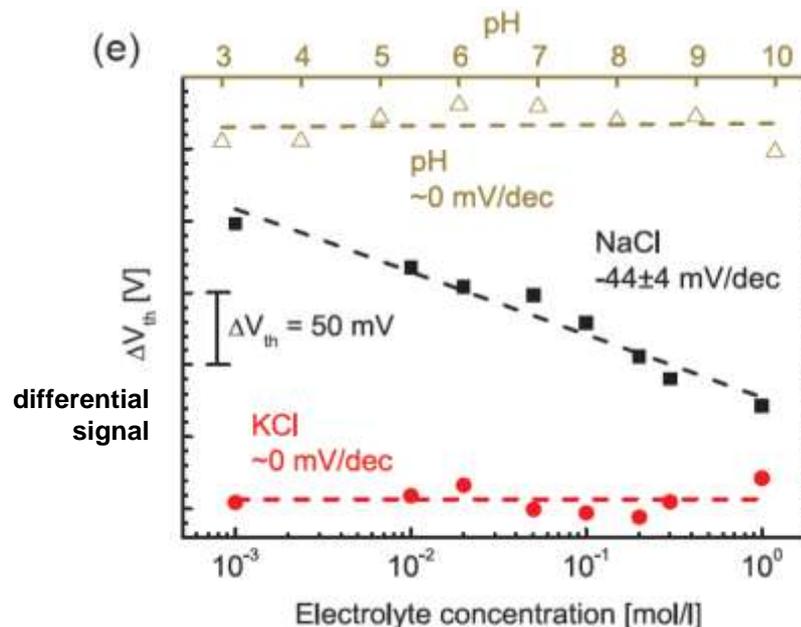
anion ( $\text{Cl}^-$ ) adsorption from electrolyte background, as for oxides

functionalization with thiols at non-oxidized gold surface atoms

specific detection of  $\text{Na}^+$

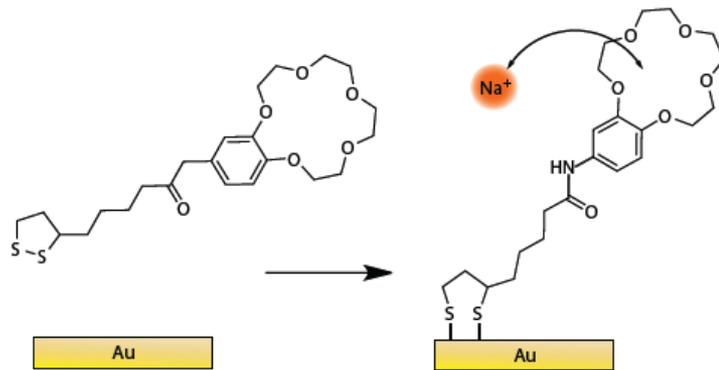


molecule: I. Wright, C. Martin, S. Müller, E. Constable

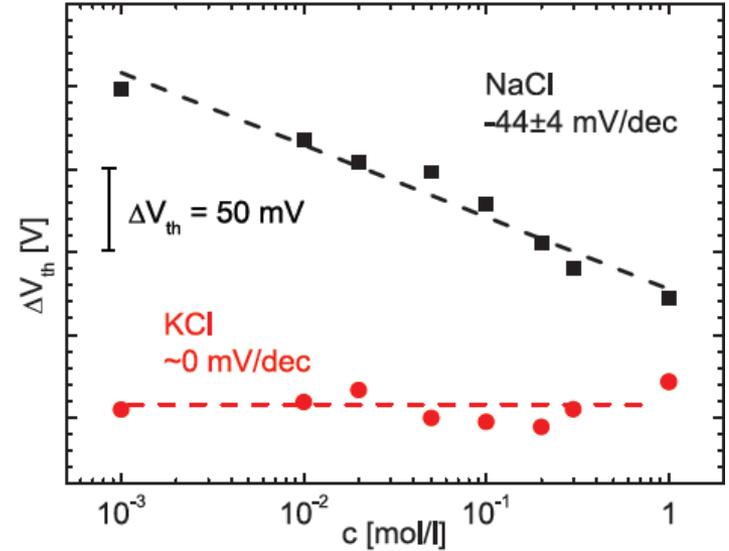


# multiple ions detection: Au and AlO surfaces

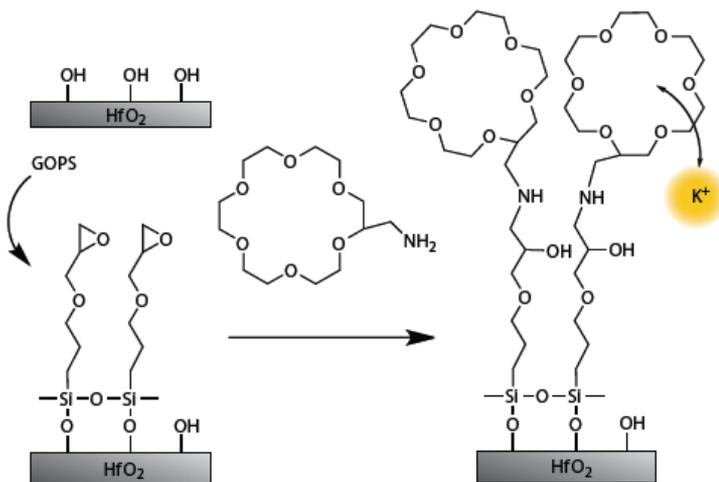
(a)



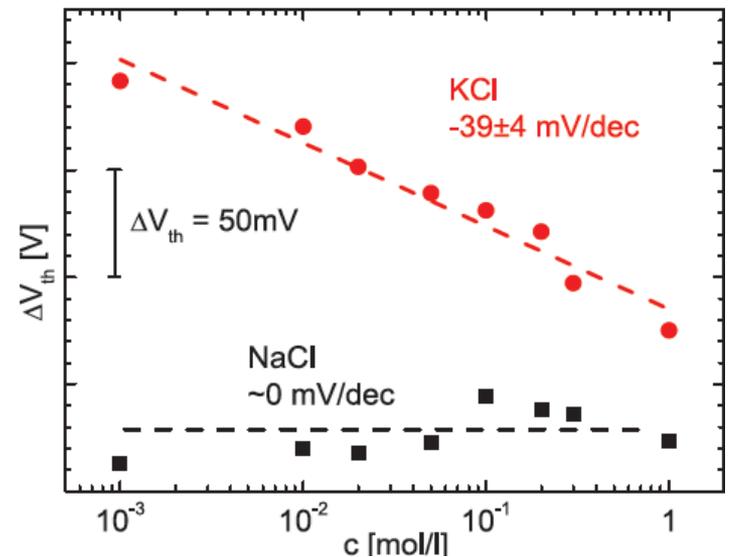
(b)



(c)



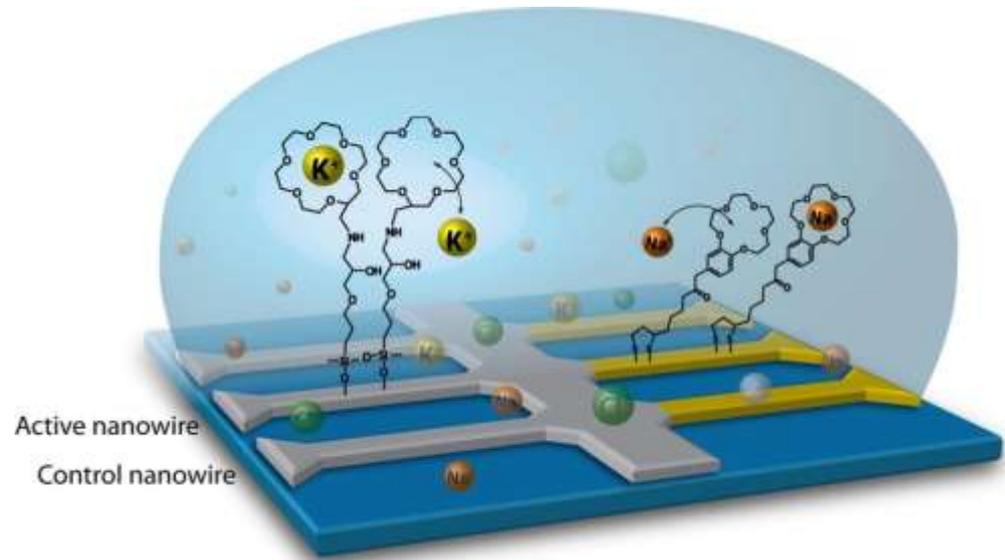
(d)



# multifunctional platform

## ions detection

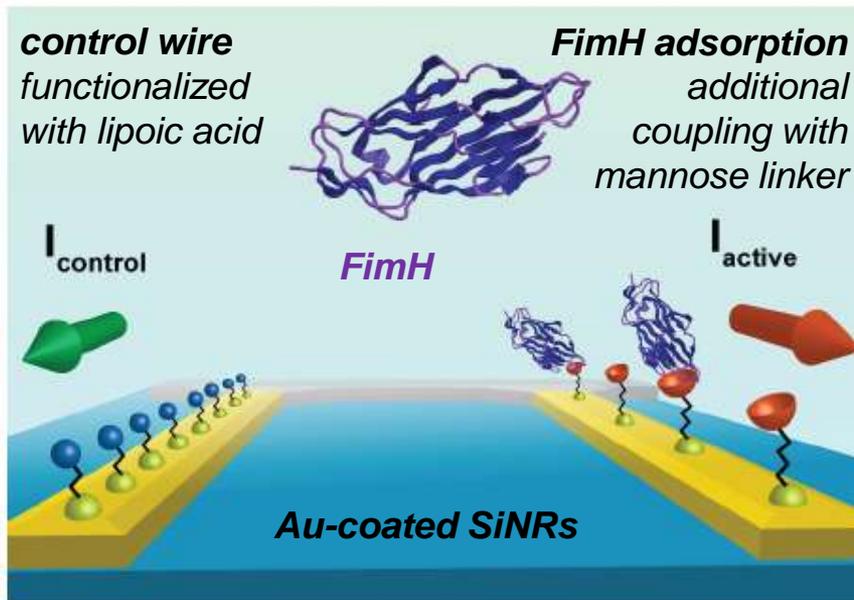
- pH, Na<sup>+</sup>, K<sup>+</sup>, Ca<sup>2+</sup>, F<sup>-</sup> sensing with good selectivity using appropriate receptor molecules
- *in-situ* functionalization on different surfaces with microchannels
- so far, up to 4 different functionalizations in a differential configuration on one chip



# beyond ions: biomolecules kinetics

## FimH detection (*bacterial lectin*)

with B. Ernst, G. Navarra, Dpt. Pharmacology, Uni Basel



**lectins:** carbohydrate-binding proteins involved in physiological and pathophysiological processes

e.g.: *cell-cell recognition, inflammation, infectious diseases (UTI), immune response, cancer*

see Sharon, J. Biol. Chem. 2007; Oppenheimer et al., Acta Histochem. 2010

**UTI therapy:** high-affinity FimH antagonists

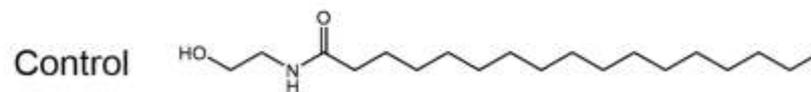
⇒ affinity screening tests: **SPR**

Ernst et al., J. Med. Chem. 2010, 2012; Chemmedchem 2012

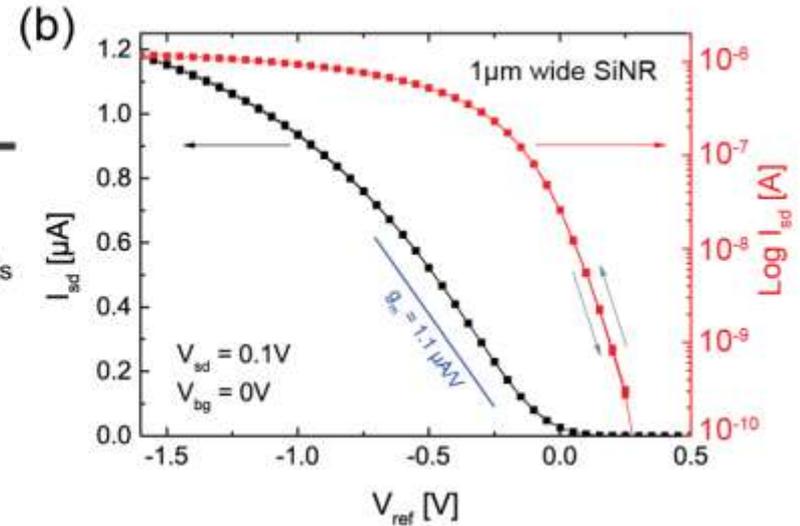
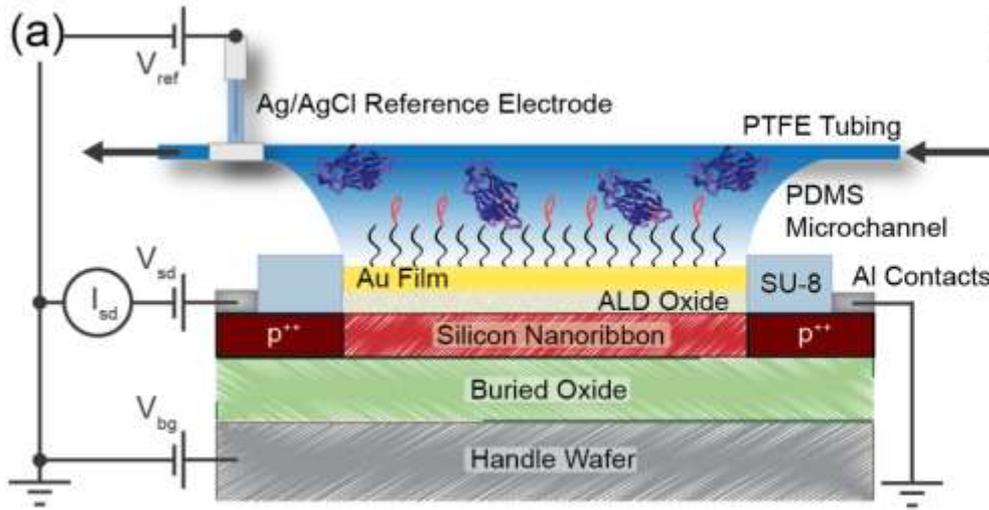
⇒ **can SiNW do the job ?**

**functionalization**

- mercaptohexadecanoic acid (MHDA)
- amine coupling for ligand



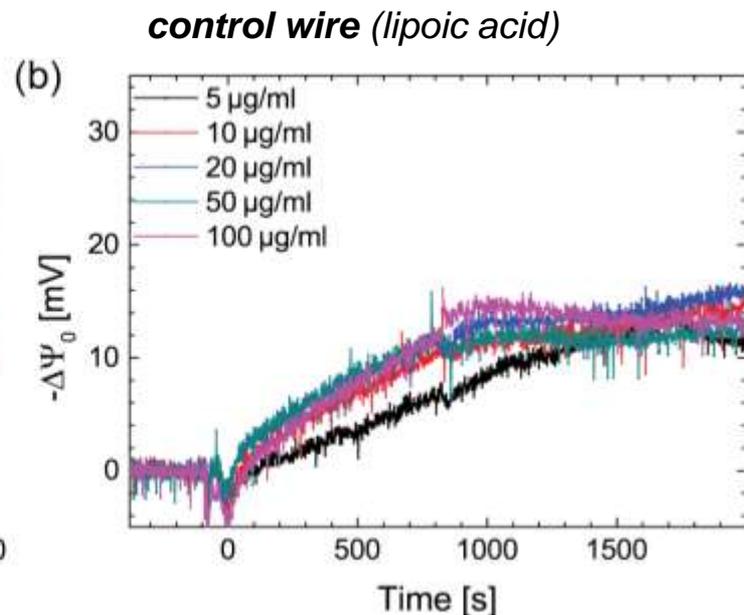
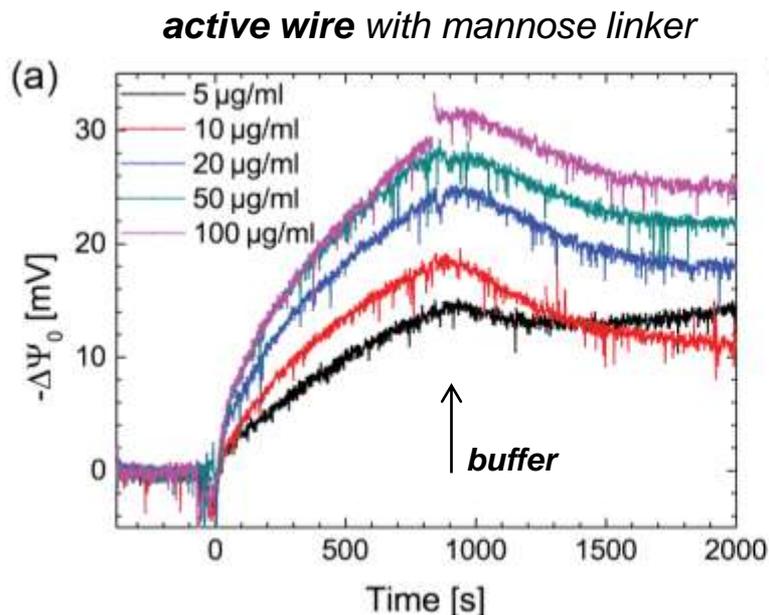
# beyond ions



- reduced ionic strength buffer: 10mM HEPES, pH 8 (Debye length  $\lambda_D \geq 3$  nm) ensure that the proteins are within the electrical double to affect the surface potential
- at pH 8: FimH neg. charged  $\Rightarrow I_{sd}$  increase upon binding
- SiNW operated in **linear region (constant transconductance  $g_m$ )**

# FimH binding kinetics vs concentration

SiNRs



SiNRs

- **non-specific adsorption** (control wire)  
*lipophilic character of MHDA layer*
- **signal only a function of surf. pot. change**  
*site binding model see Reed et al., Nat. Nano 2012.*

# surface bound ligands/m<sup>2</sup>

charge per analyte

$$\Delta\Psi_0 = -\Delta V_{th} = -\frac{\Delta I_{sd}}{g_m} = \frac{qA}{C_0} [B]_0 \times \frac{[A]}{K_D + [A]}$$

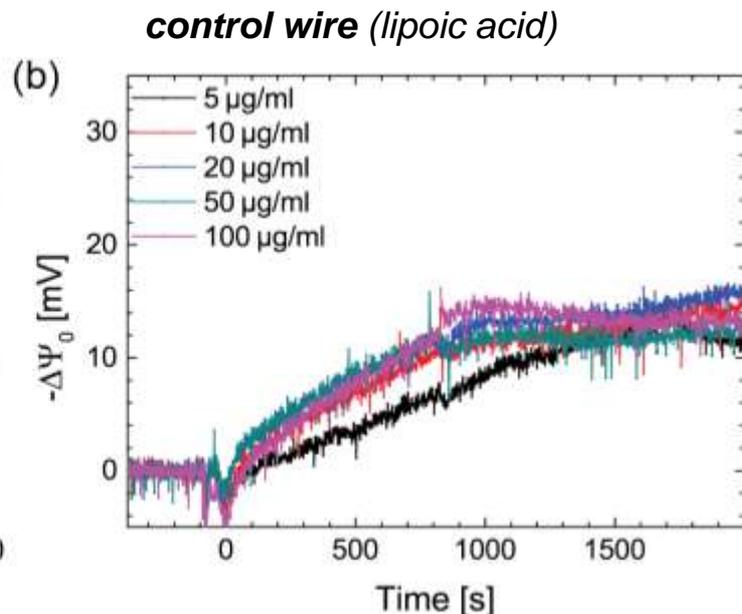
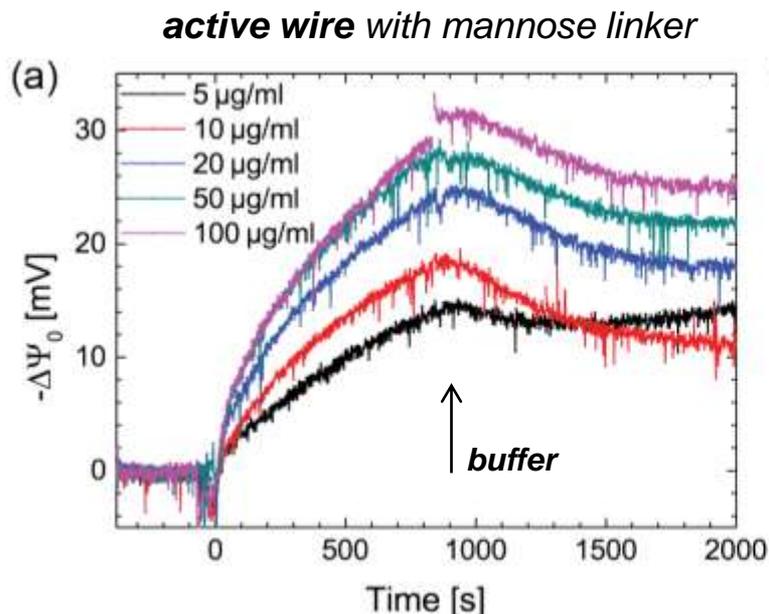
( $g_m = \partial I_{sd} / \partial V_{ref}$ )

equilibrium dissociation constant

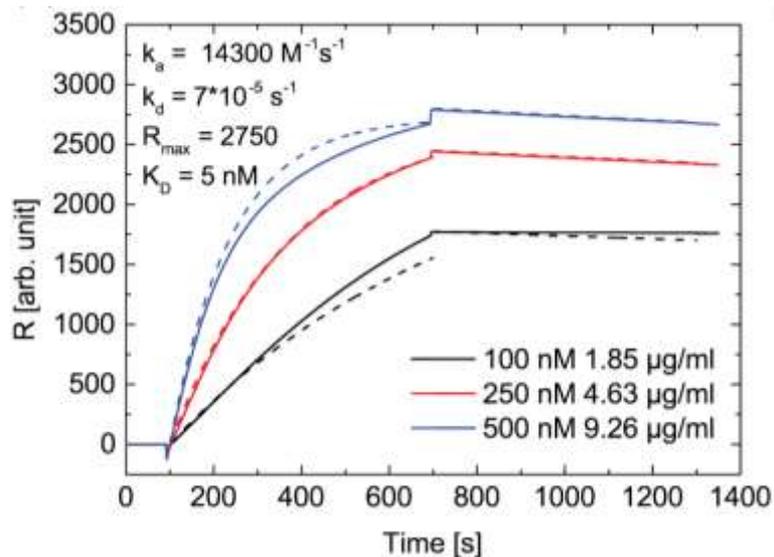
analyte bulk concentration

# FimH binding kinetics vs concentration

SiNRs



SPR



SiNRs

- **non-specific adsorption** (control wire)  
*lipophilic character of MHDA layer*
- **signal only a function of surf. pot. change**  
*see Reed et al., Nat. Nano 2012.*

SPR (Biacore T200, Navarra, Ernst et al., Basel)

- **saturation at lower FimH concentrations**
- **dissociation less pronounced**

*dashed lines: Langmuir kinetics*  
 $K_D \sim 5\text{nM}$  is obtained.

# FimH binding kinetics vs concentration

## comparison SiNRs & SPR

- different **association and dissociation rates** ( $k_a$ ,  $k_d$ )

**NB: variations between SPR systems!**

Cannon et al., *Anal. Biochem.* 2004; Katsamba et al., *Anal. Biochem.* 2006

## possible origins of differences

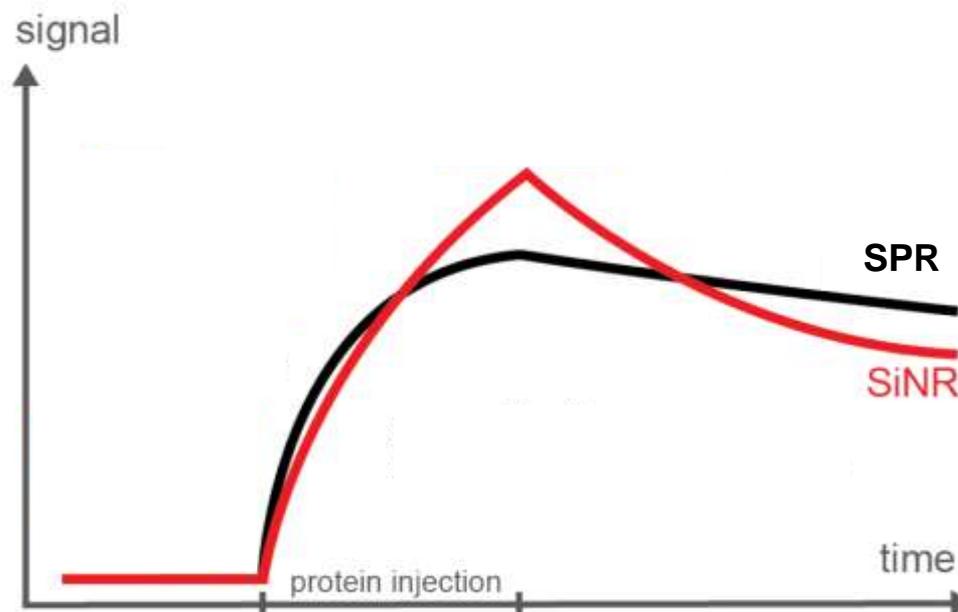
- **flow rate at sensor surface & different surface areas**

- *FimH*-mediated bacterial **adhesion affected by shear forces**  
see e.g. Vogel et al., *J. Bacteriol.* 2007, *J. Biol. Chem.* 2008  
- **re-adsorption** of proteins in flow

- **different effective protein concentration** (*fluidics*)

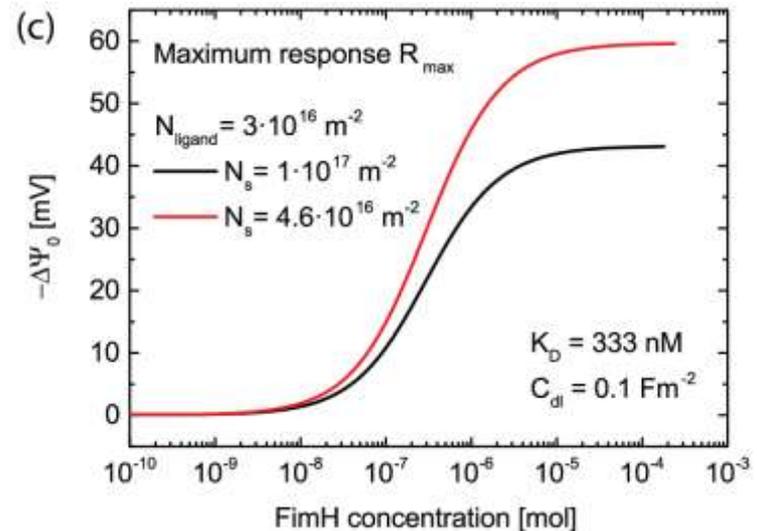
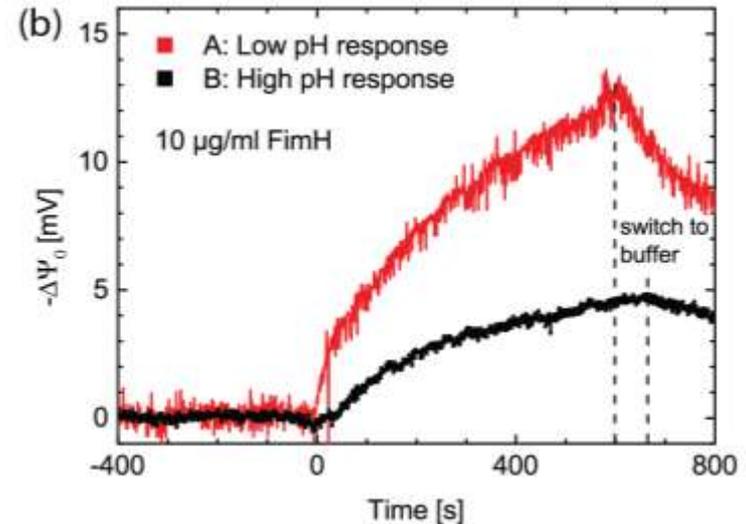
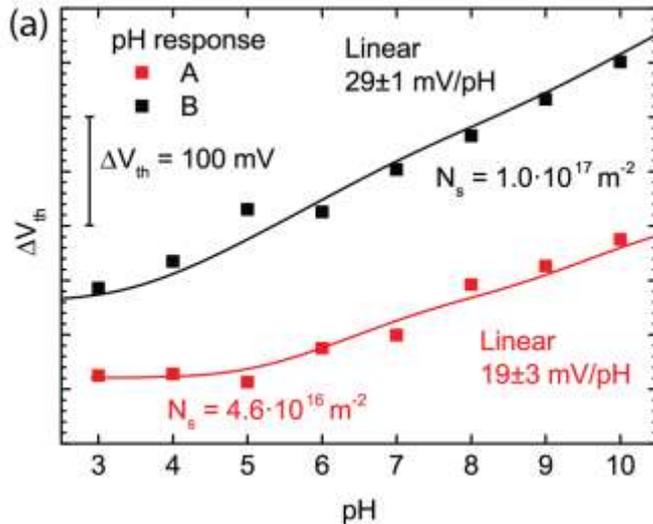
- **different sensing mechanisms: optical** ( $\lambda_{\text{evan}} \sim 300\text{nm}$ ) **or charge** ( $\lambda_D \sim 3\text{nm}$ )  
⇒ protein surface rearrangements affect SiNRs stronger than SPR, **longer time const.**

Rabe et al., *Adv. Colloid Interface Sci.* 2011, Roach et al., *JACS* 2005



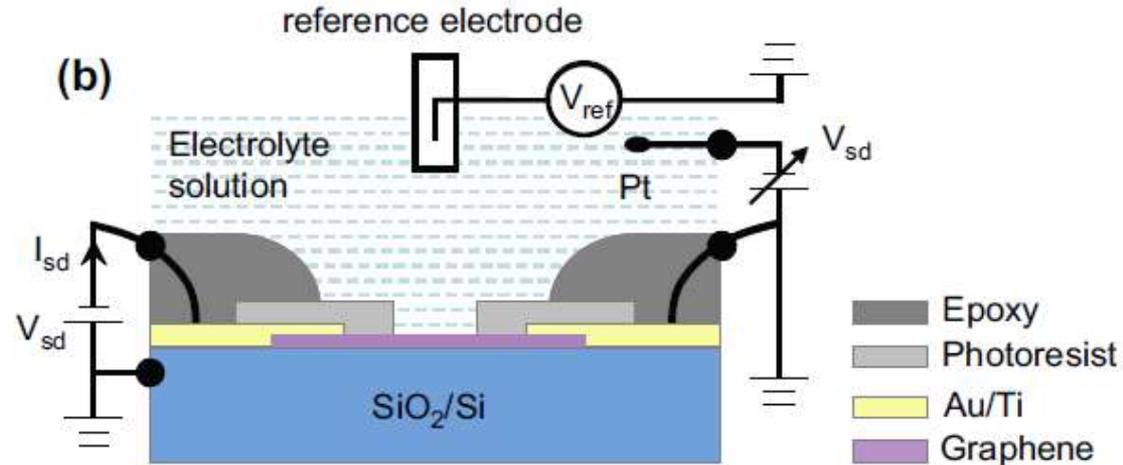
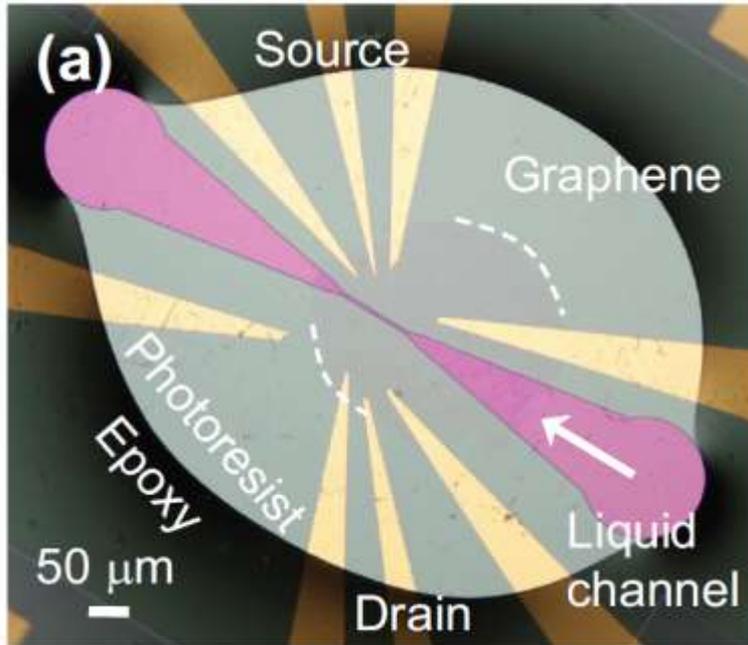
Fluidic channel	BioFET	Biacore
Flow rate	26 $\mu\text{L}/\text{min}$	20 $\mu\text{L}/\text{min}$
Height	100 $\mu\text{m}$	40 $\mu\text{m}$
Width	500 $\mu\text{m}$	500 $\mu\text{m}$
Length	4 mm	2.4 mm
Volume	$\approx 0.2 \mu\text{L}$	$\approx 0.05 \mu\text{L}$

# proteins detection: competing reactions



can we do it with graphene?

# Graphene ISFET

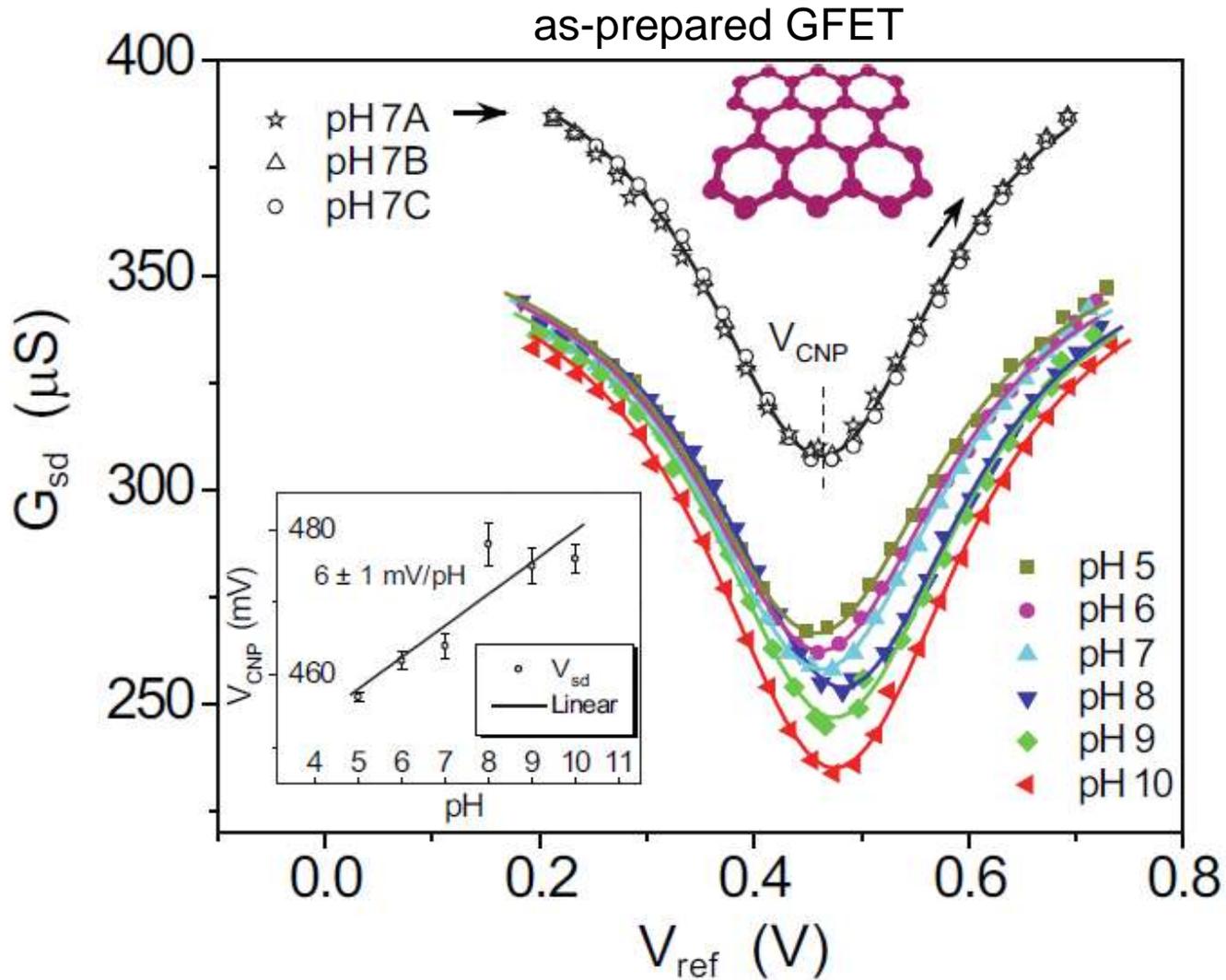


reported literature values for pH sensitivity

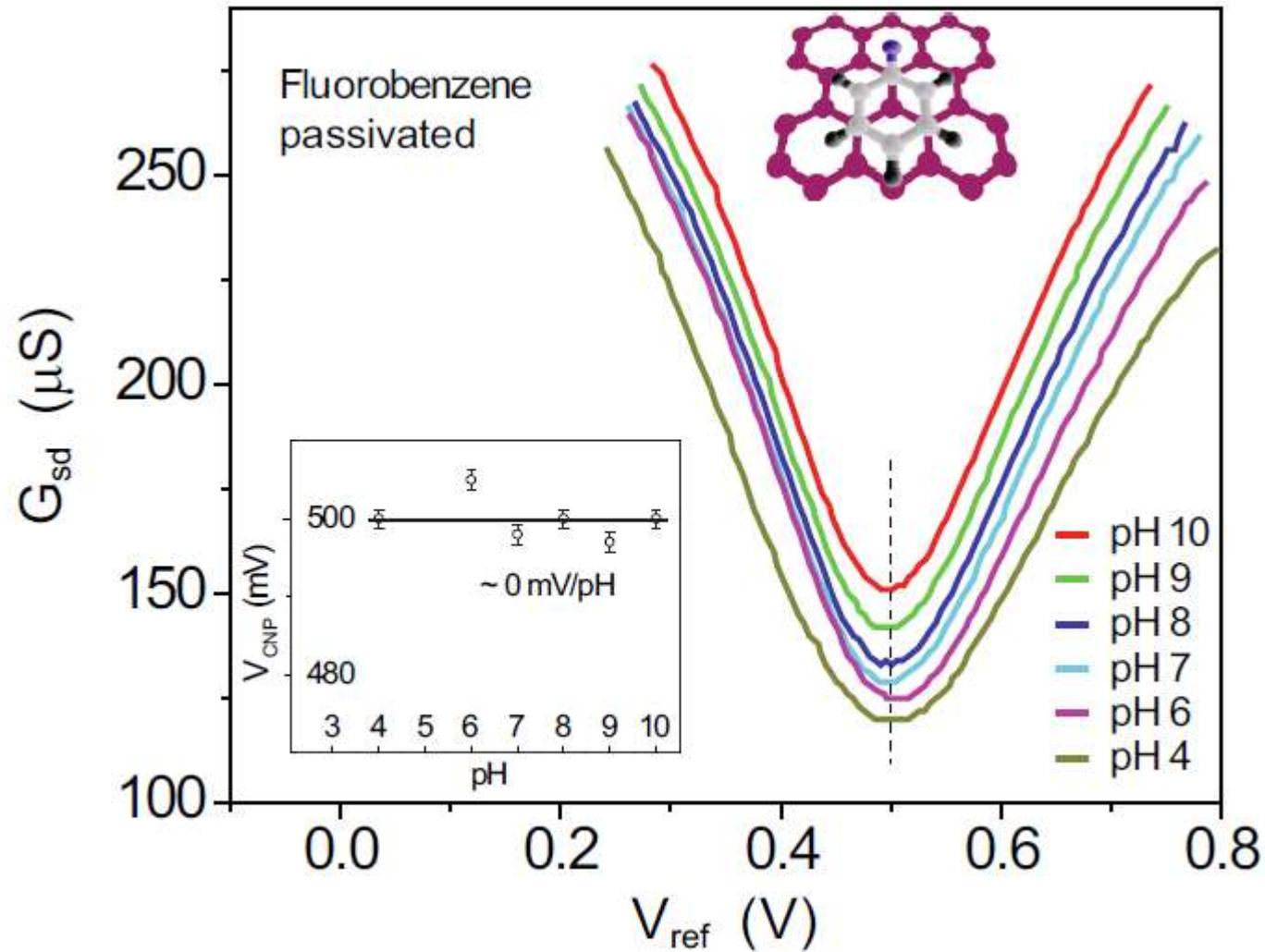
~12 mV/pH to ~100 mV/pH  
(vs liquid gate)

Ang et al., JACS (2008)  
Ristein et al., J. Phys. D: Appl. Phys. (2010)  
Cheng et al., Nano Lett. (2010)  
Ohno et al., Nano Lett. (2009)  
Heller et al., JACS (2010)

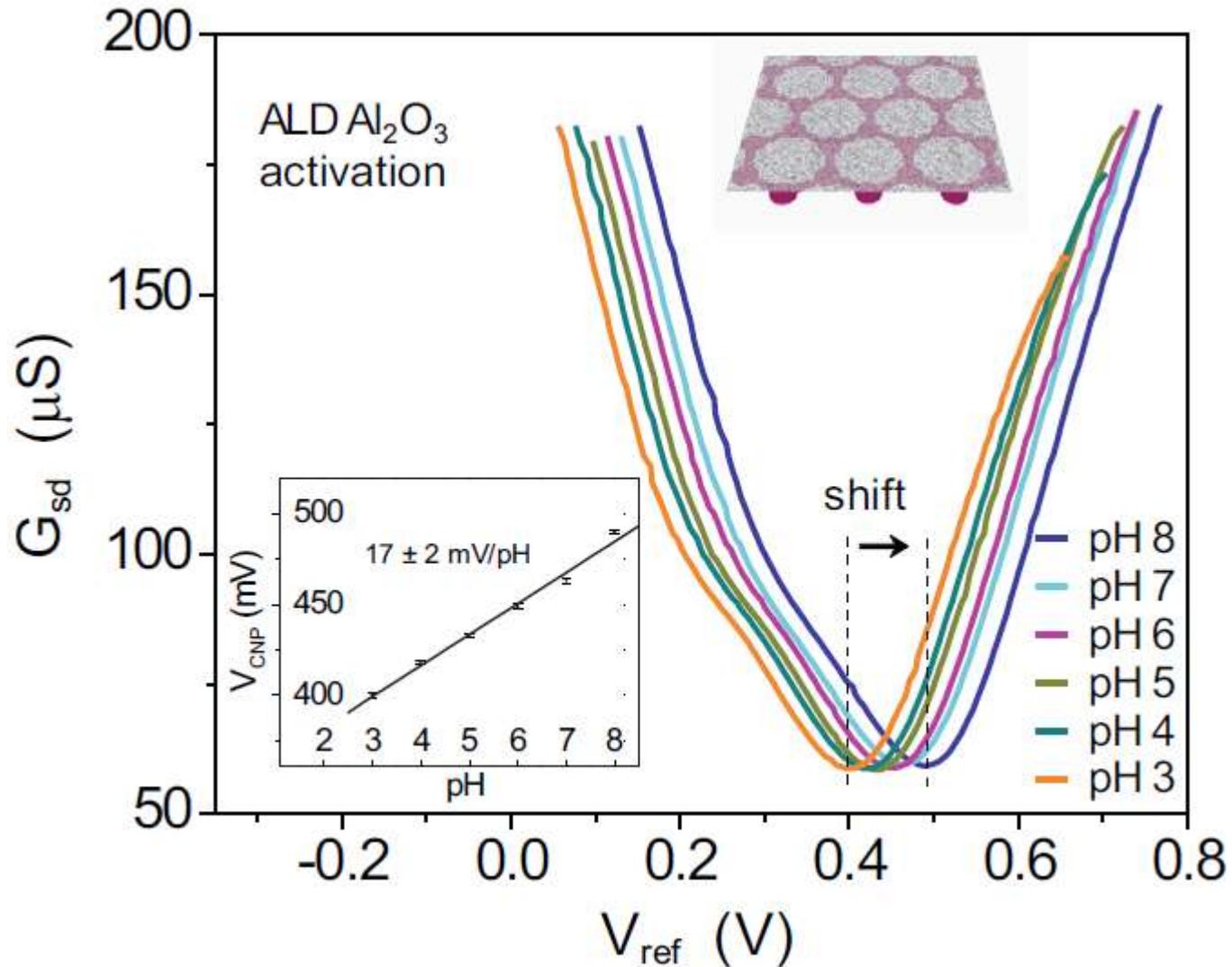
# Graphene ISFET



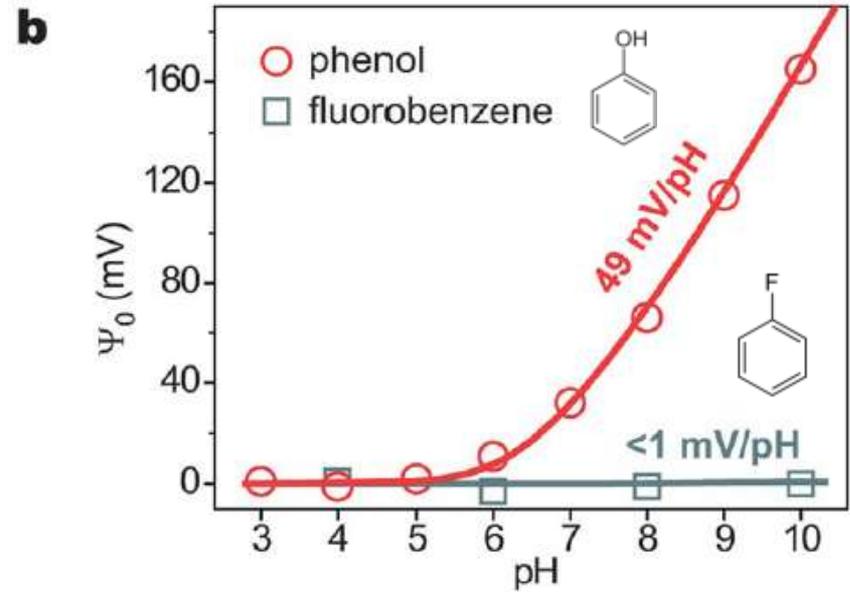
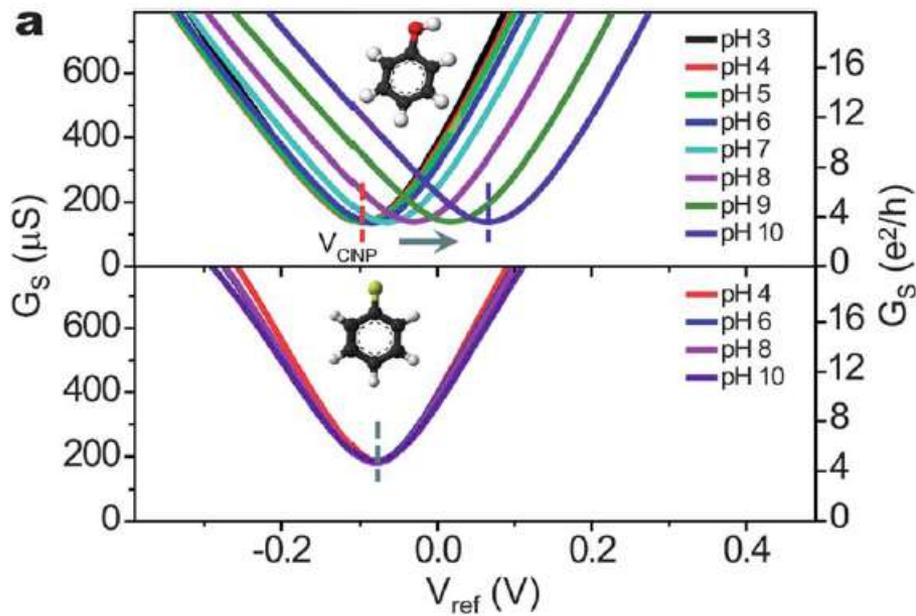
# Graphene ISFET: passivation



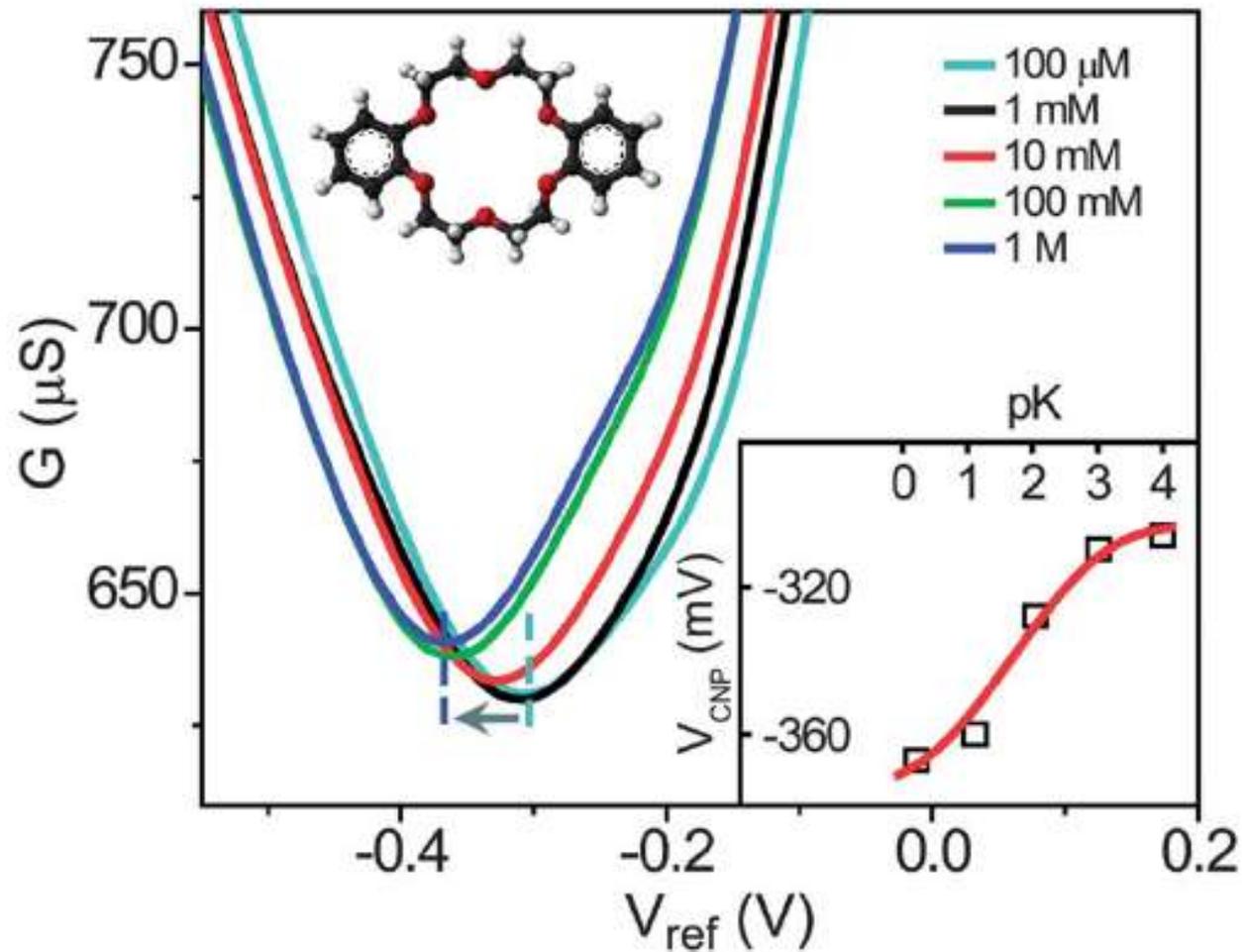
# Graphene FET: oxide layer



# Graphene ISFET: "active" molecule functionalization



# Graphene ISFET: response to K<sup>+</sup> ions



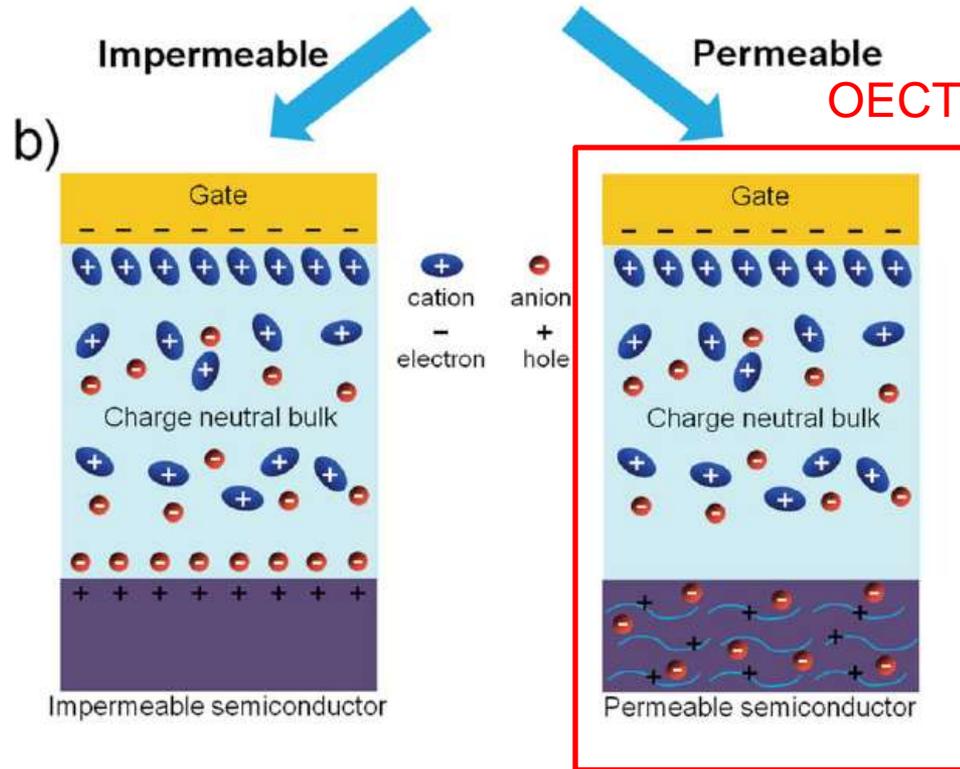
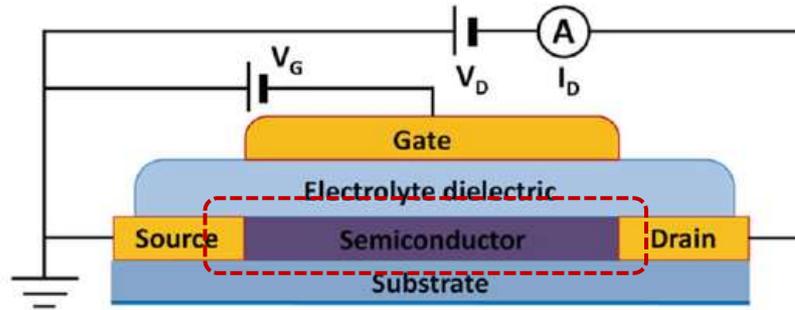
**NB: similar research for CNTs**

see e.g. M. Hersam et al., *Chem. Soc. Rev.* 42, 2824 (2013)

W. Fu, C. Nef et al., *Nanoscale*. 2013

can we do it with ... conducting polymers ?

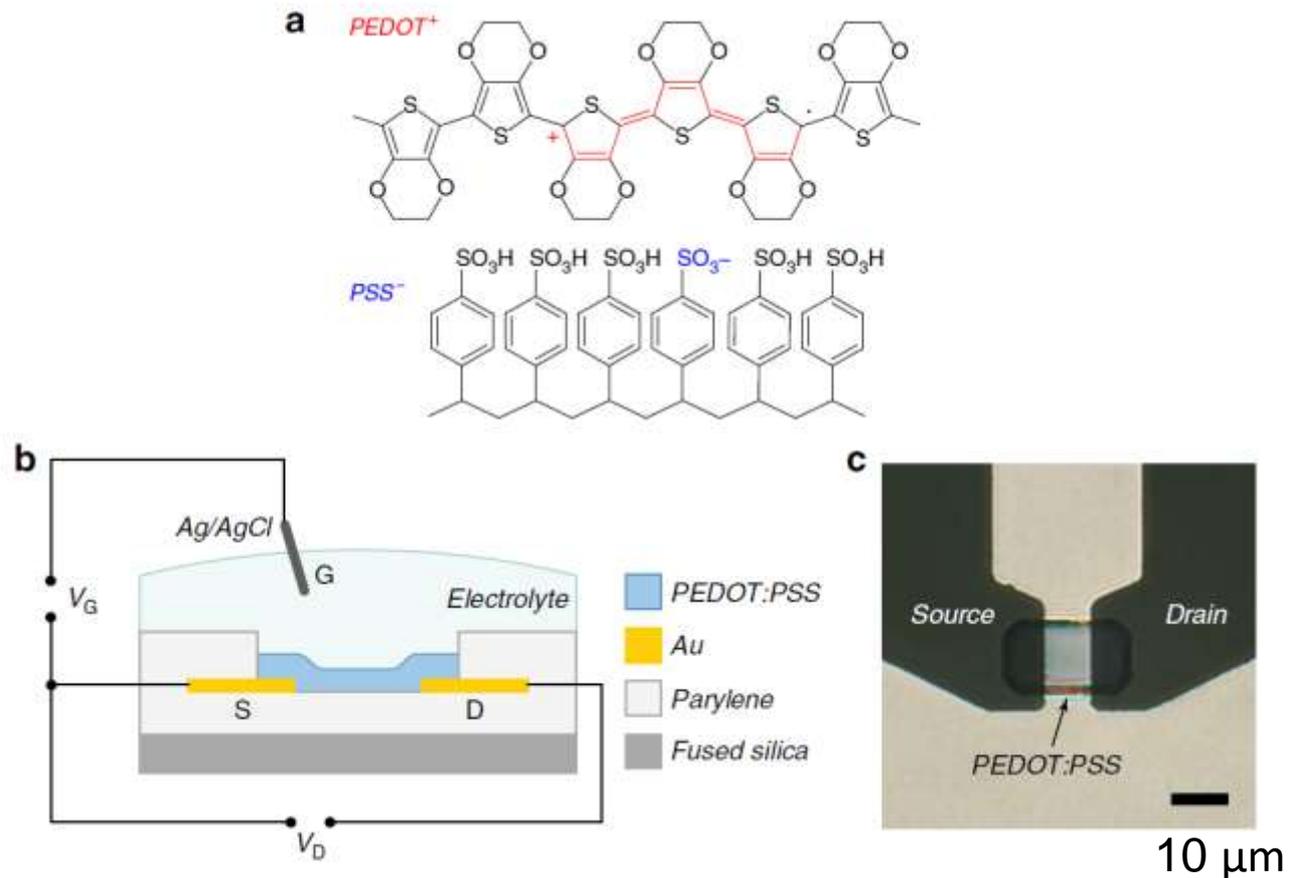
# organic electrochemical transistors (OECTs)



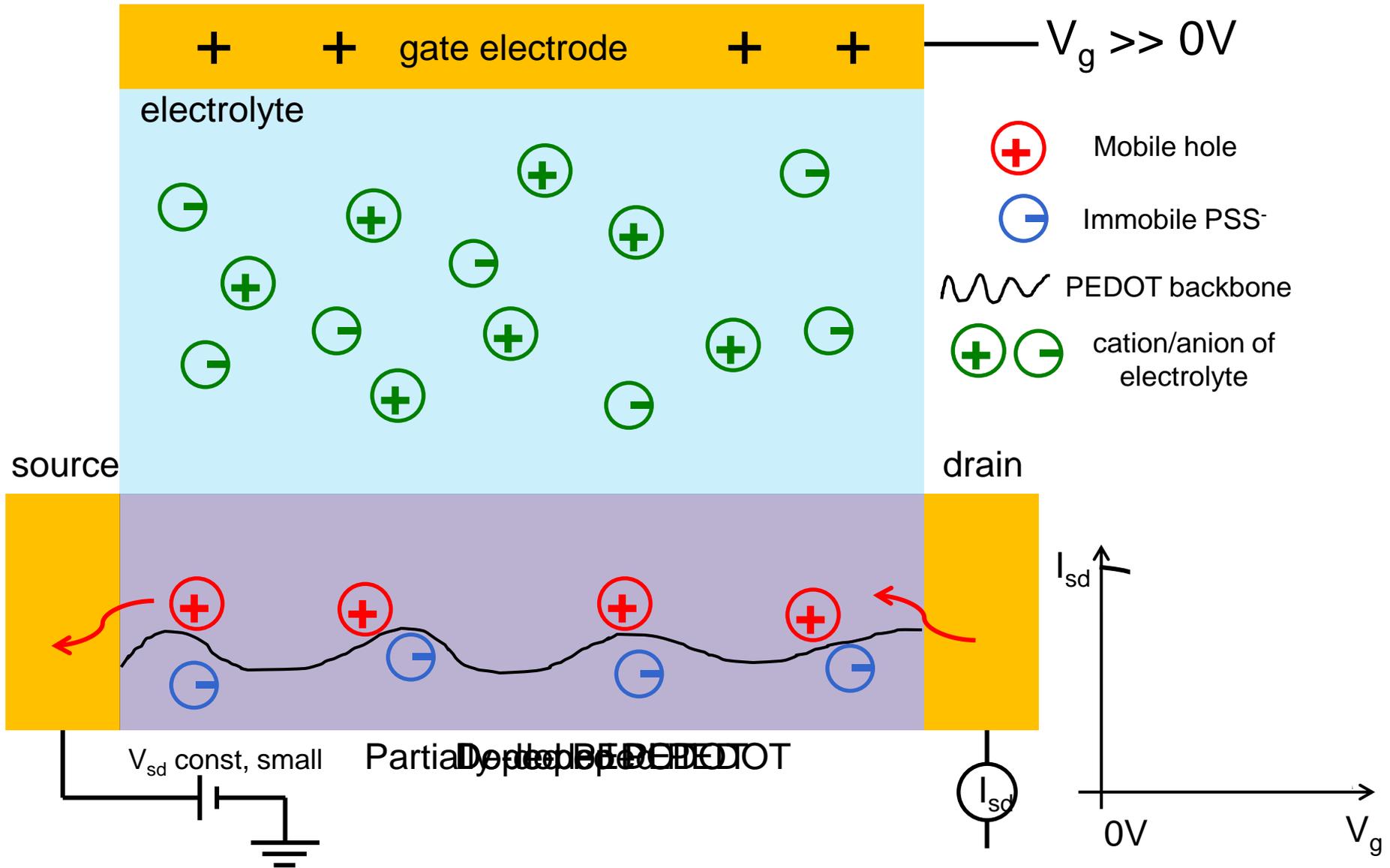
## Common assumptions:

- p-type semiconductor ( $n_p=10^{21}$ - $10^{23}\text{cm}^{-3}$ )
- constant mobility ( $\mu_h=0.045$ - $1\text{ cm}^2/\text{Vs}$ )
- Injected ions distribute homogeneously

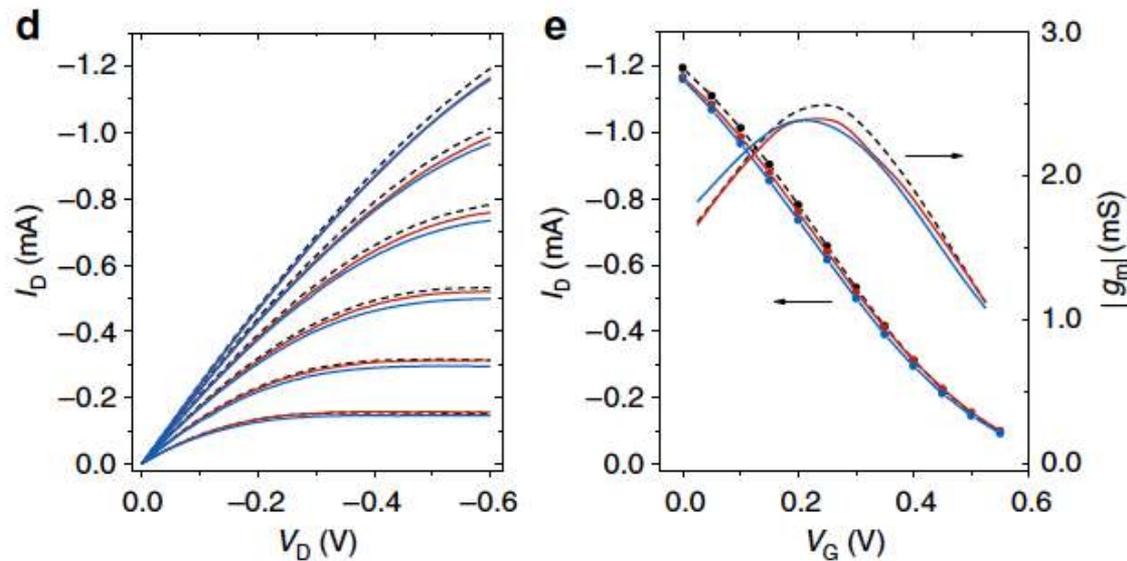
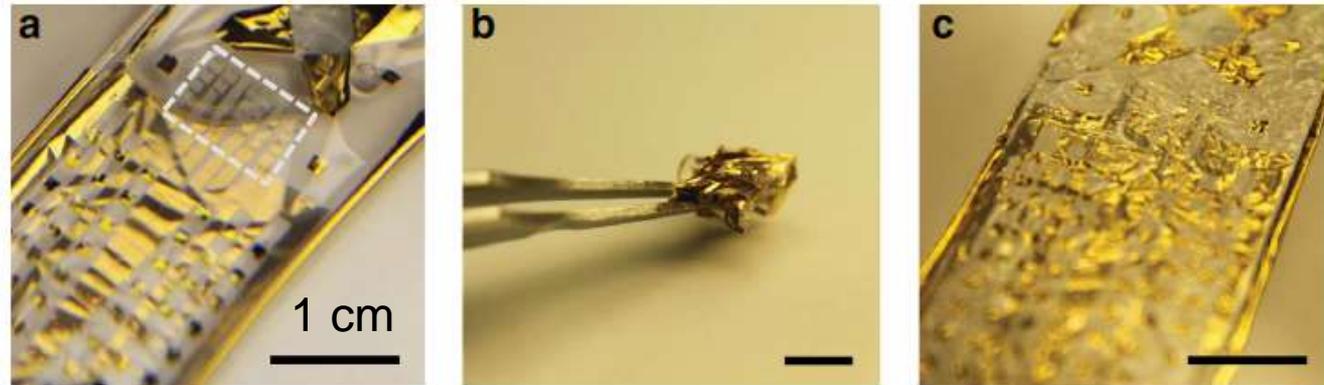
# organic electrochemical transistors (OECTs): PEDOT:PSS



# working principle PEDOT:PSS OECT



# OECTs - mechanical stability



black: as prepared  
red: after peeling  
blue: after crumpling

⇒ R. Stoop, M. Sessolo et al.: characterization & noise measurements  
*Phys Rev. Applied* (2017)

- **general aspects on sensing**  
*sensitivity, specificity*  
*overview of transducers*
- **field effect transistors (FETs) as charge sensors**  
*MOSFET, graphene and GFET*

## **Examples**

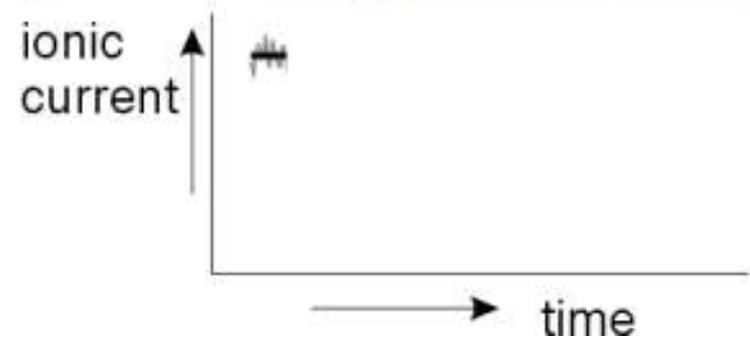
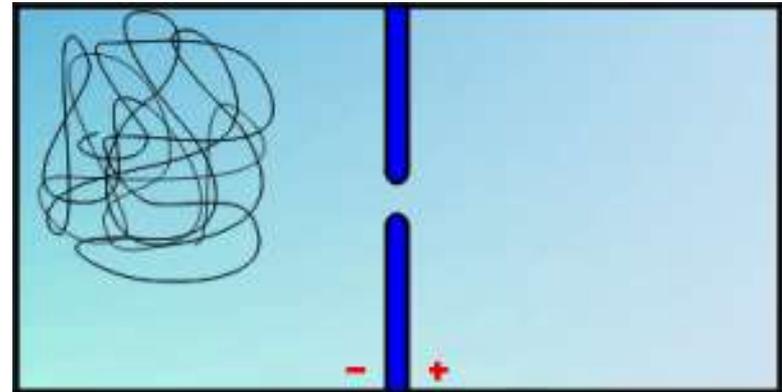
- Ion sensitive field-effect transistors (ISFETs) for pH, ionic and biochemicals detection
- Nanopores for sequencing

# DNA sequencing using nanopores

- **basic principle: DNA translocation and current blockade**  
*cf Coulter counter for single cells*

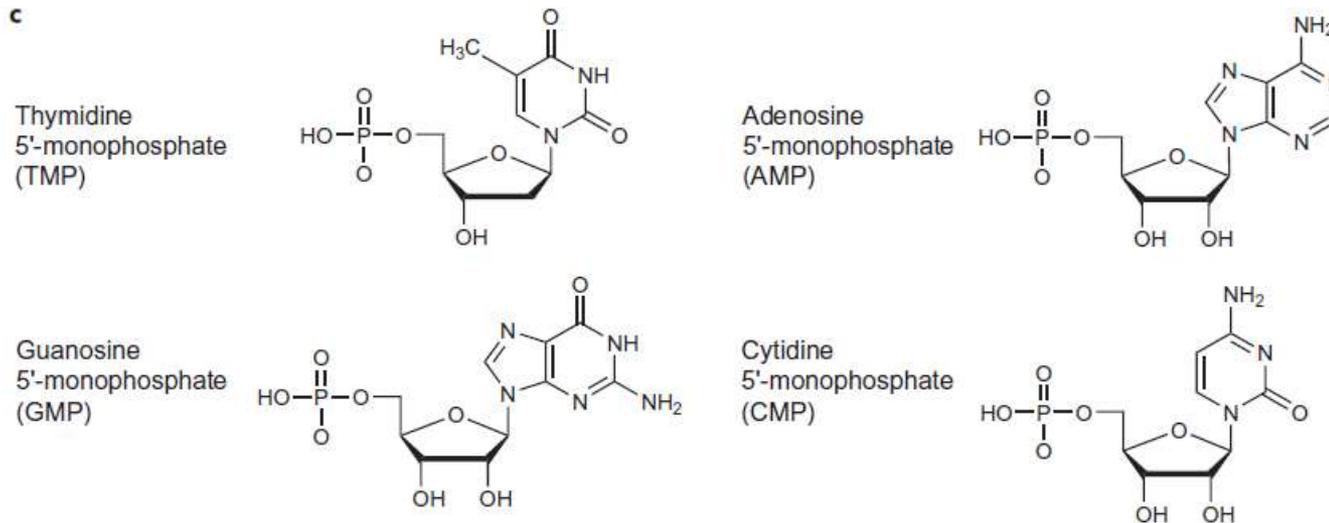
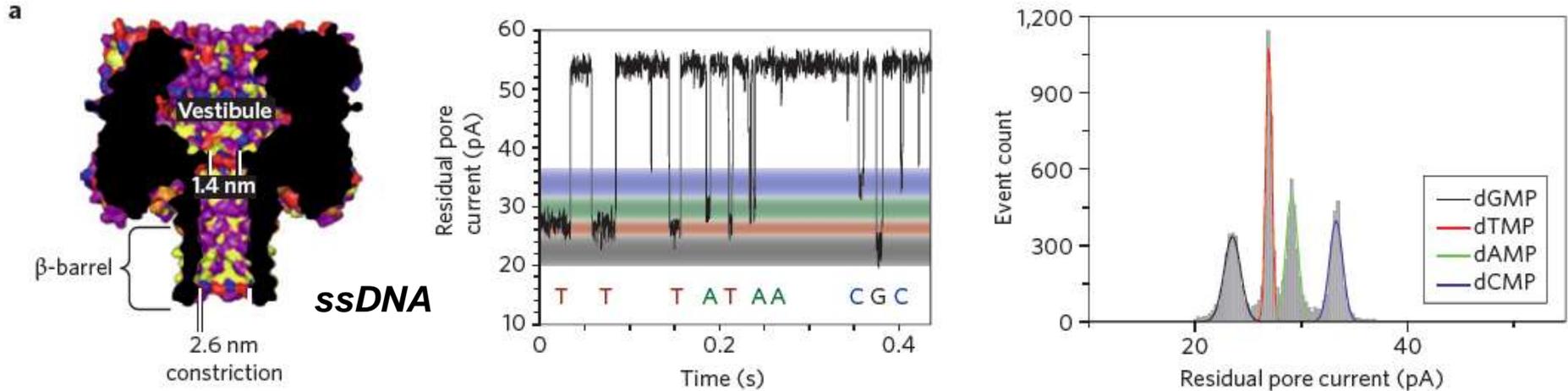


small diameter, high repetition rate  
**identification of bases?**



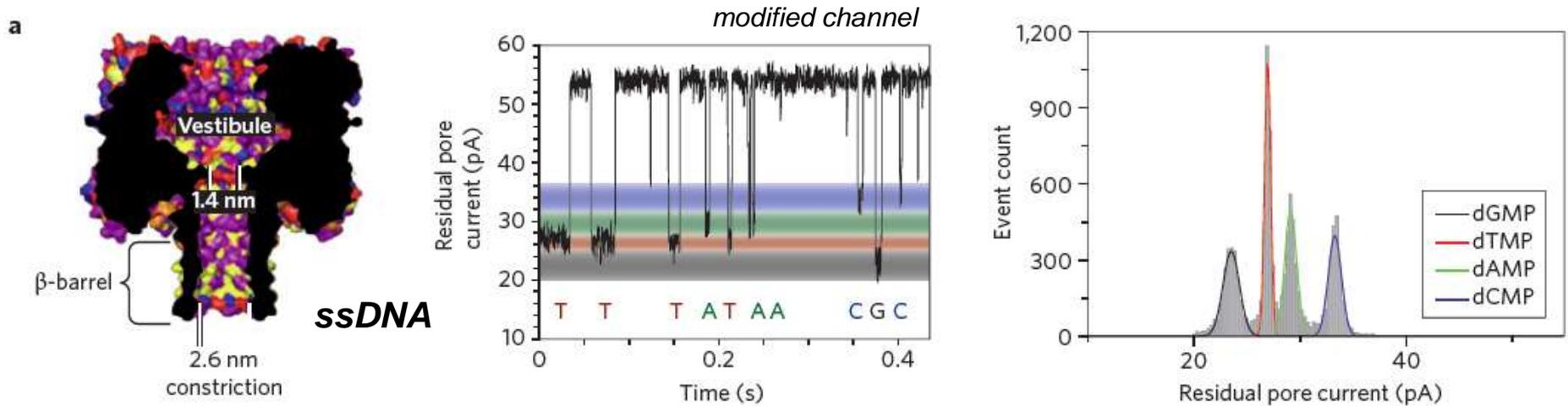
# DNA sequencing using nanopores

## biological nanopores structural cross-section of $\alpha$ -haemolysin

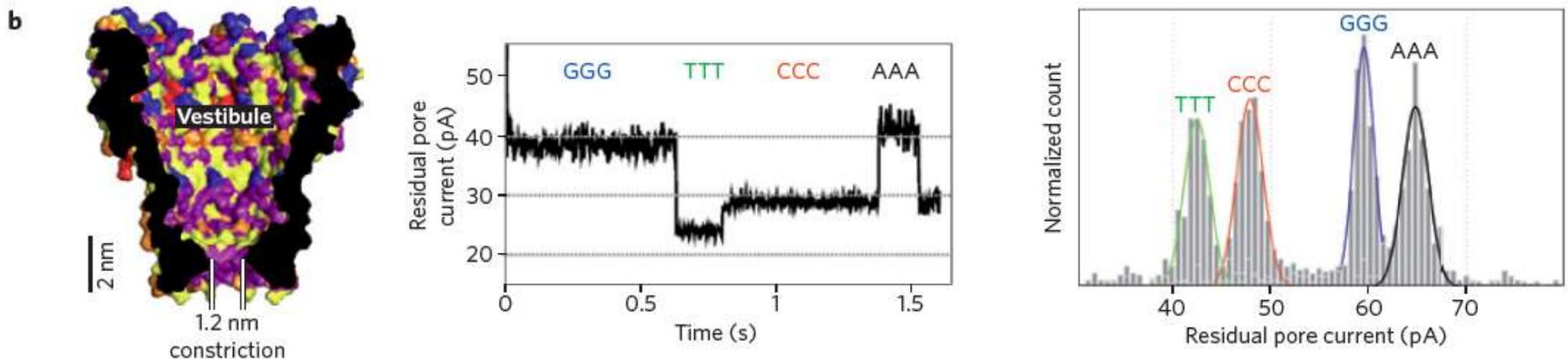


# DNA sequencing using nanopores

## structural cross-section of $\alpha$ -haemolysin



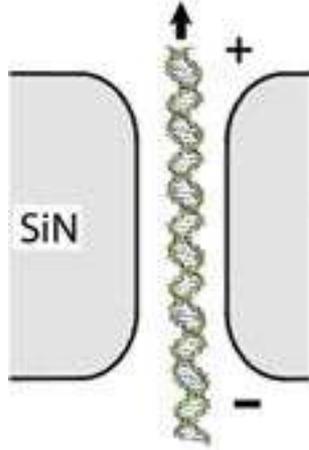
## structural cross-section of MspA



### ***dsDNA segment with ssDNA triplets***

*dsDNA temporarily blocks translocation until dsDNA dissociates due to high local electric field*

# solid state nanopores

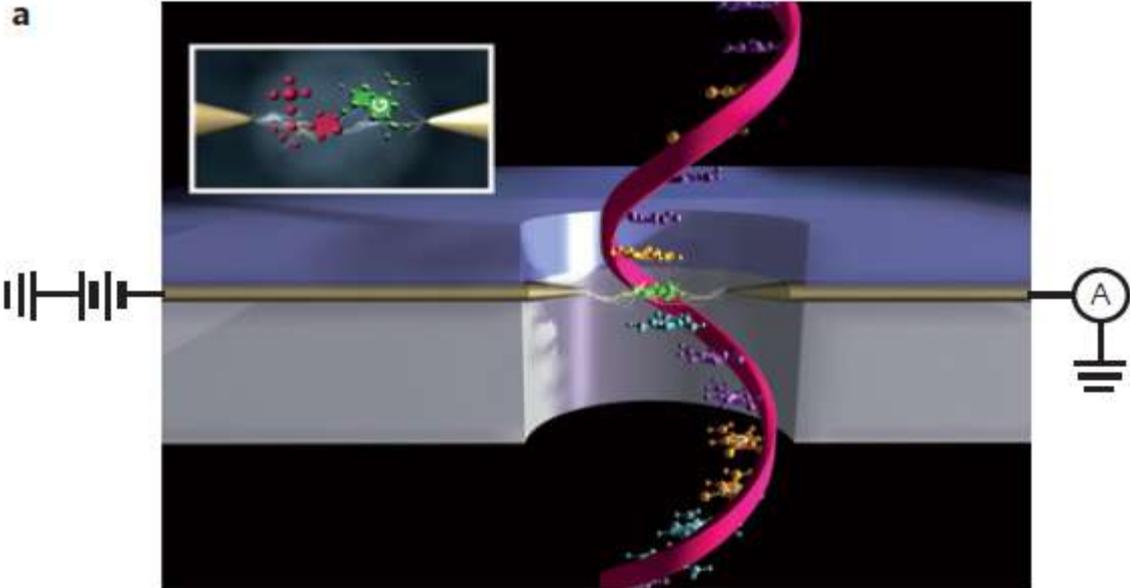


**drawback:** thickness of channel (SiN membrane)  
*channel will contain many bases (base to base: <0.5nm)*

⇒ ***no high-resolution DNA sequencing***

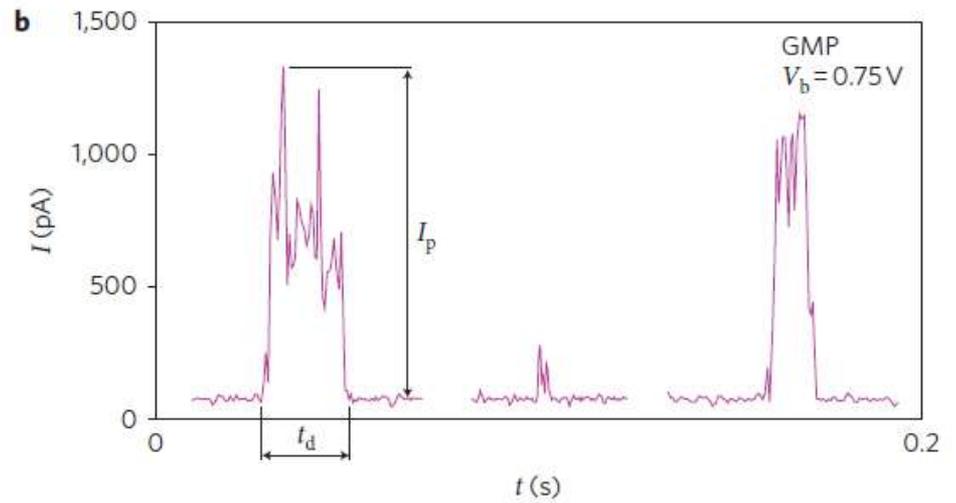
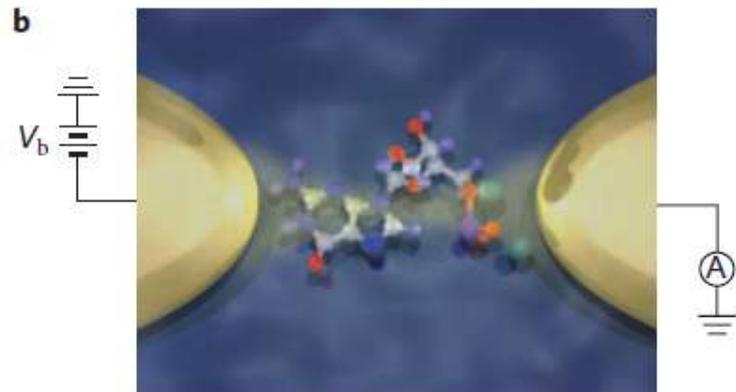
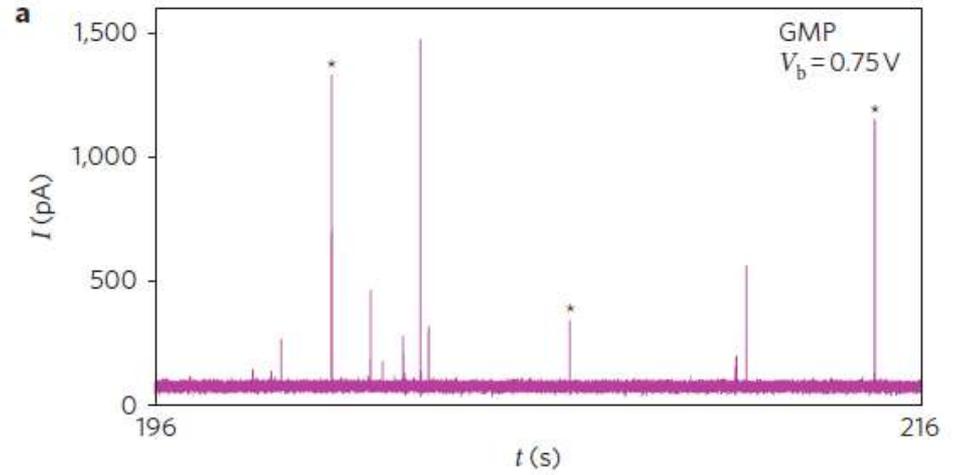
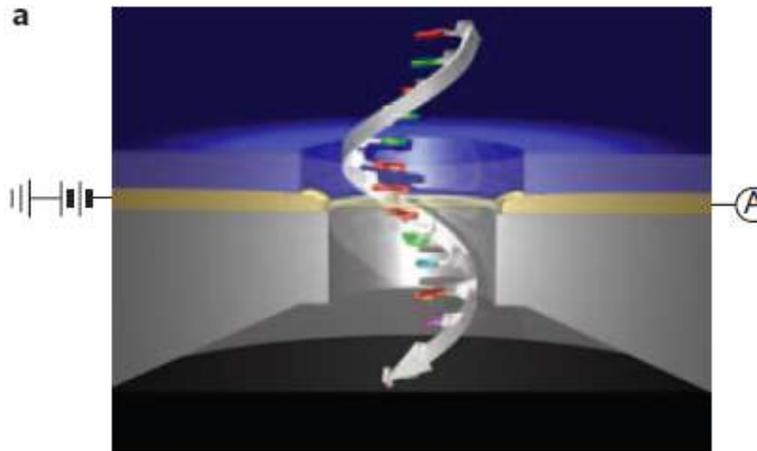
*Dekker et al.,*

**possible solution: integrate tunnel device**

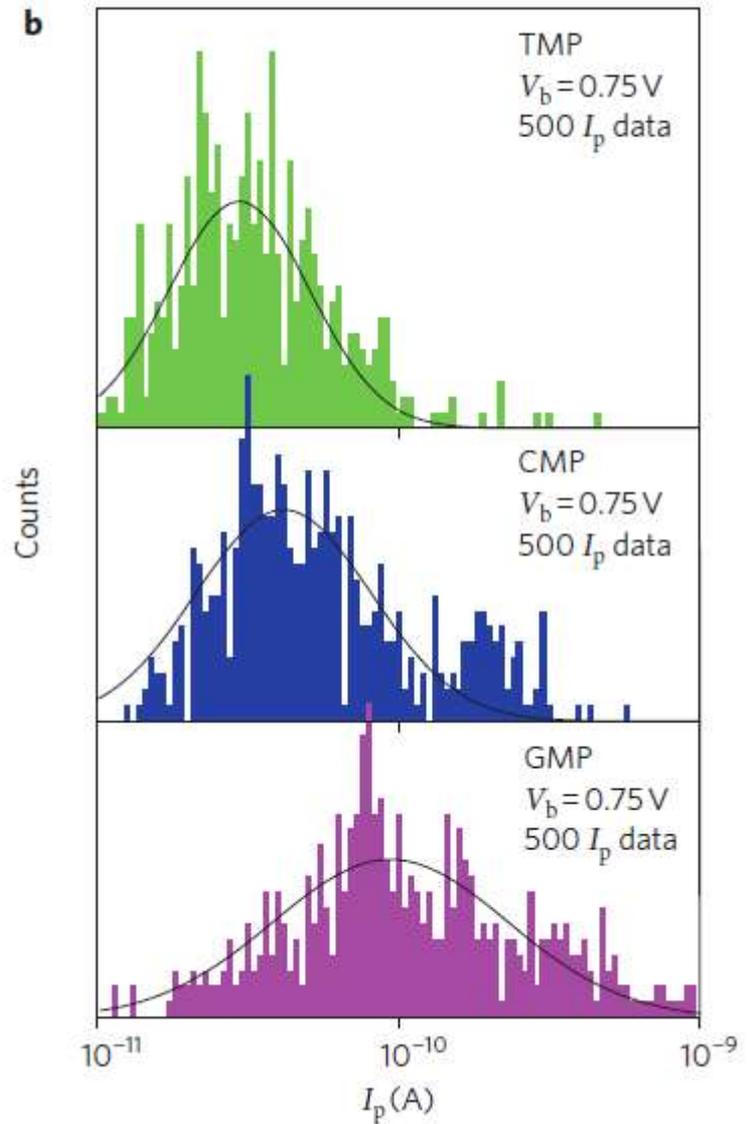
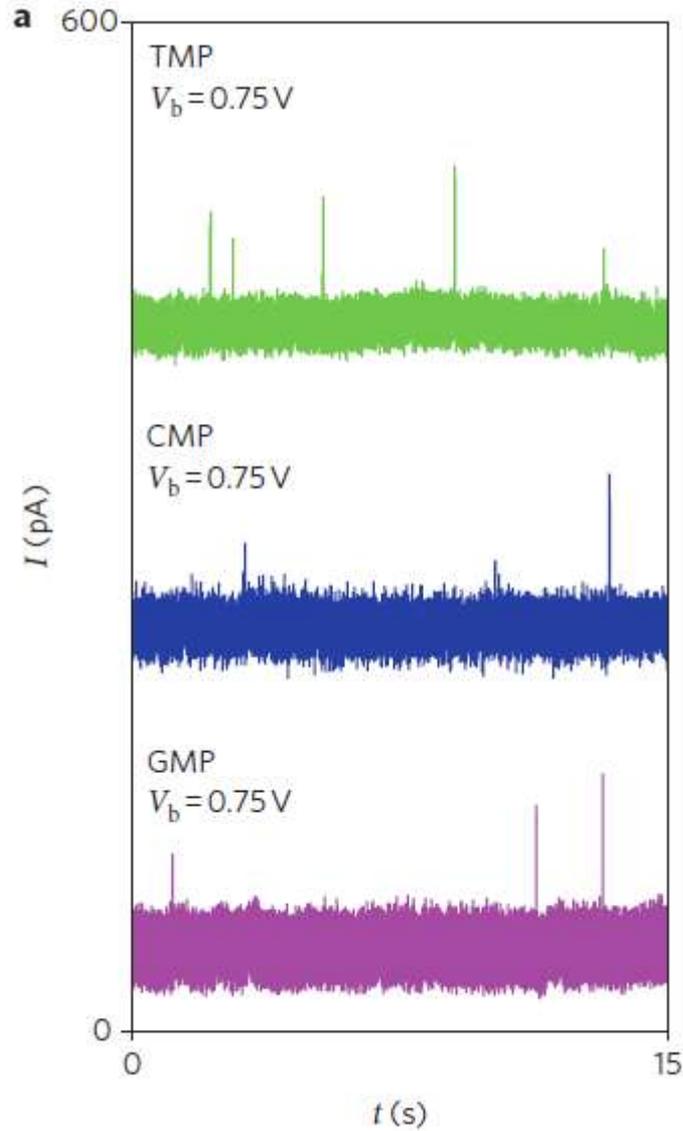


*Bashir et al., Nat. Nano, (2011)*  
*Kawai et al., Nat. Nano (2010)*

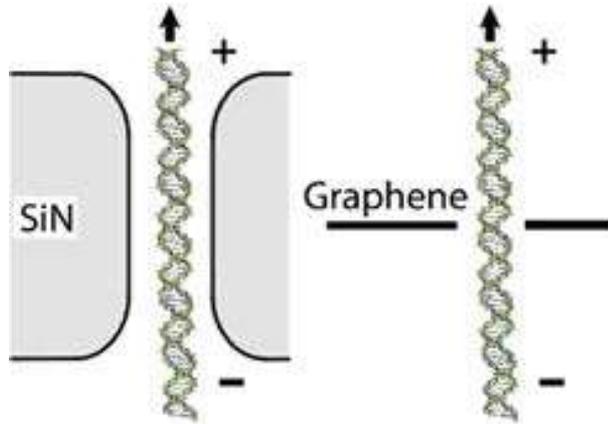
# solid state nanopores



# solid state nanopores

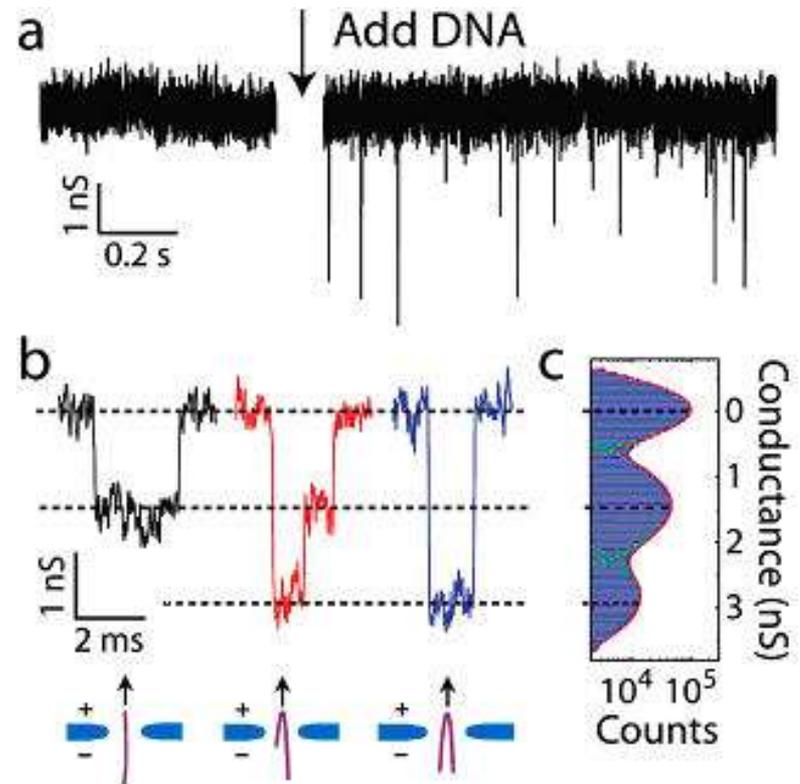
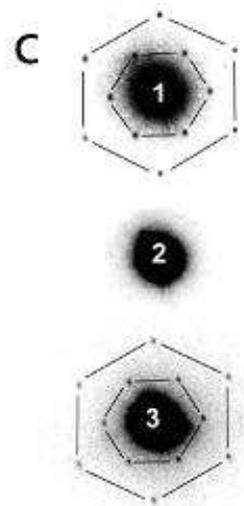
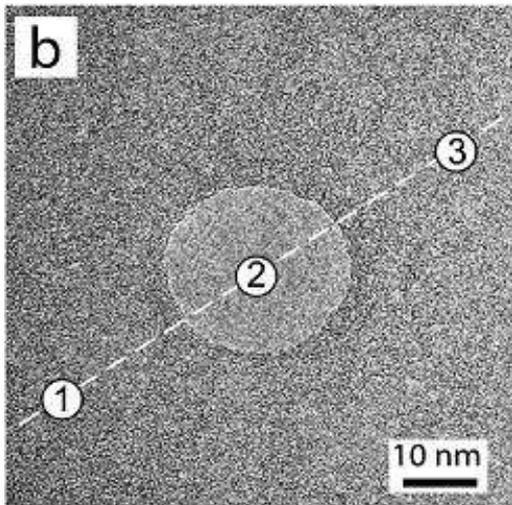


# graphene nanopores



- + thinner than 1 base
- + can be used as electrode to detect base
- hydrophobic

proof of concept: 22nm hole, monolayer graphene  
lambda DN translocation



# An integrated semiconductor device enabling non-optical genome sequencing

Jonathan M. Rothberg<sup>1</sup>, Wolfgang Hinz<sup>1</sup>, Todd M. Rearick<sup>1</sup>, Jonathan Schultz<sup>1</sup>, William Mileski<sup>1</sup>, Mel Davey<sup>1</sup>, John H. Leamon<sup>1</sup>, Kim Johnson<sup>1</sup>, Mark J. Milgrew<sup>1</sup>, Matthew Edwards<sup>1</sup>, Jeremy Hoon<sup>1</sup>, Jan F. Simons<sup>1</sup>, David Marran<sup>1</sup>, Jason W. Myers<sup>1</sup>, John F. Davidson<sup>1</sup>, Annika Branting<sup>1</sup>, John R. Nobile<sup>1</sup>, Bernard P. Puc<sup>1</sup>, David Light<sup>1</sup>, Travis A. Clark<sup>1</sup>, Martin Huber<sup>1</sup>, Jeffrey T. Branciforte<sup>1</sup>, Isaac B. Stoner<sup>1</sup>, Simon E. Cawley<sup>1</sup>, Michael Lyons<sup>1</sup>, Yutao Fu<sup>1</sup>, Nils Homer<sup>1</sup>, Marina Sedova<sup>1</sup>, Xin Miao<sup>1</sup>, Brian Reed<sup>1</sup>, Jeffrey Sabina<sup>1</sup>, Erika Feierstein<sup>1</sup>, Michelle Schorn<sup>1</sup>, Mohammad Alanjary<sup>1</sup>, Eileen Dimalanta<sup>1</sup>, Devin Dressman<sup>1</sup>, Rachel Kasinskas<sup>1</sup>, Tanya Sokolsky<sup>1</sup>, Jacqueline A. Fidanza<sup>1</sup>, Eugeni Namsaraev<sup>1</sup>, Kevin J. McKernan<sup>1</sup>, Alan Williams<sup>1</sup>, G. Thomas Roth<sup>1</sup> & James Bustillo<sup>1</sup>

The seminal importance of DNA sequencing to the life sciences, biotechnology and medicine has driven the search for more scalable and low-cost sequencing technologies. We describe a DNA sequencing technology in which scalable, low-cost semiconductor devices are used to make **an integrated circuit able to directly perform sequencing of genomes**. Sequence data are obtained by directly sensing the ion-mediated DNA polymerase synthesis using all-natural nucleotides on this massive array of sensing device or ion chip. The ion chip contains **ion-sensitive, field-effect transistors in perfect register with 1.2 million wells**, which provide confinement and catalytic reactions. Use of the most widely used metal-oxide semiconductor (CMOS) technology enables **large-scale production and scaling of the device to higher densities and larger array sizes**. We show the performance of the system by sequencing three bacterial genomes, its robustness and scalability by producing ion chips with up to 10 times as many sensors and sequencing a human genome.

**1000 US\$ /  
genome sequencing**

**IonTorrent/  
ThermoFischer**

# NB: sequencing using ... ISFETs

